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(19) **United States**(12) **Patent Application Publication**
Machida et al.(10) **Pub. No.: US 2012/0316445 A1**(43) **Pub. Date: Dec. 13, 2012**(54) **ULTRASONIC TRANSDUCER AND
ULTRASONIC DIAGNOSTIC DEVICE USING
SAME**(76) Inventors: **Shuntaro Machida**, Kokubunji
(JP); **Taiichi Takezaki**, Tachikawa
(JP); **Toshiyuki Mine**, Fussa (JP)(21) Appl. No.: **13/577,816**(22) PCT Filed: **Jan. 25, 2011**(86) PCT No.: **PCT/JP2011/051344**

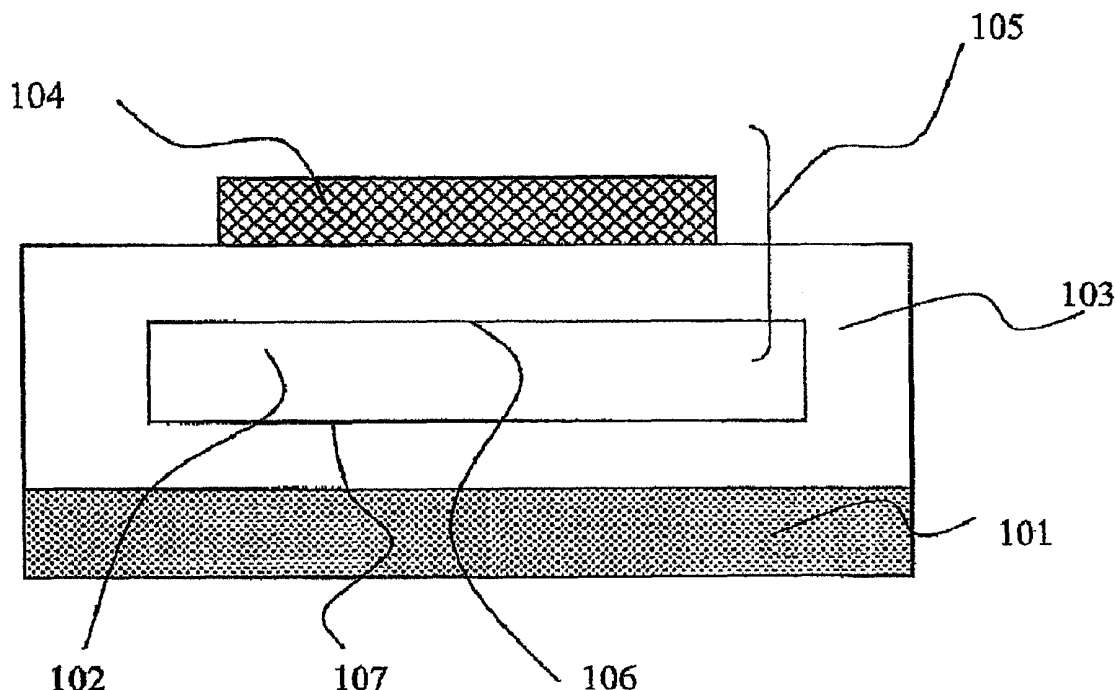
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(2), (4) Date: **Aug. 8, 2012**(30) **Foreign Application Priority Data**

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H02N 1/08 (2006.01)
A61B 8/00 (2006.01)(52) **U.S. Cl.** **600/459; 310/300**(57) **ABSTRACT**

In an ultrasonic transducer comprising a first electrode, a first insulating film disposed on the first electrode, a hollow part provided above the first insulating film and disposed between surfaces above and below the hollow part, a second insulating film disposed above the hollow part, and a second electrode disposed on the second insulating film, a first conductive film disposed on the side of the surface below the hollow part and a second conductive film disposed on the side of the surface above the hollow part are provided, the first conductive film and the second conductive film are disposed so that they overlap with a region in which the surfaces above and below the hollow part contact with each other as seen from above when the transducer is driven, and they do not overlap with each other in the region as seen from above. With such a configuration, there are provided a structure suitable for, even when the surface above the hollow part contacts with the surface below the hollow part, suppressing concentration of electric fields and electric currents in the insulating films in the contact region, and suppressing injection of electrical charge into the insulating films and degradation of dielectric strength thereof, and an ultrasonic diagnostic device using it.



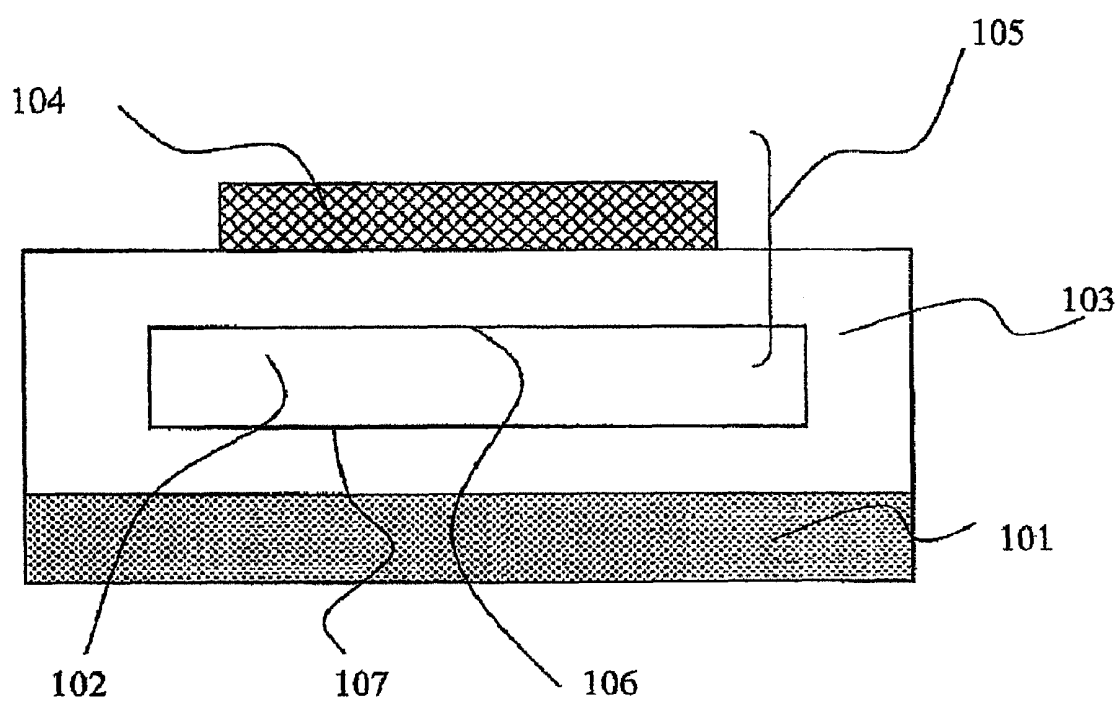


Fig. 1

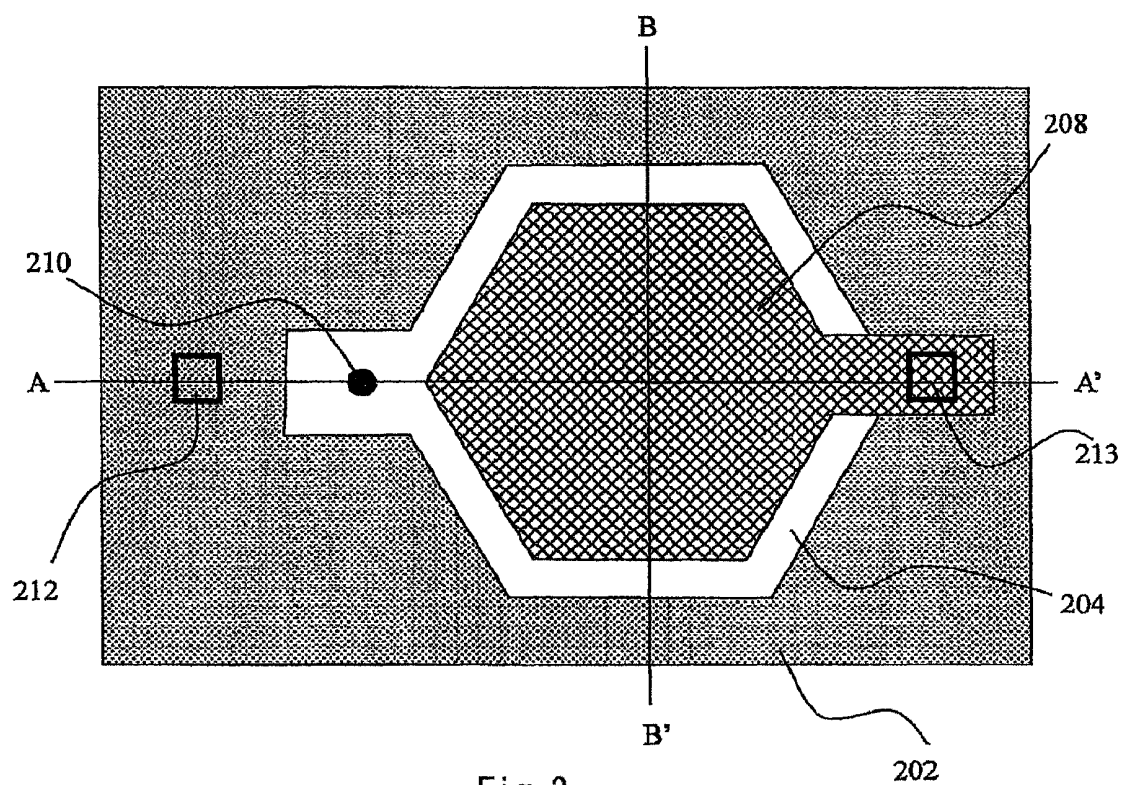
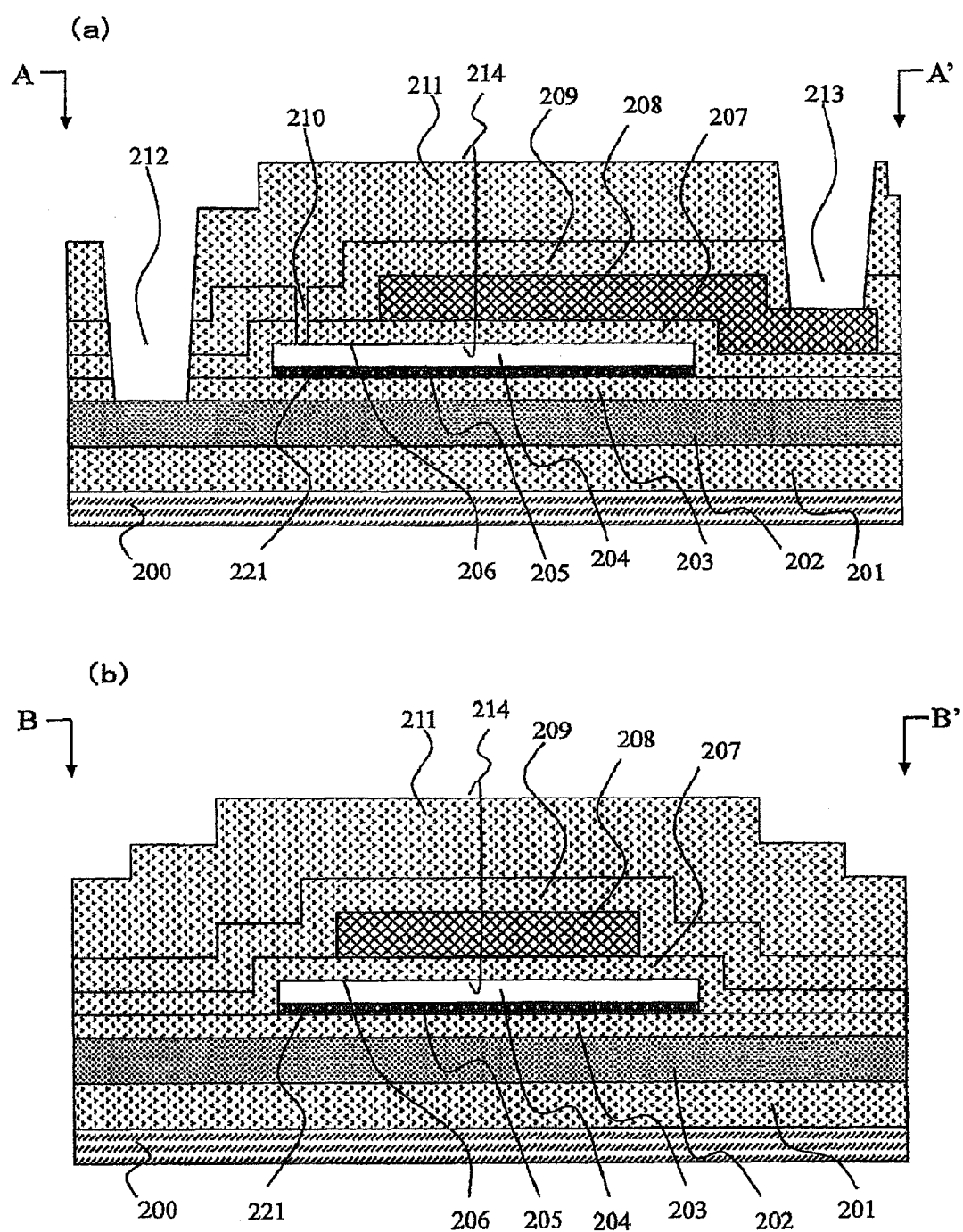
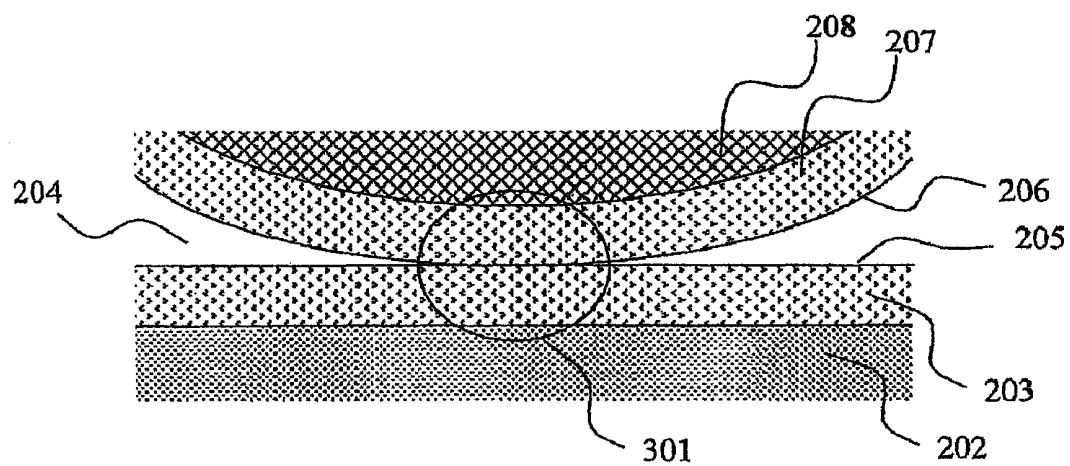


Fig. 2



(a)



(b)

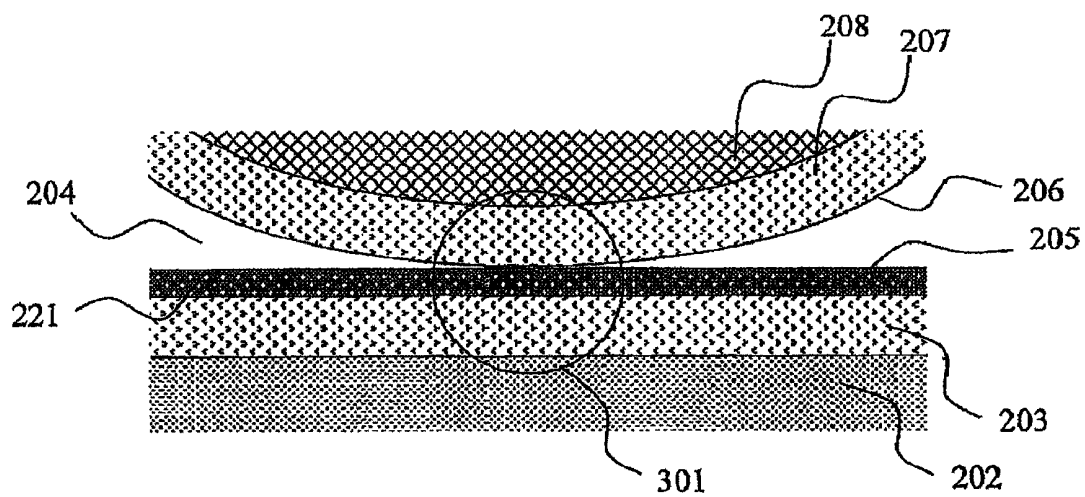


Fig. 4

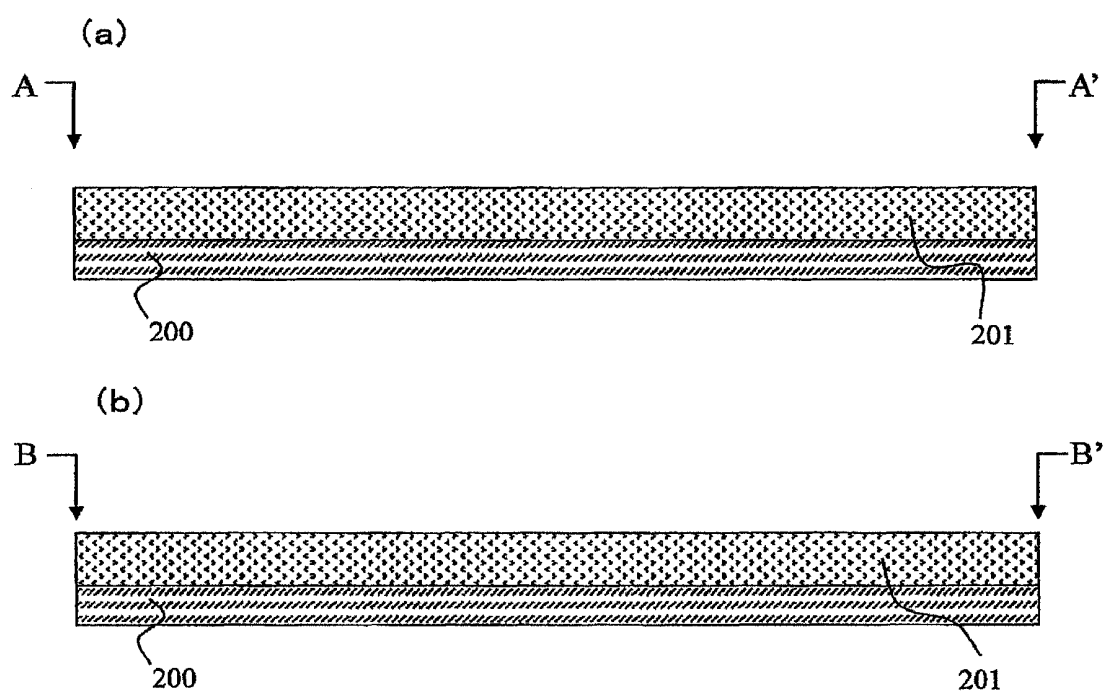


Fig. 5

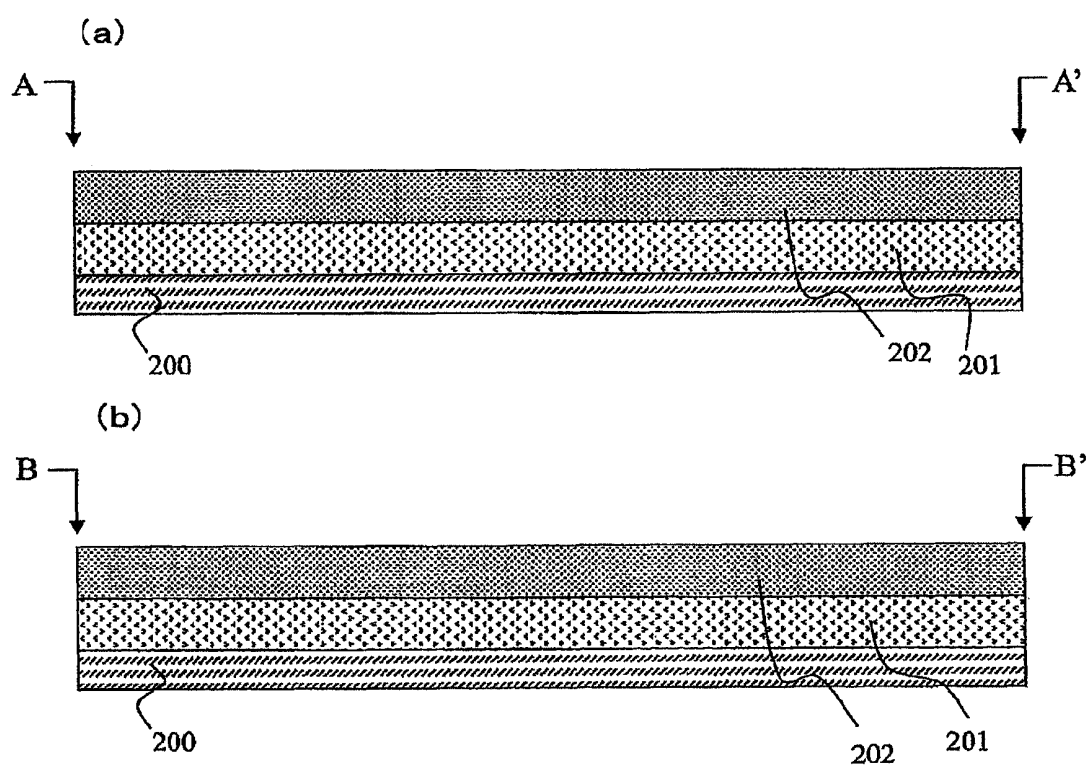


Fig. 6

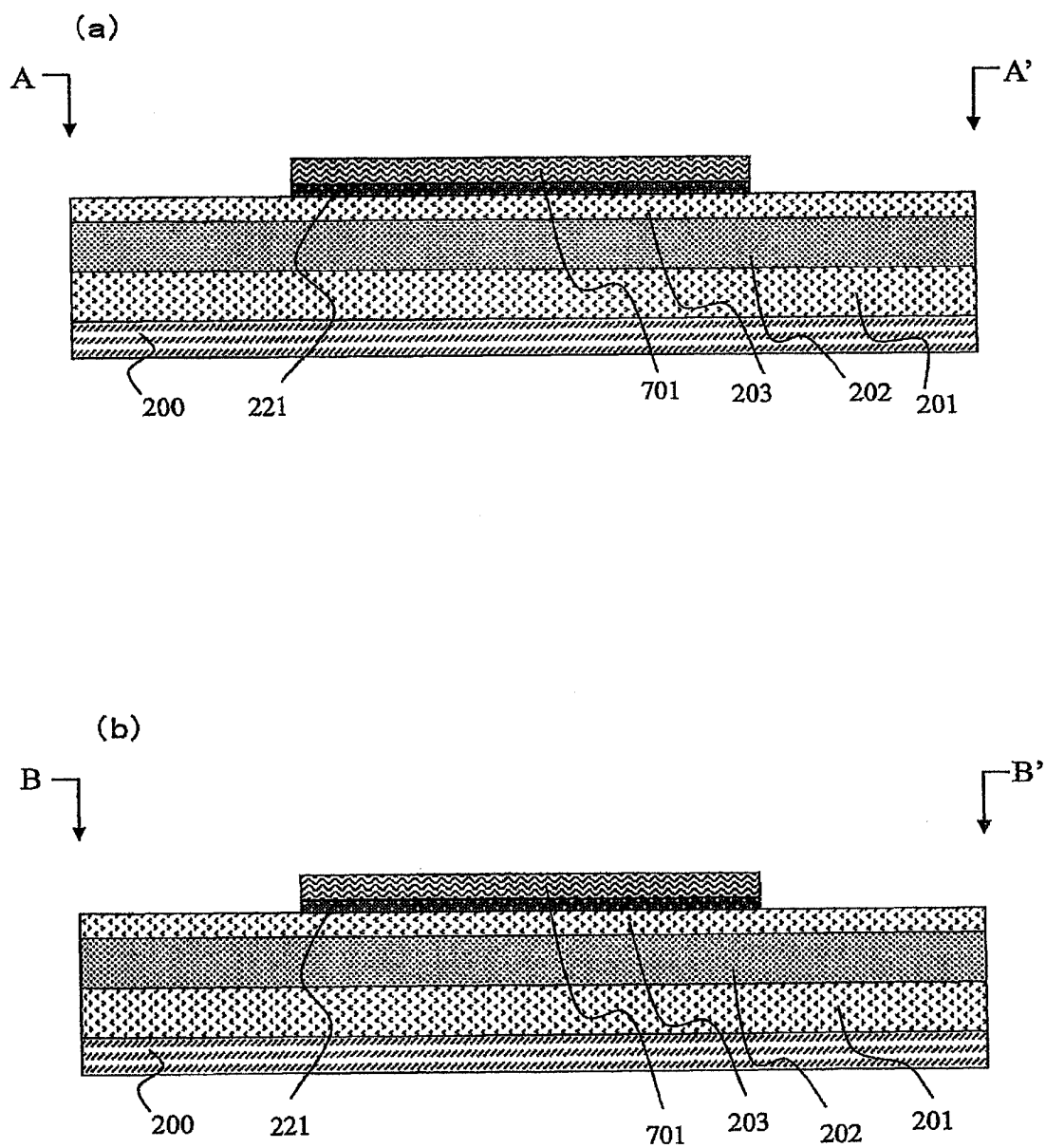


Fig. 7

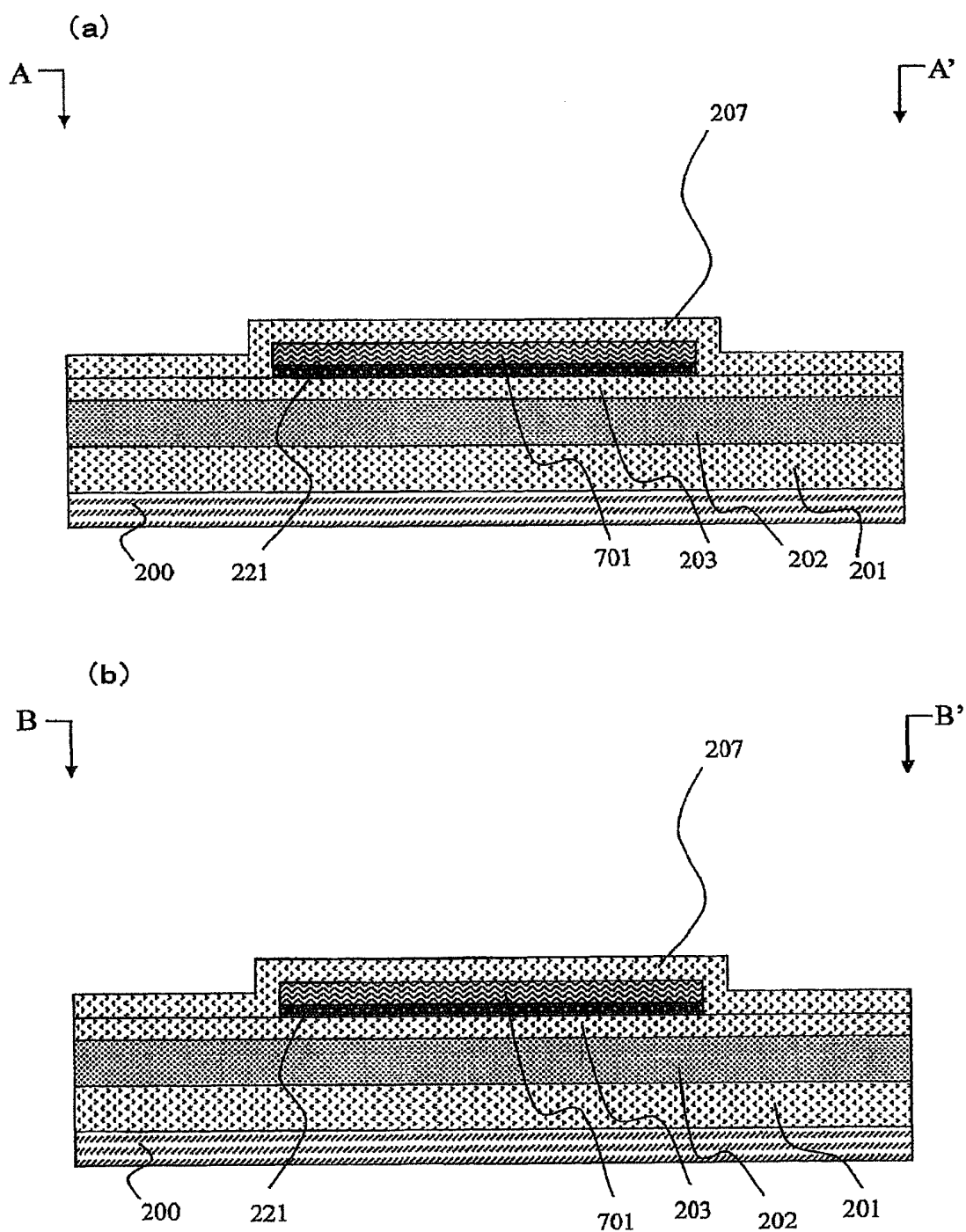


Fig. 8

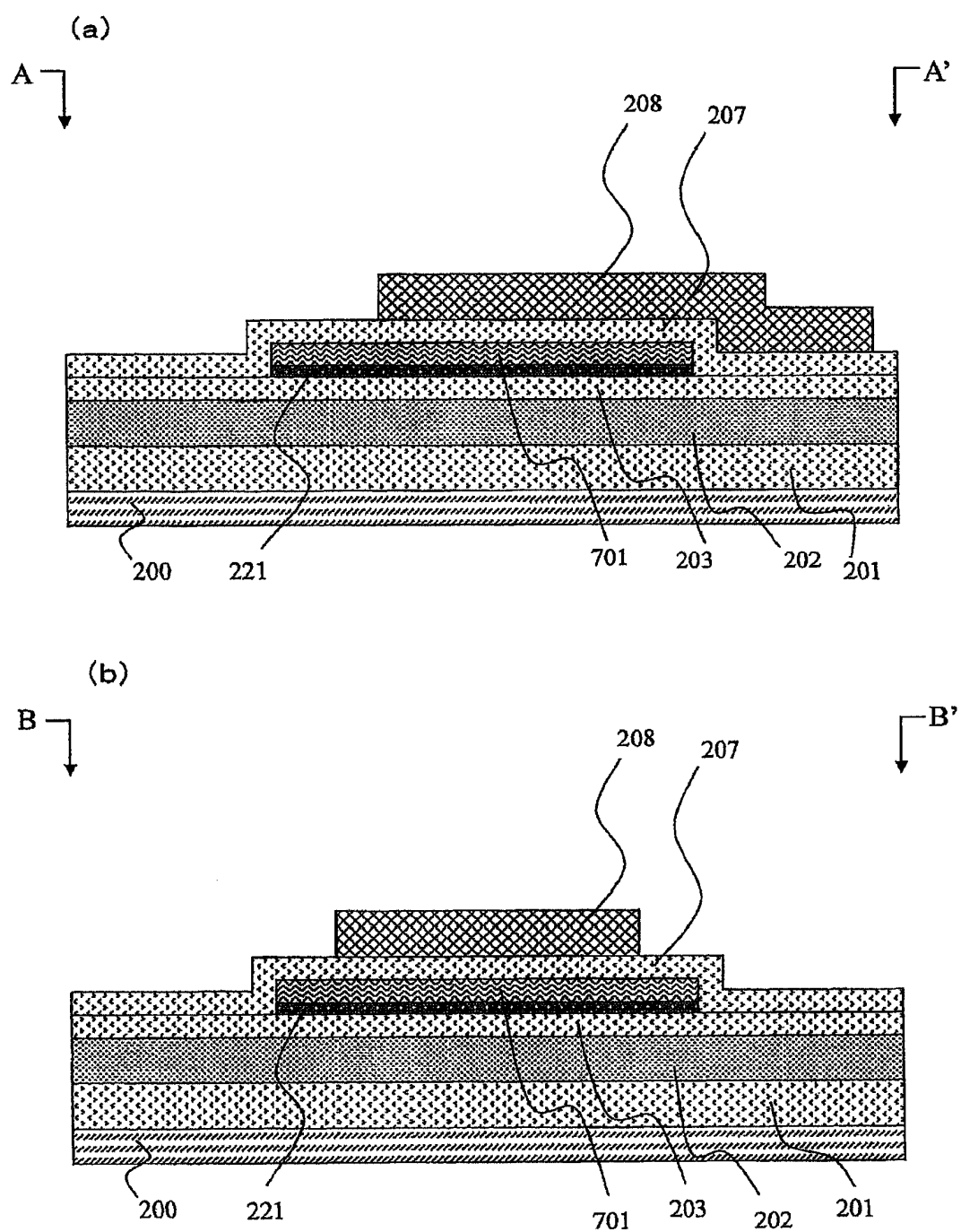


Fig. 9

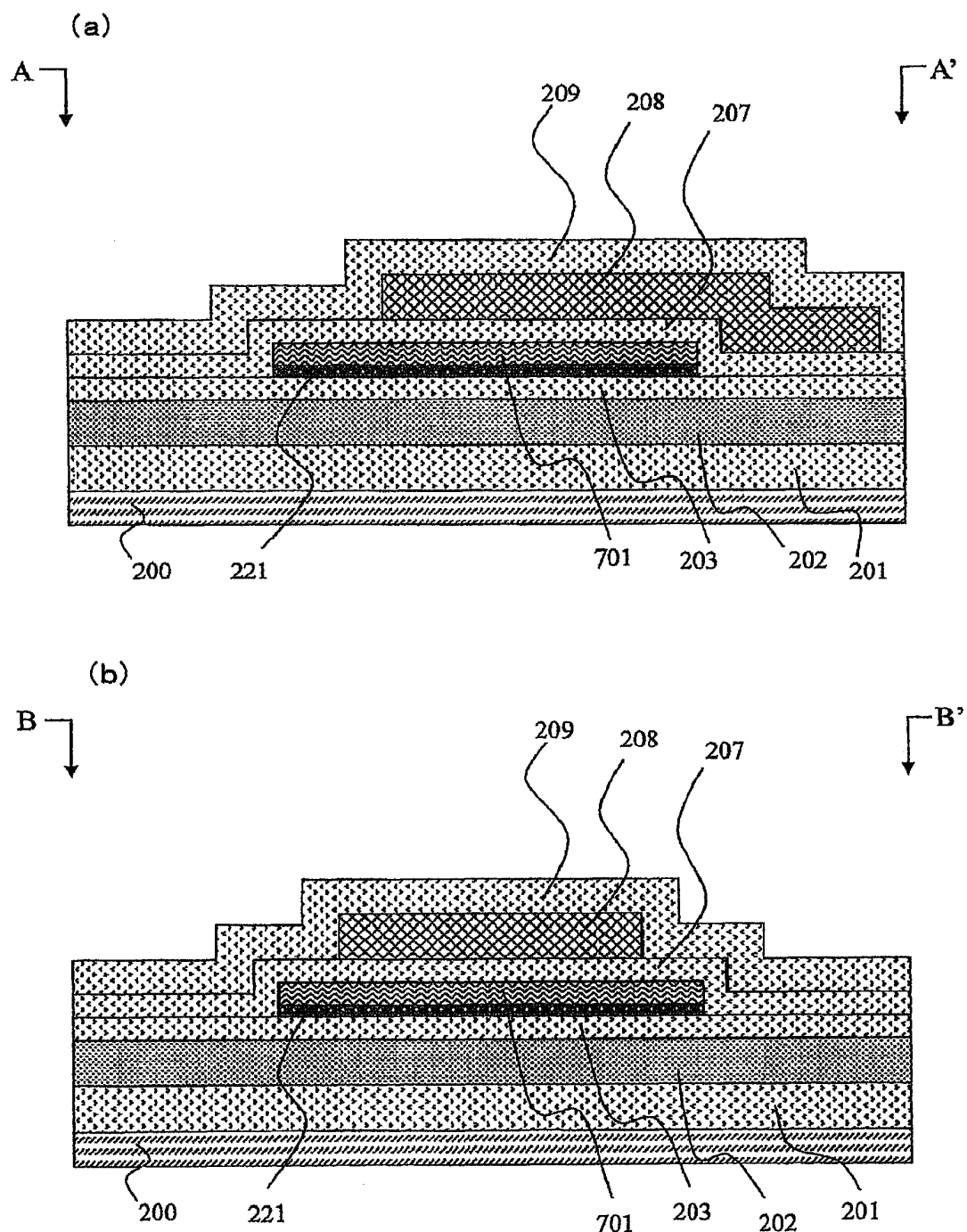


Fig. 10

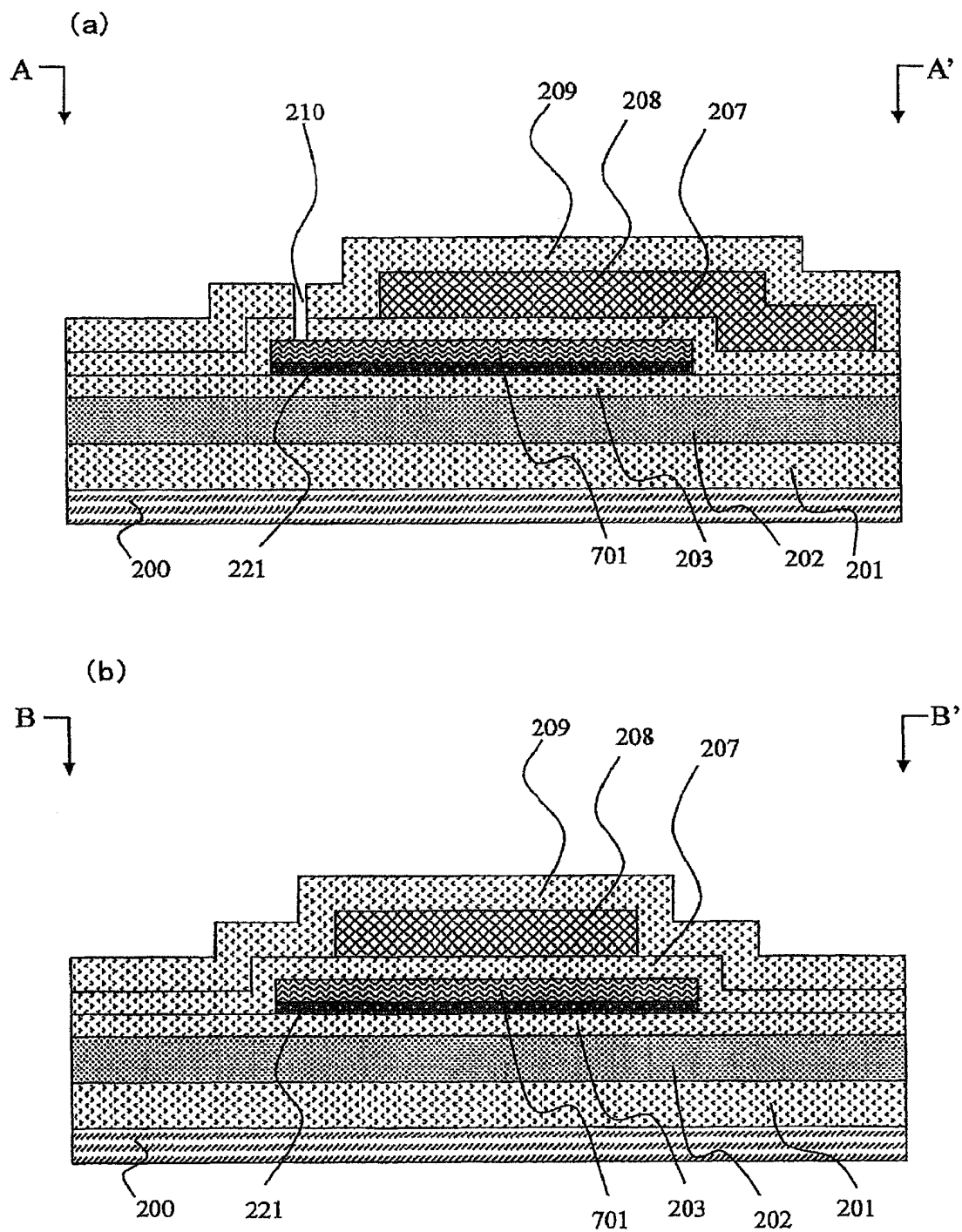
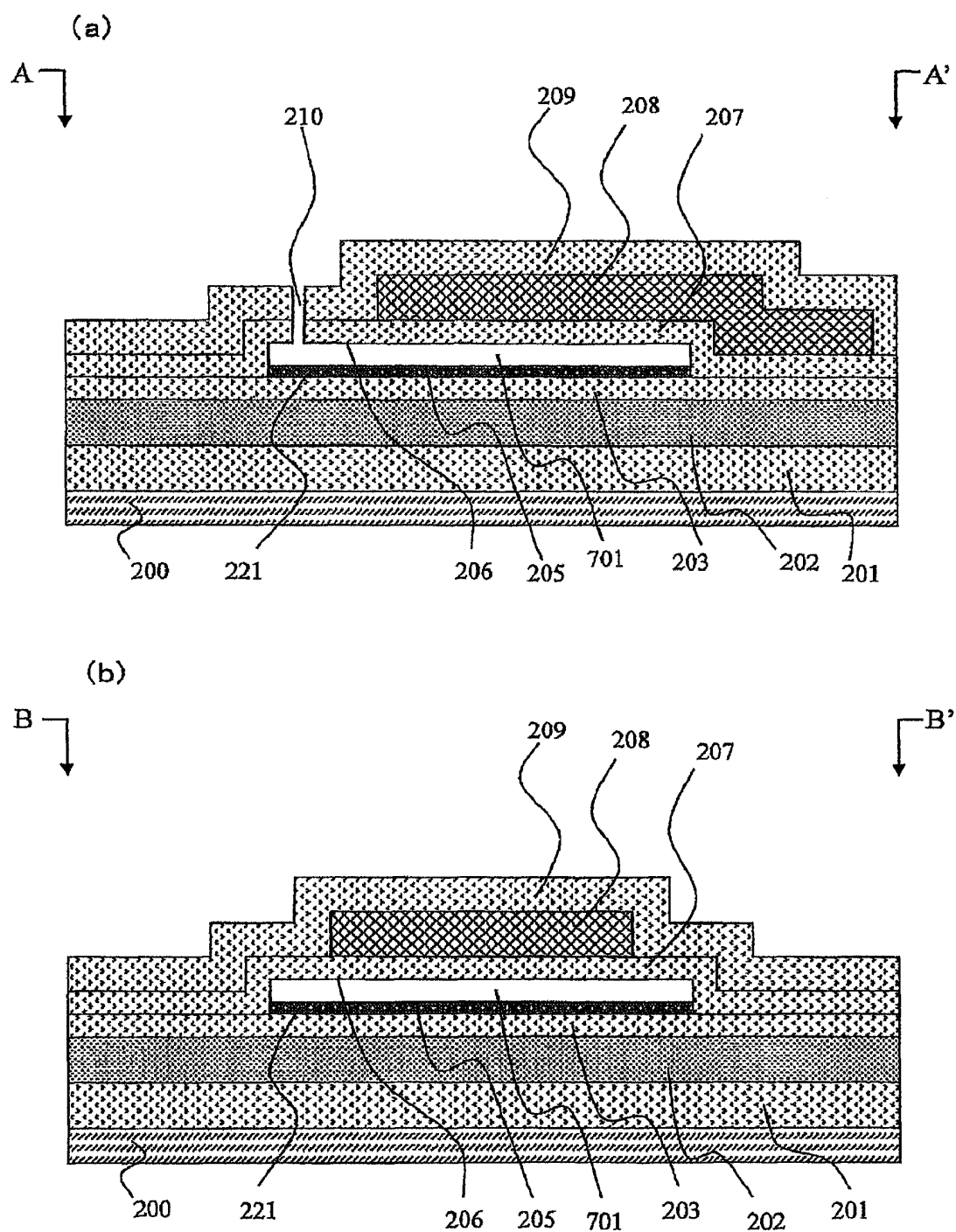


Fig. 11



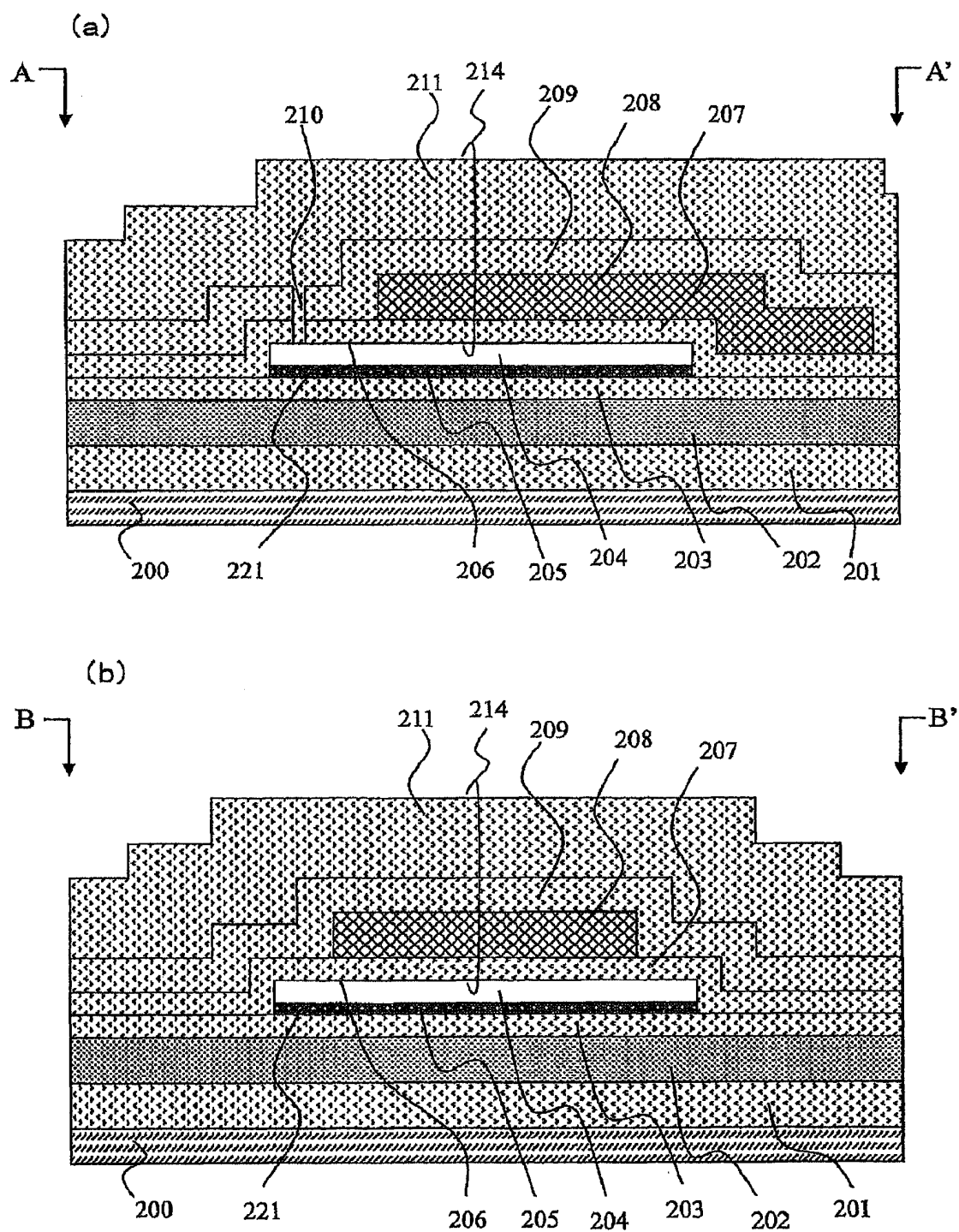
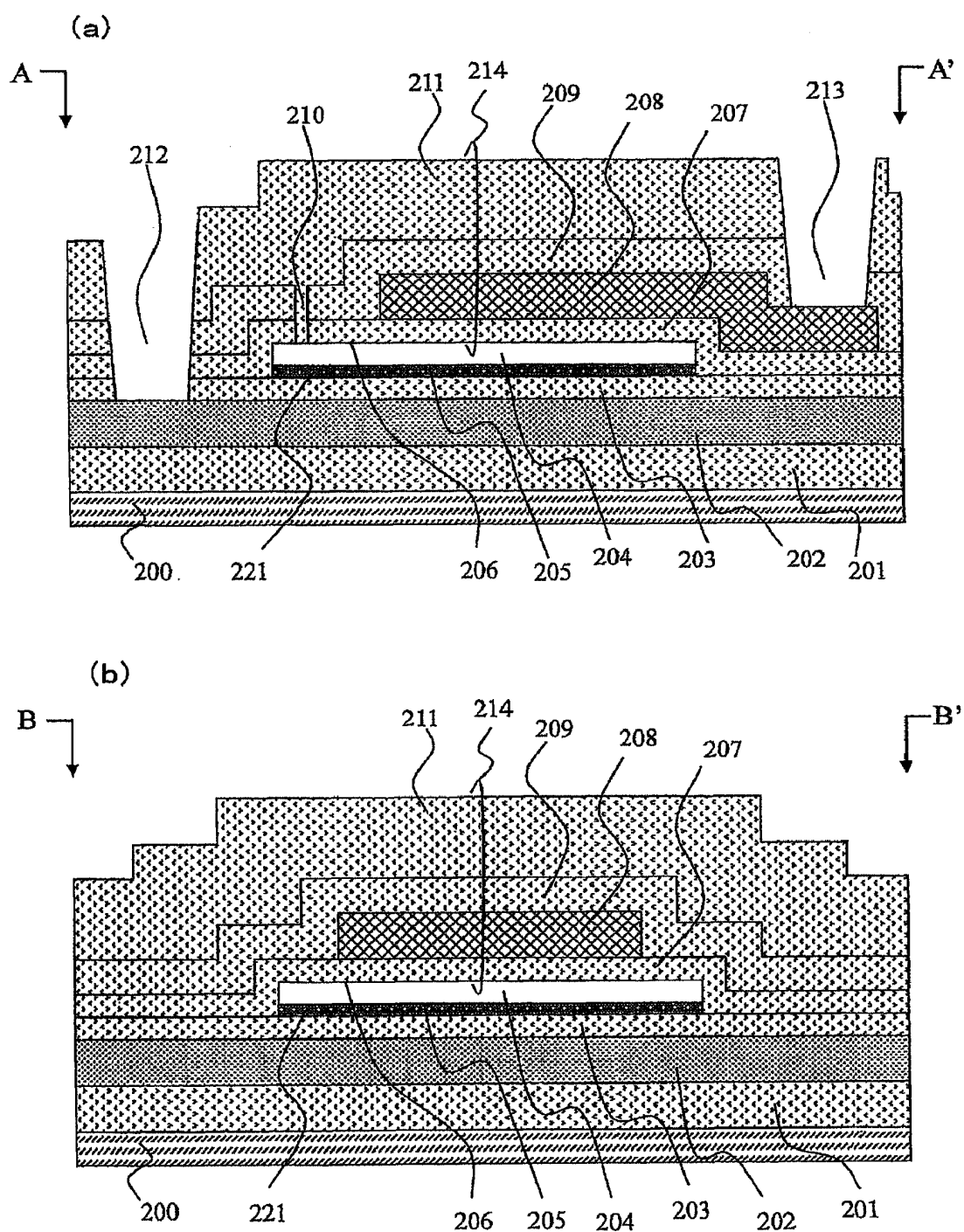


Fig. 13



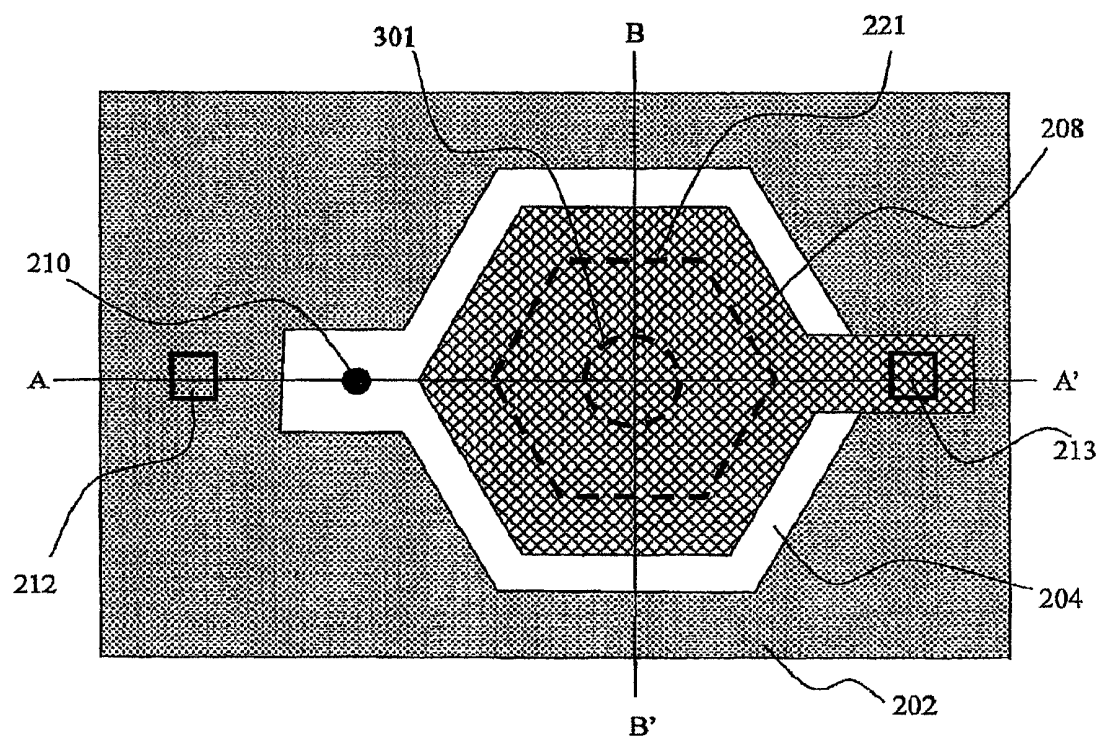


Fig. 15

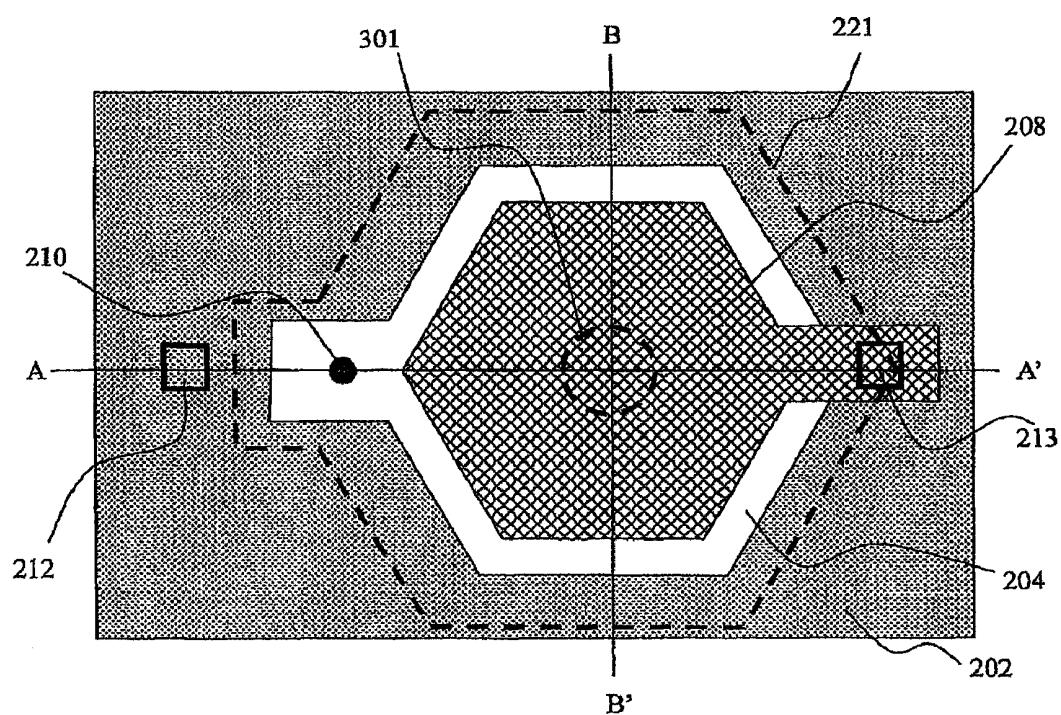


Fig. 16

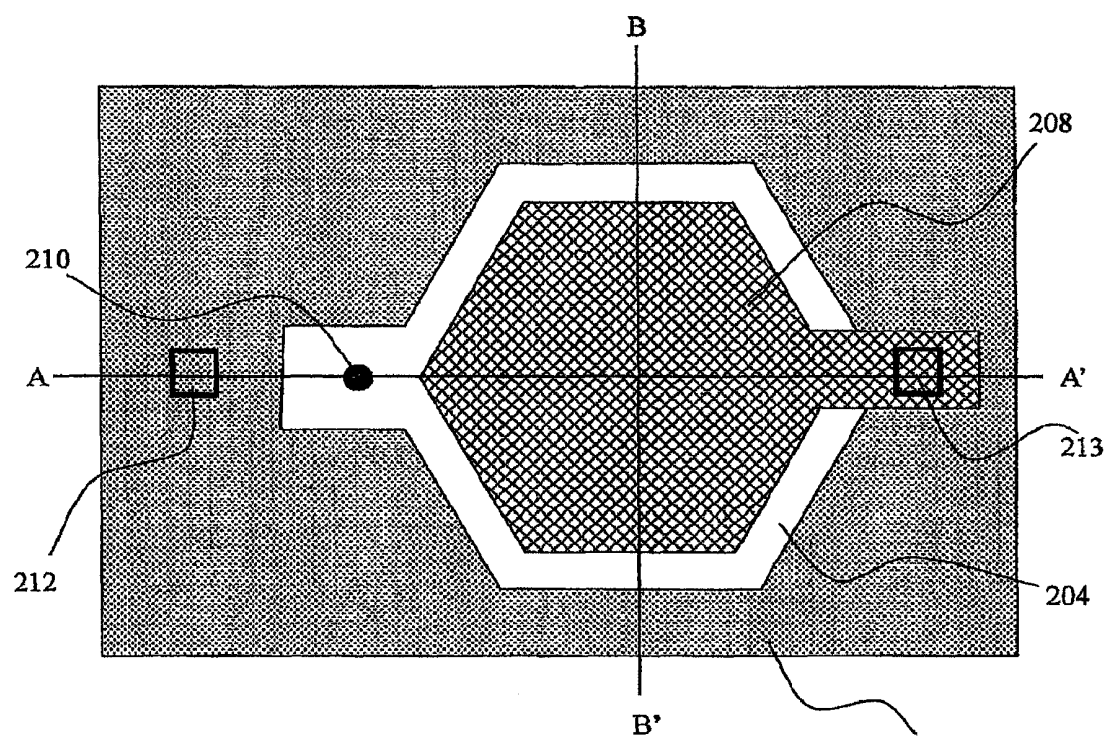


Fig. 17

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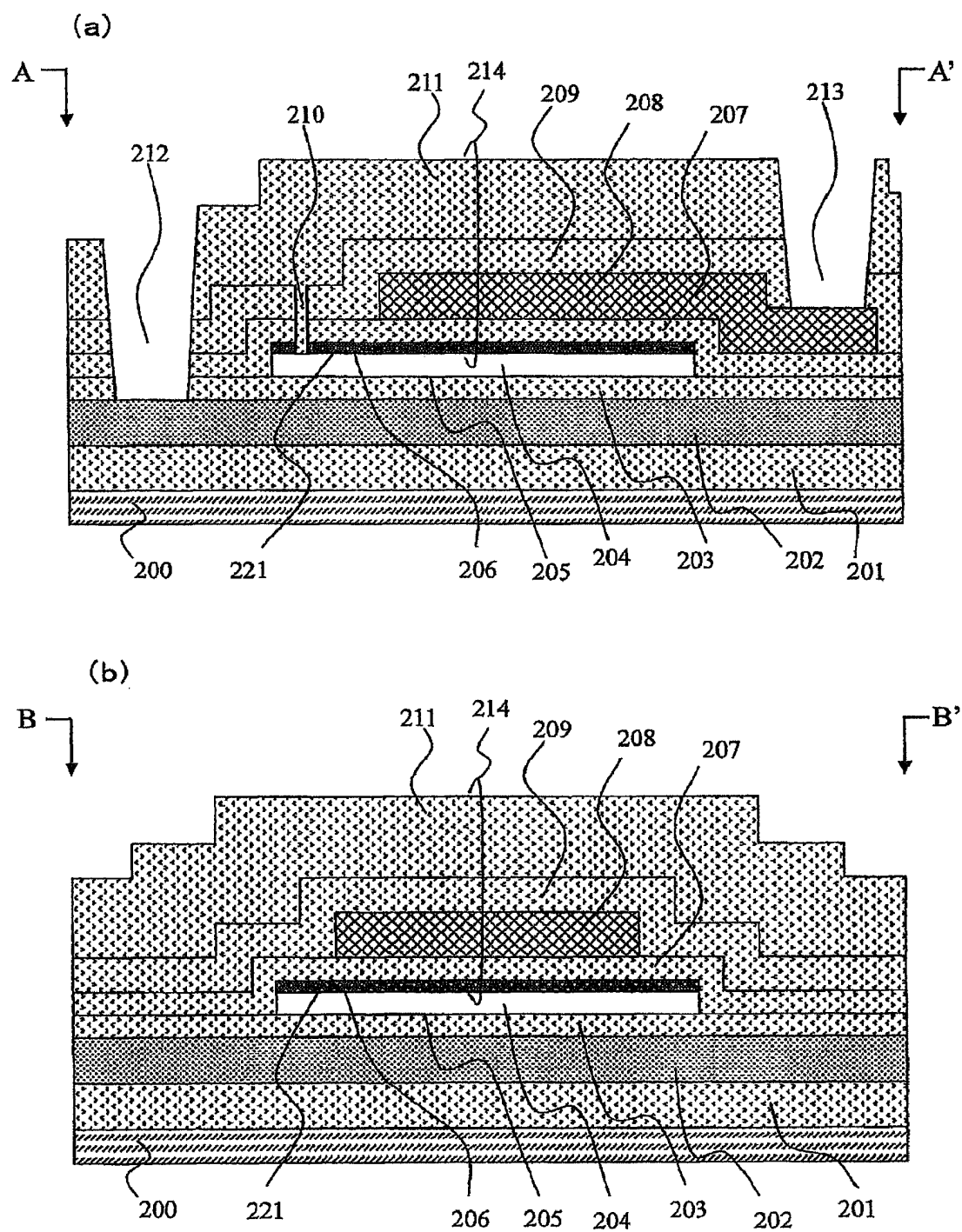
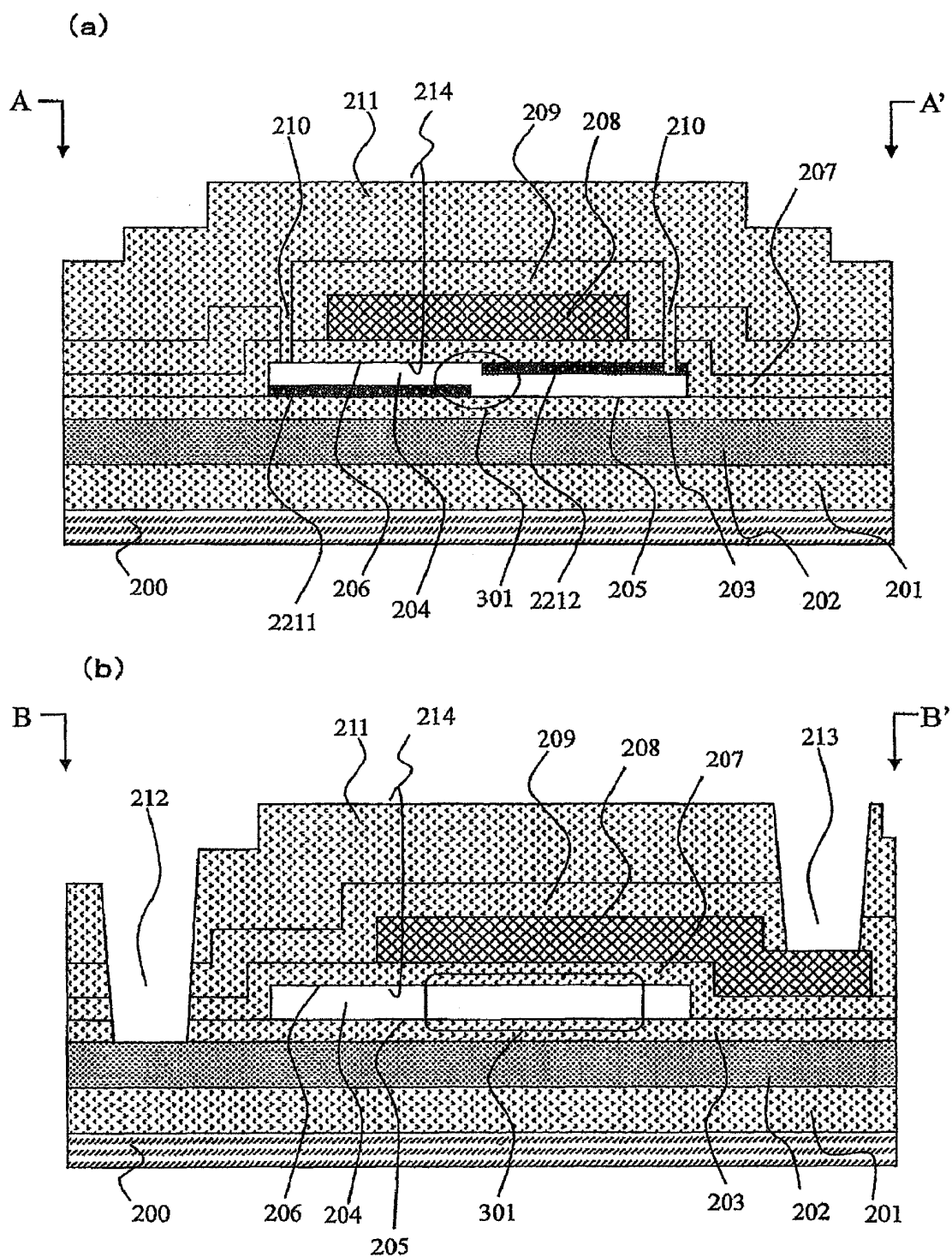


Fig. 18

Fig. 19



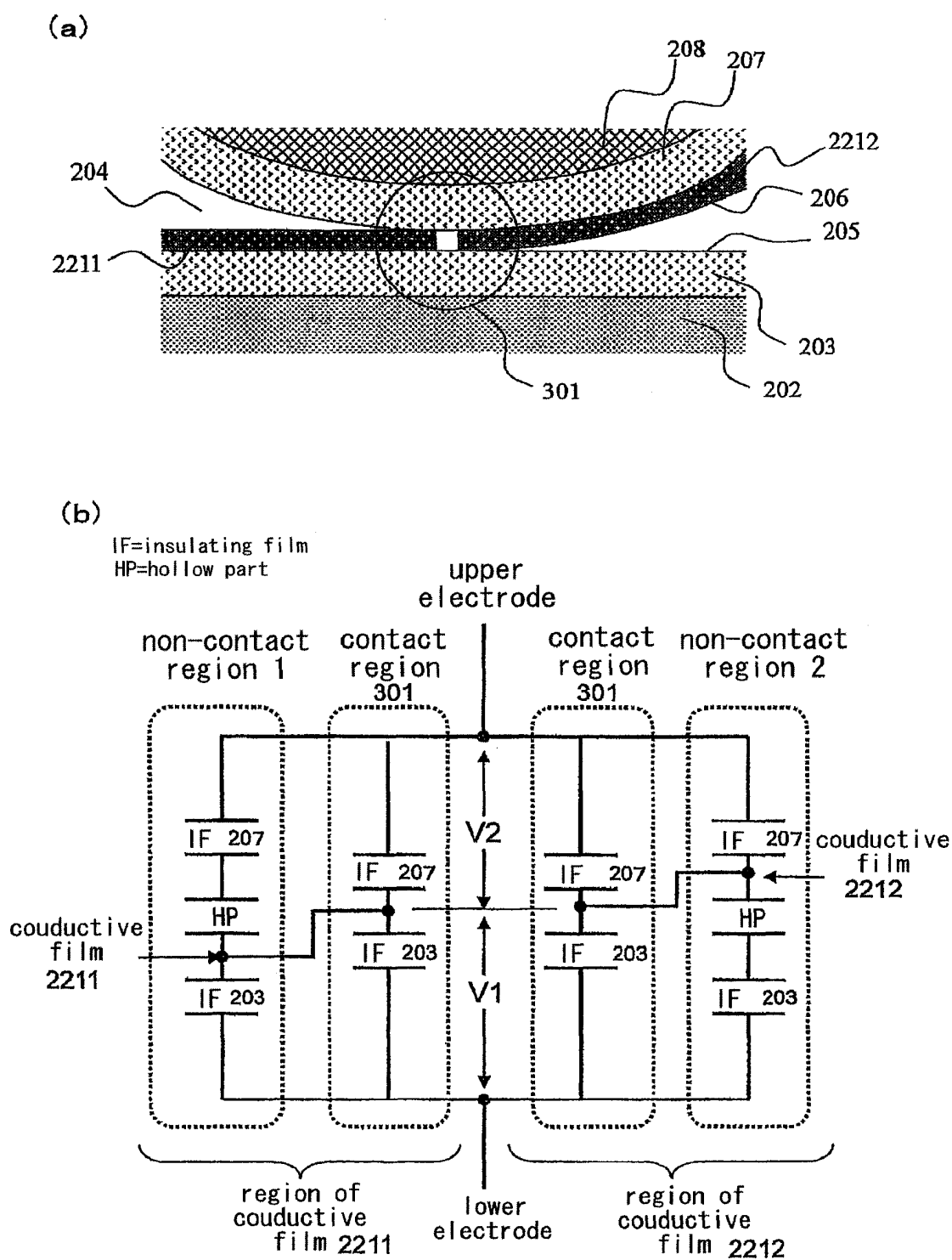


Fig. 21

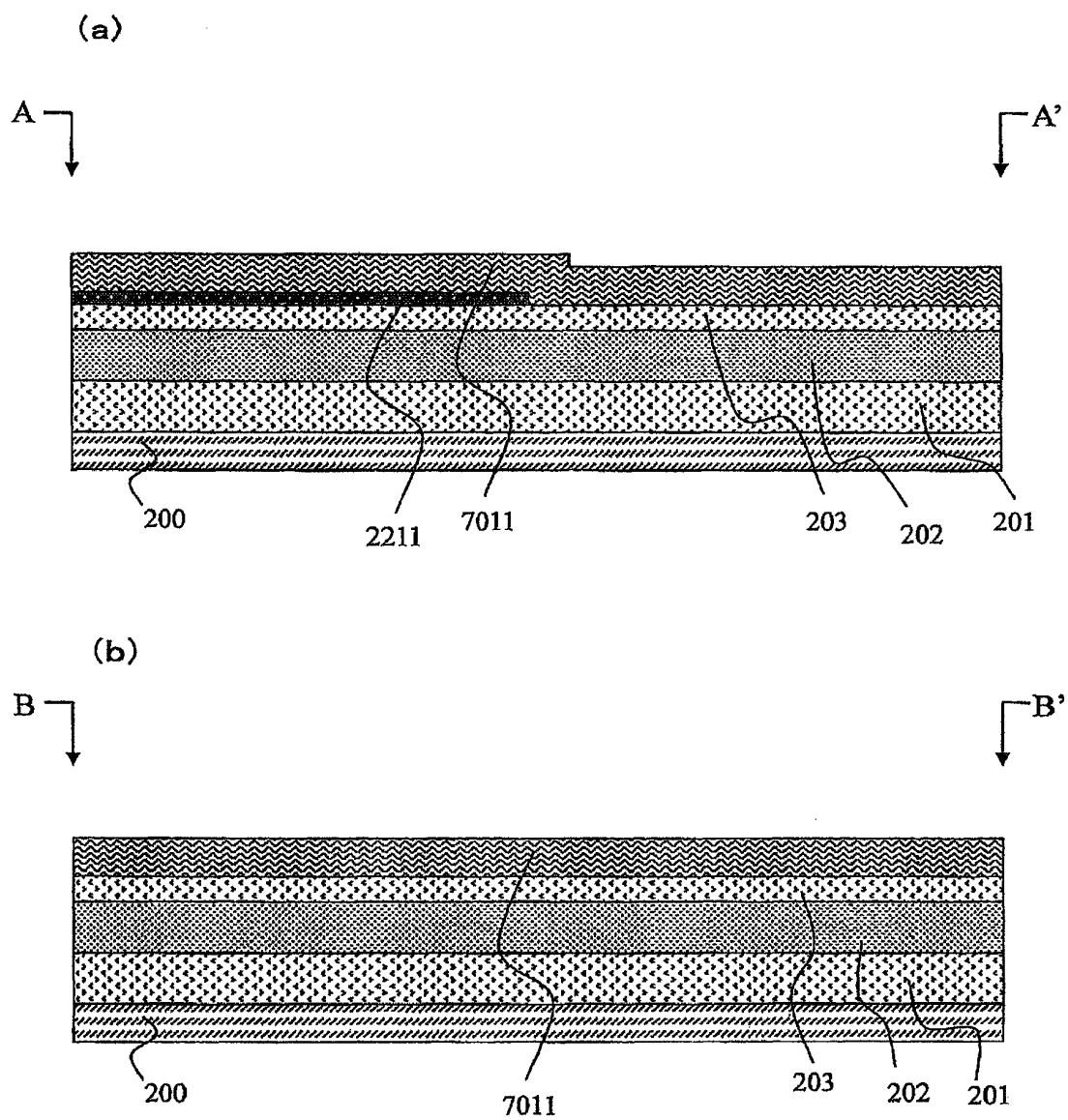


Fig. 22

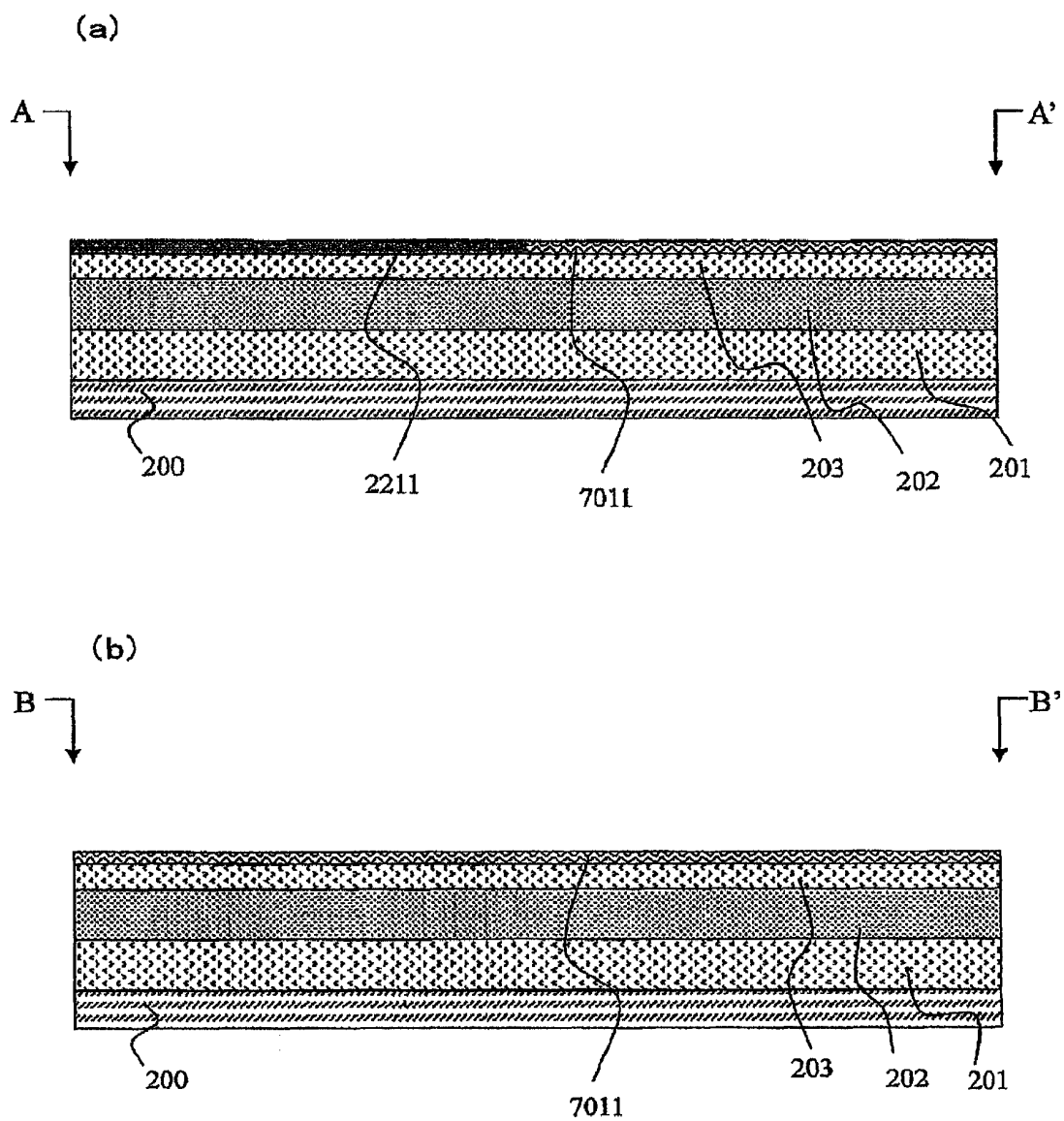


Fig. 23

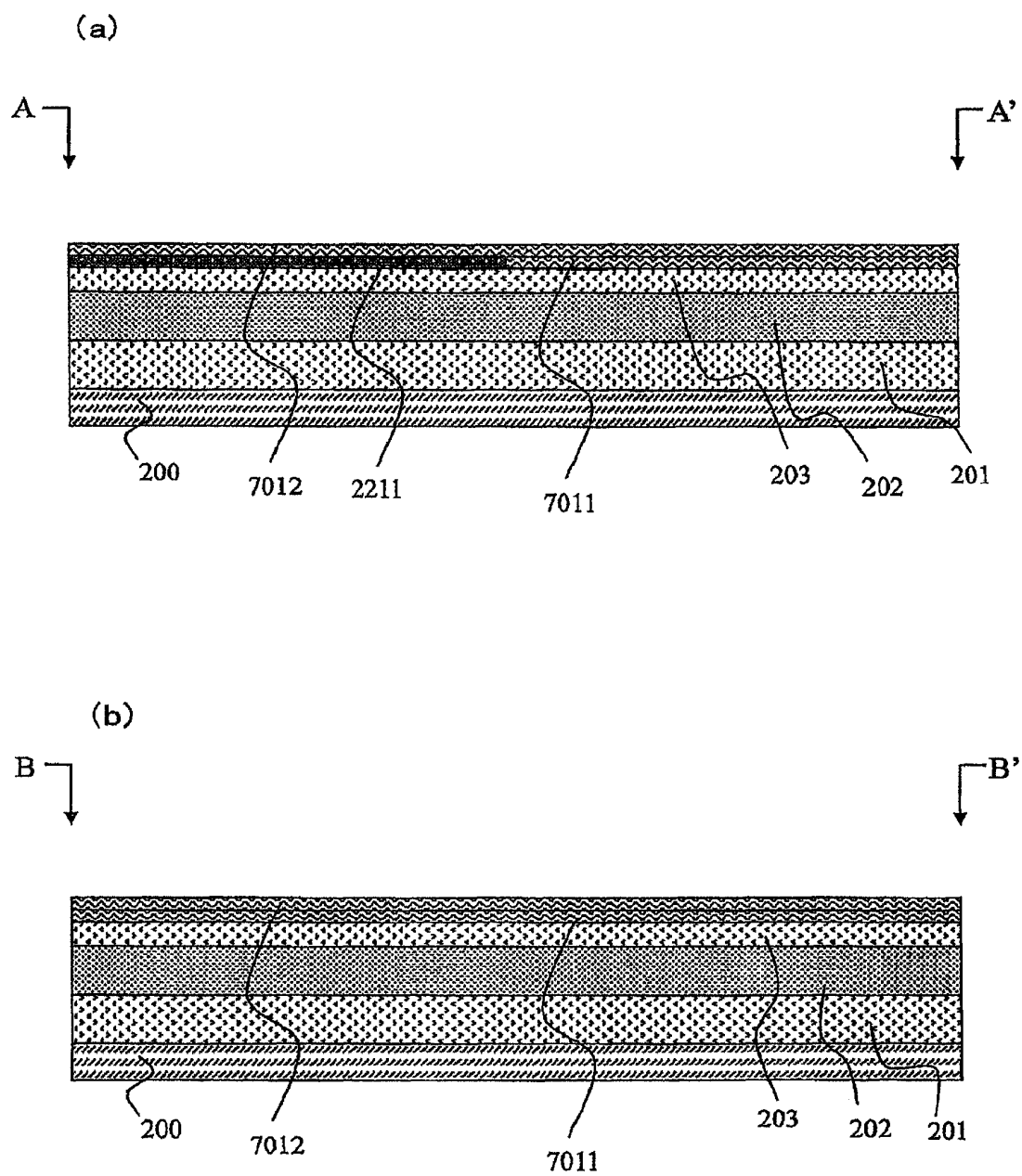


Fig. 24

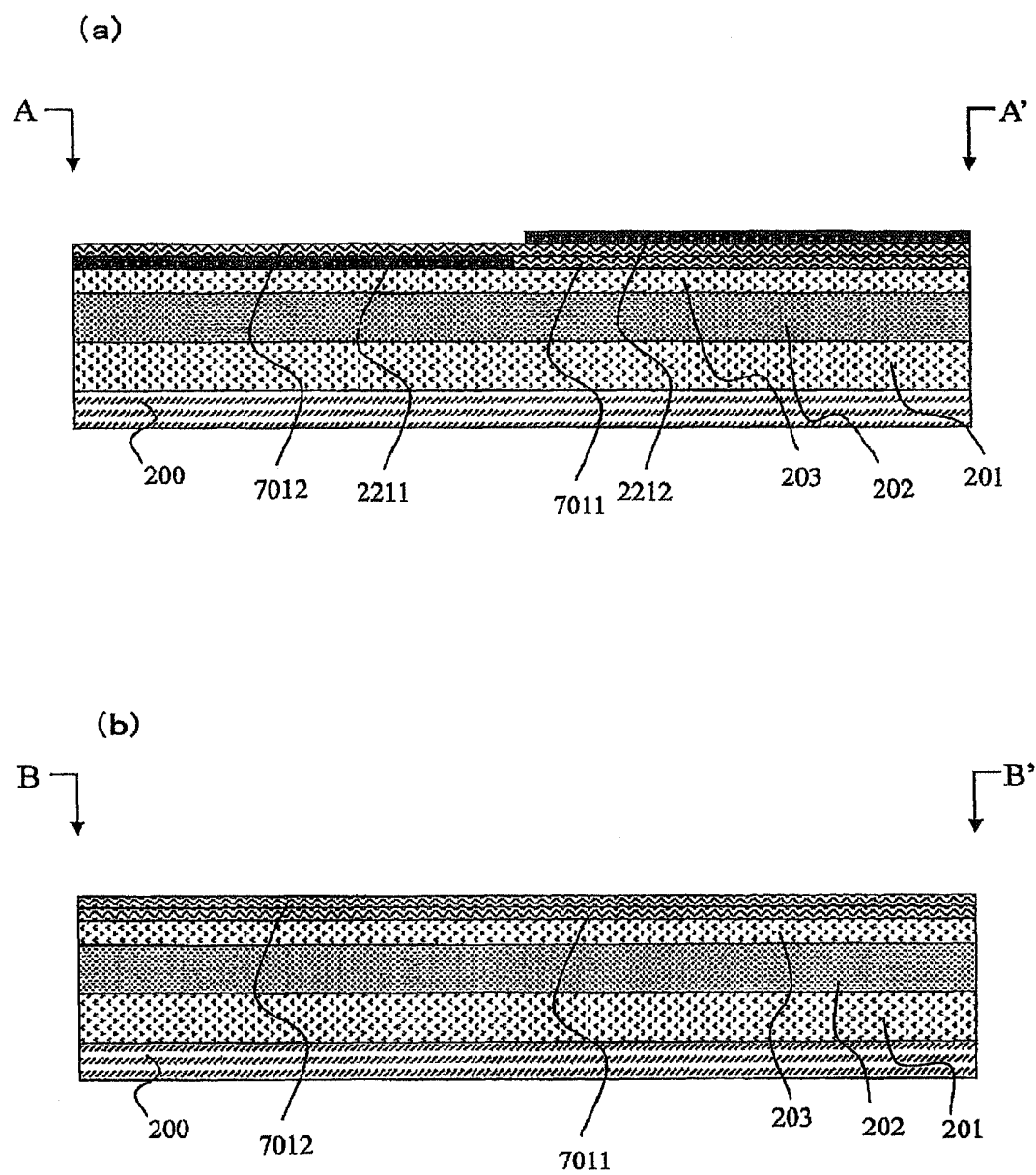


Fig. 25

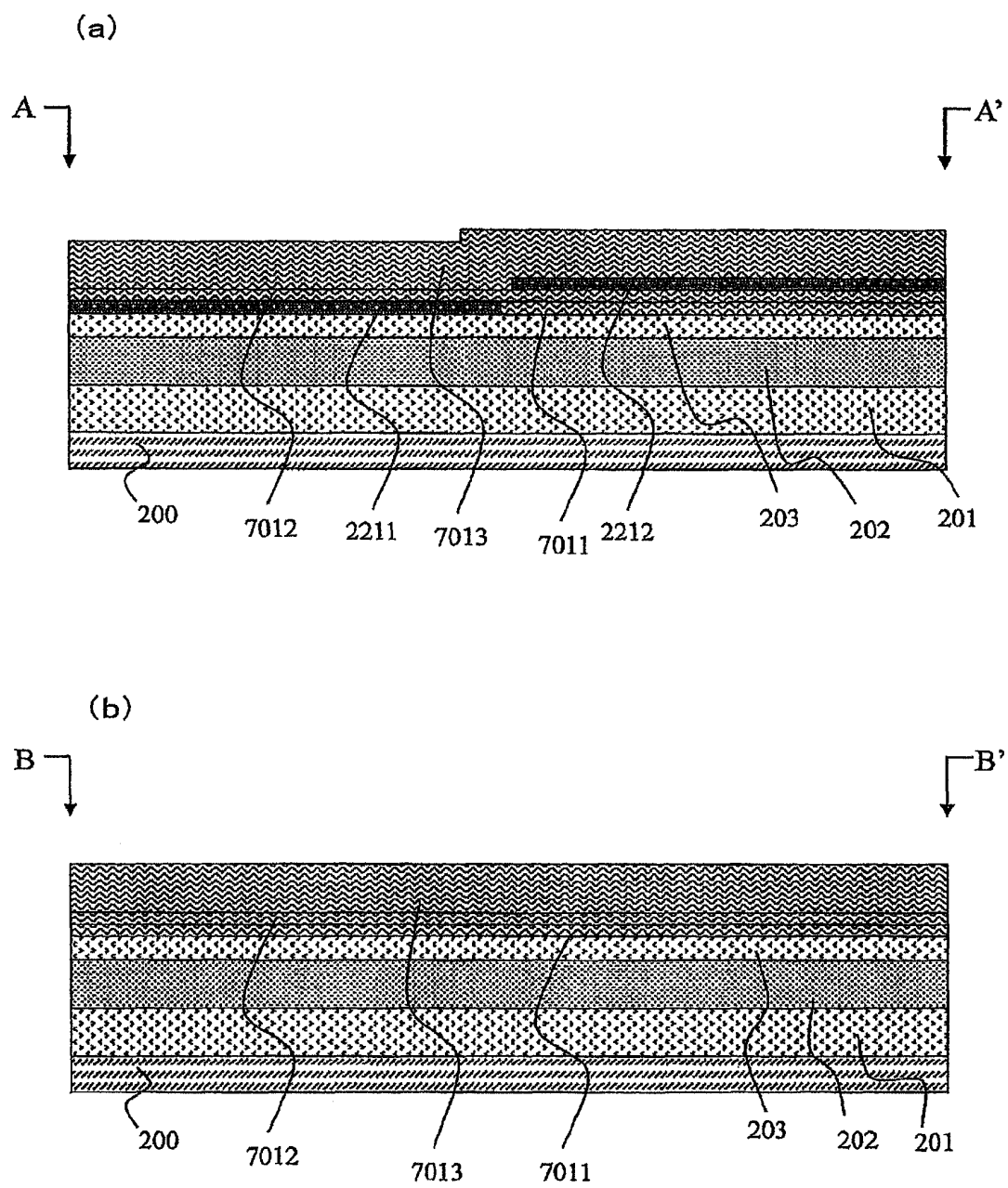


Fig. 26

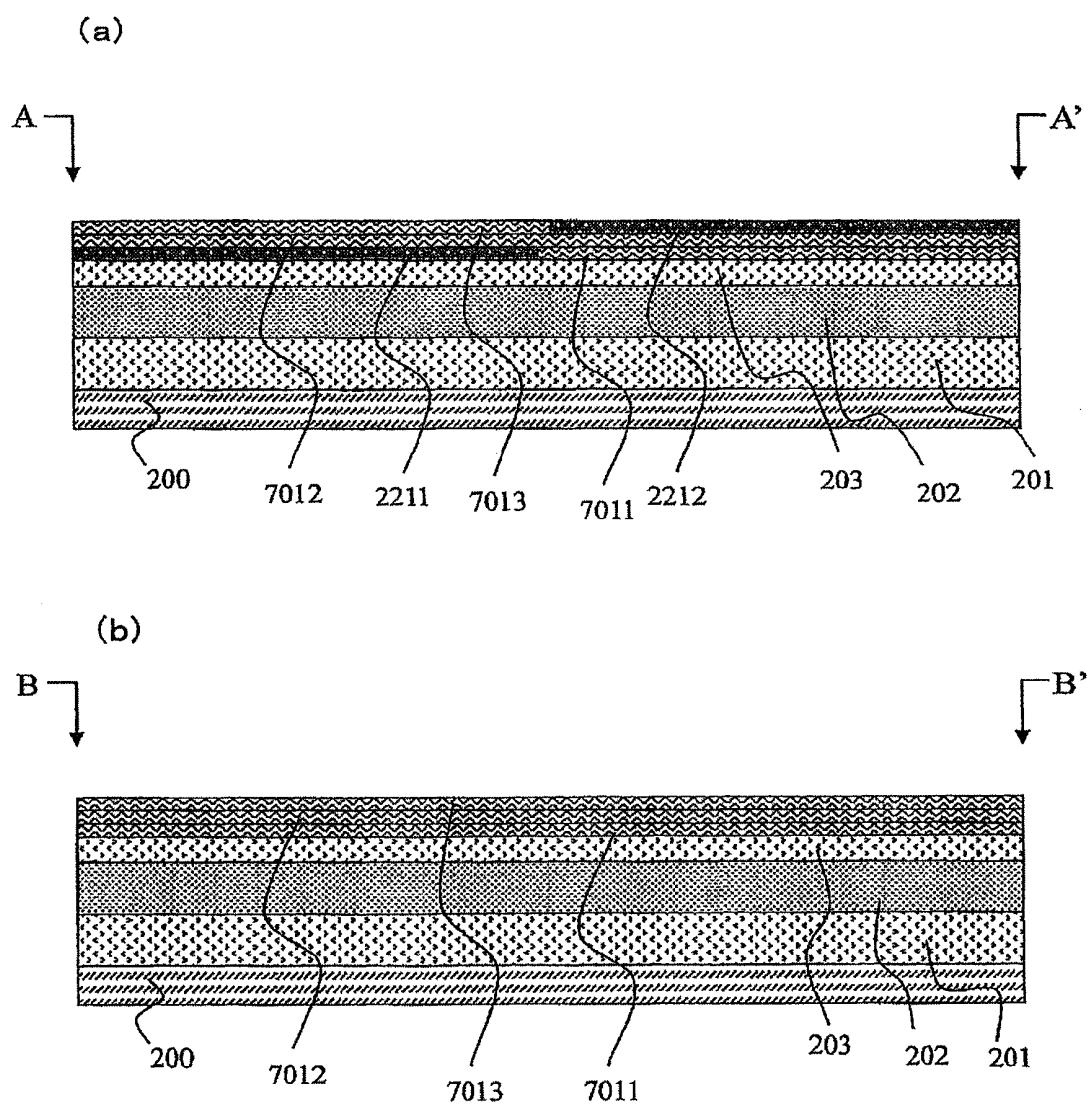


Fig. 27

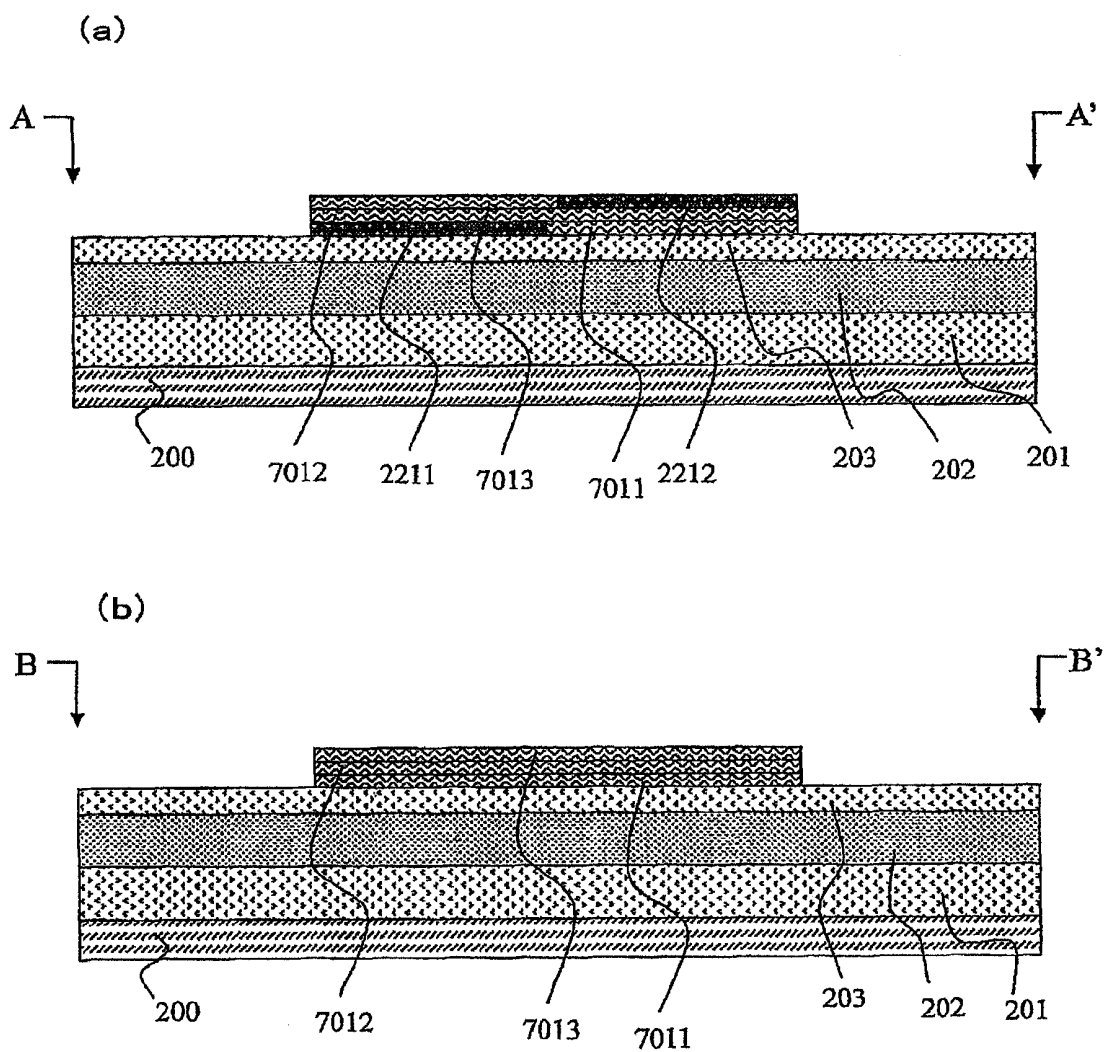


Fig. 28

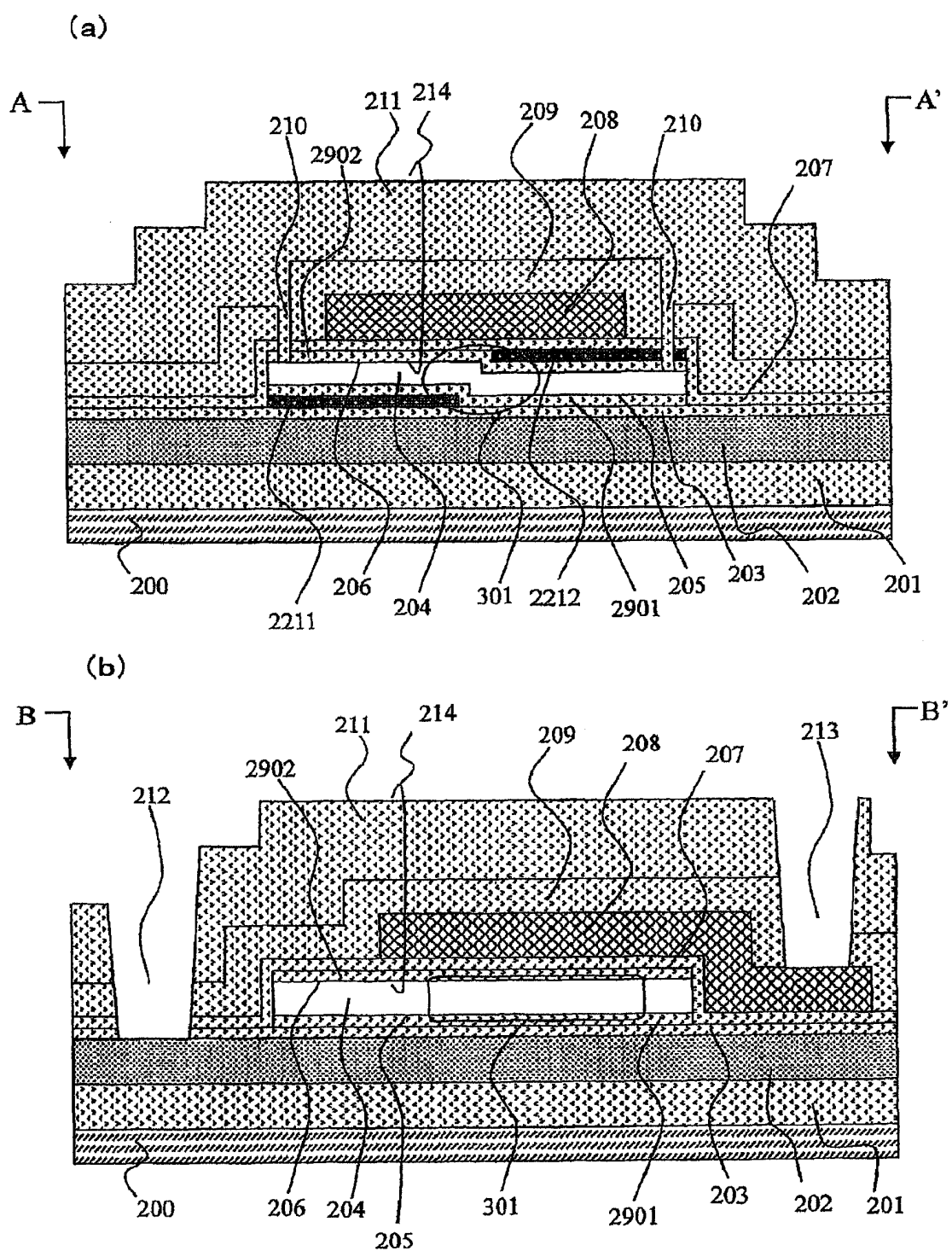


Fig. 29

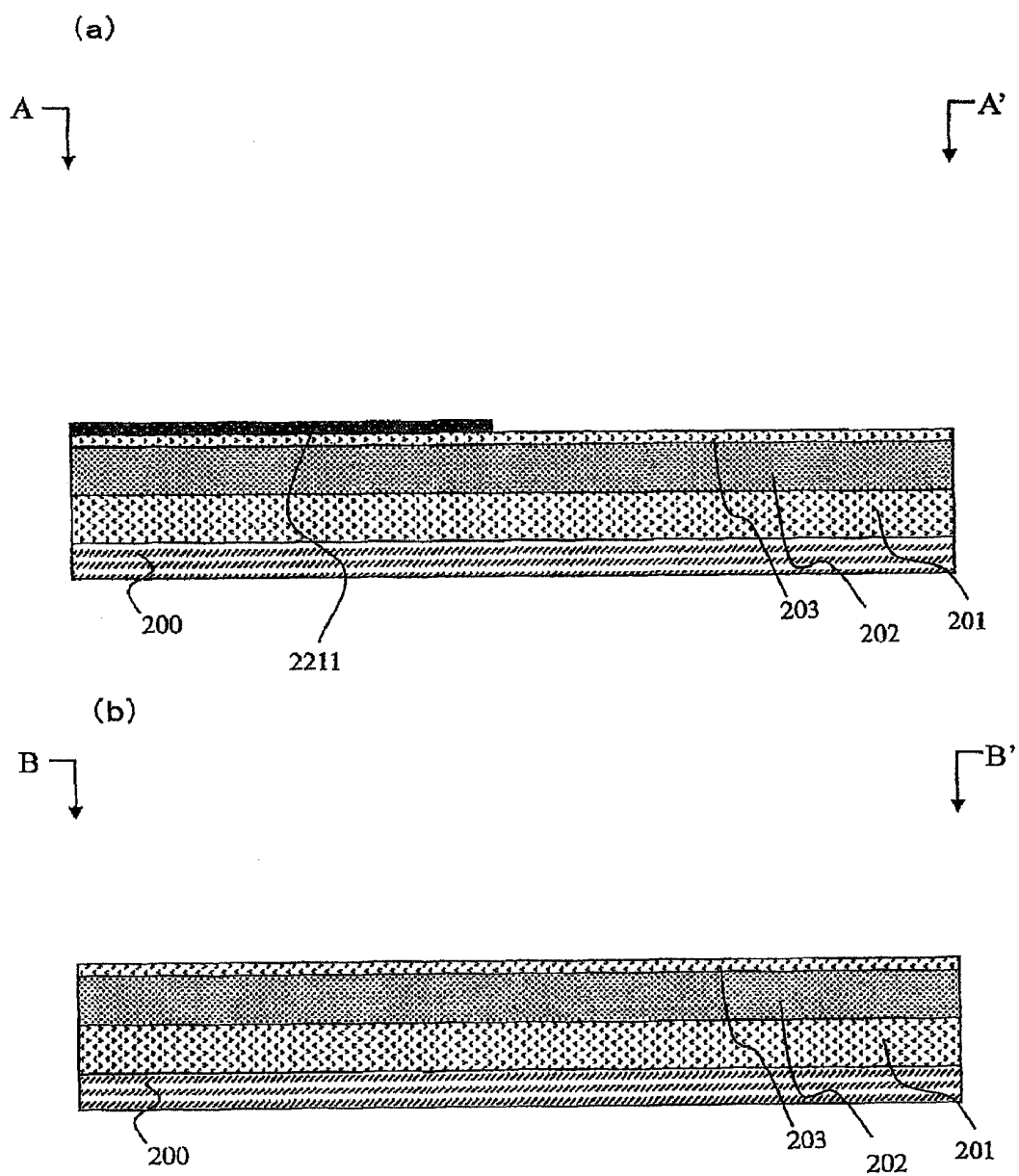


Fig. 30

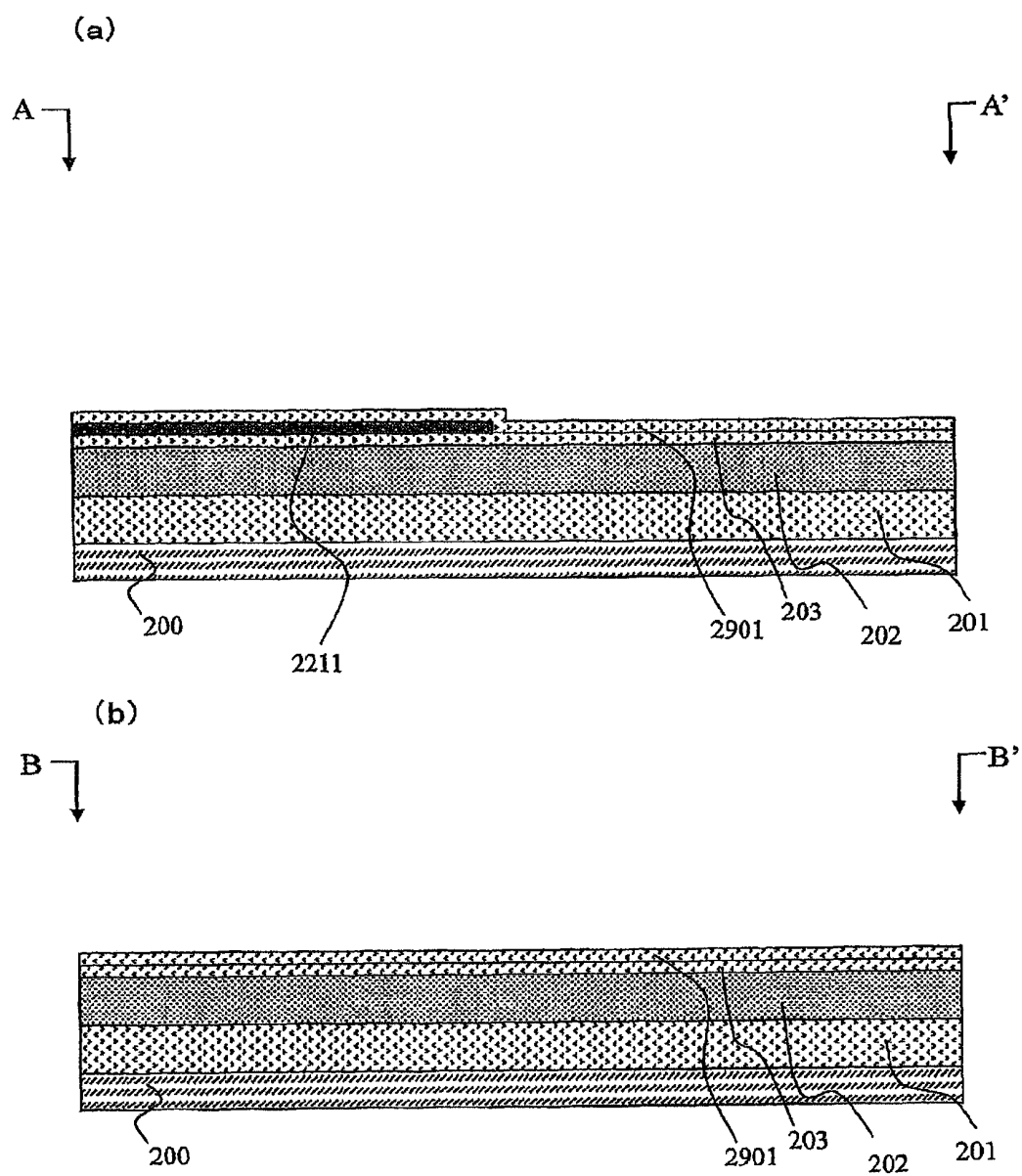


Fig. 31

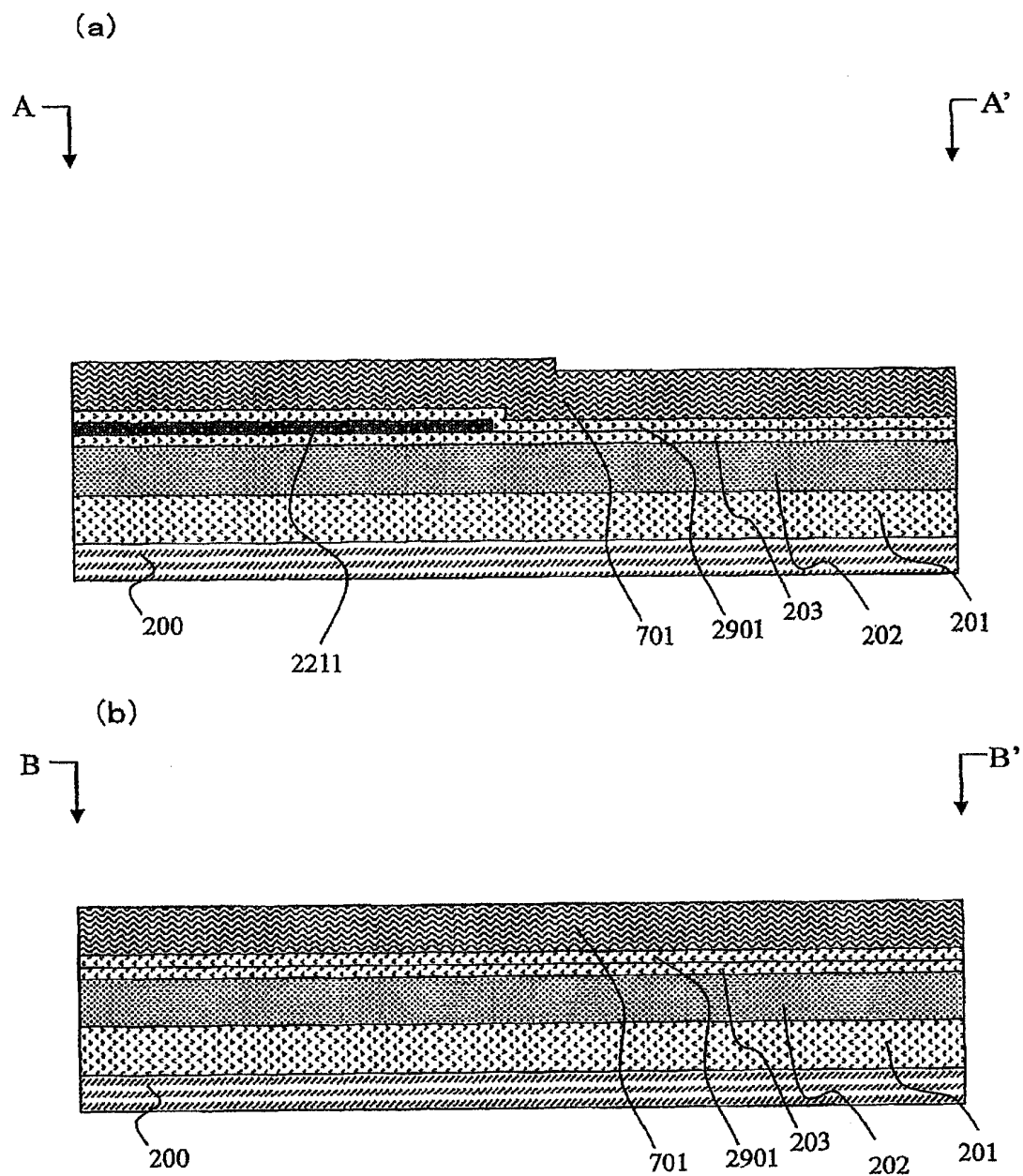


Fig. 32

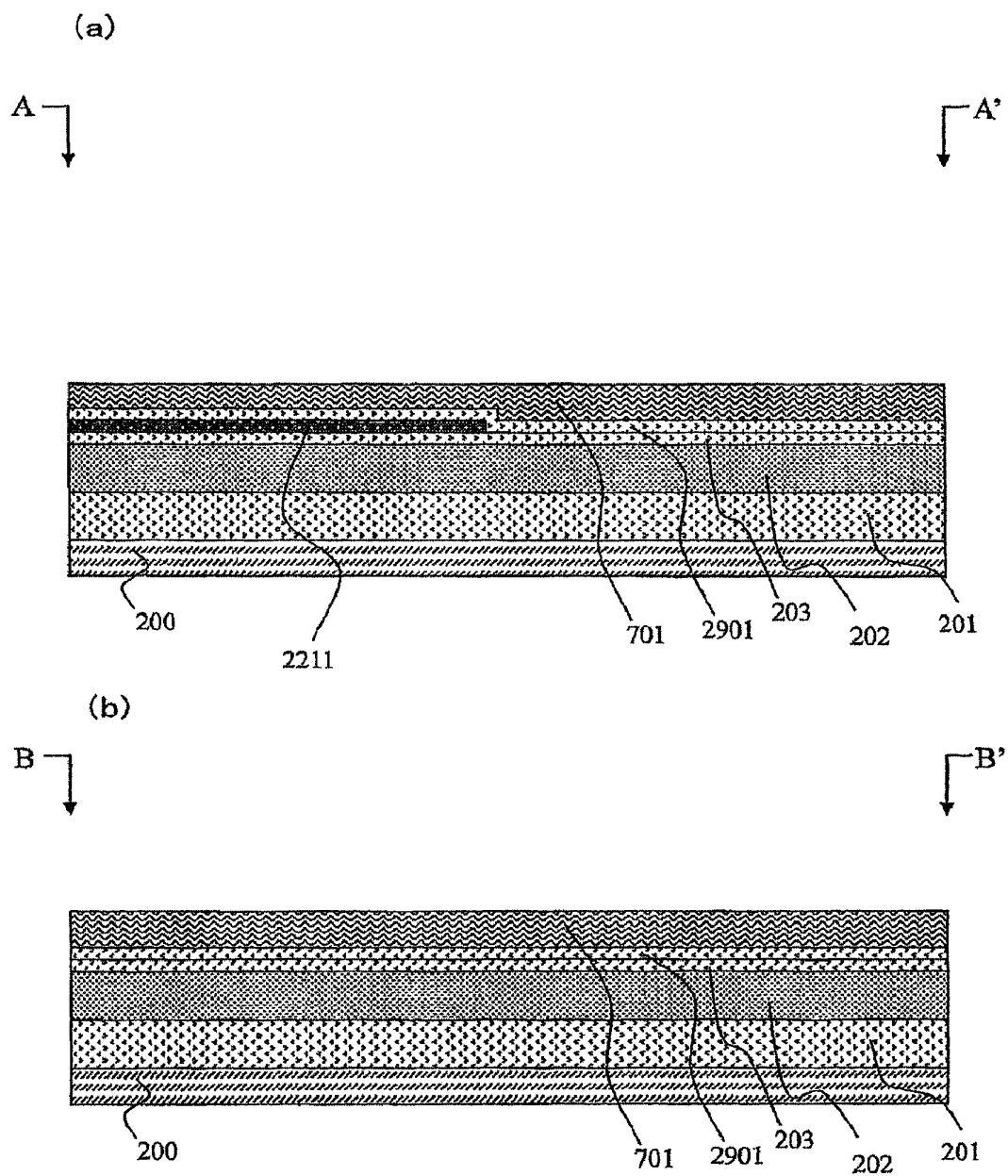


Fig. 33

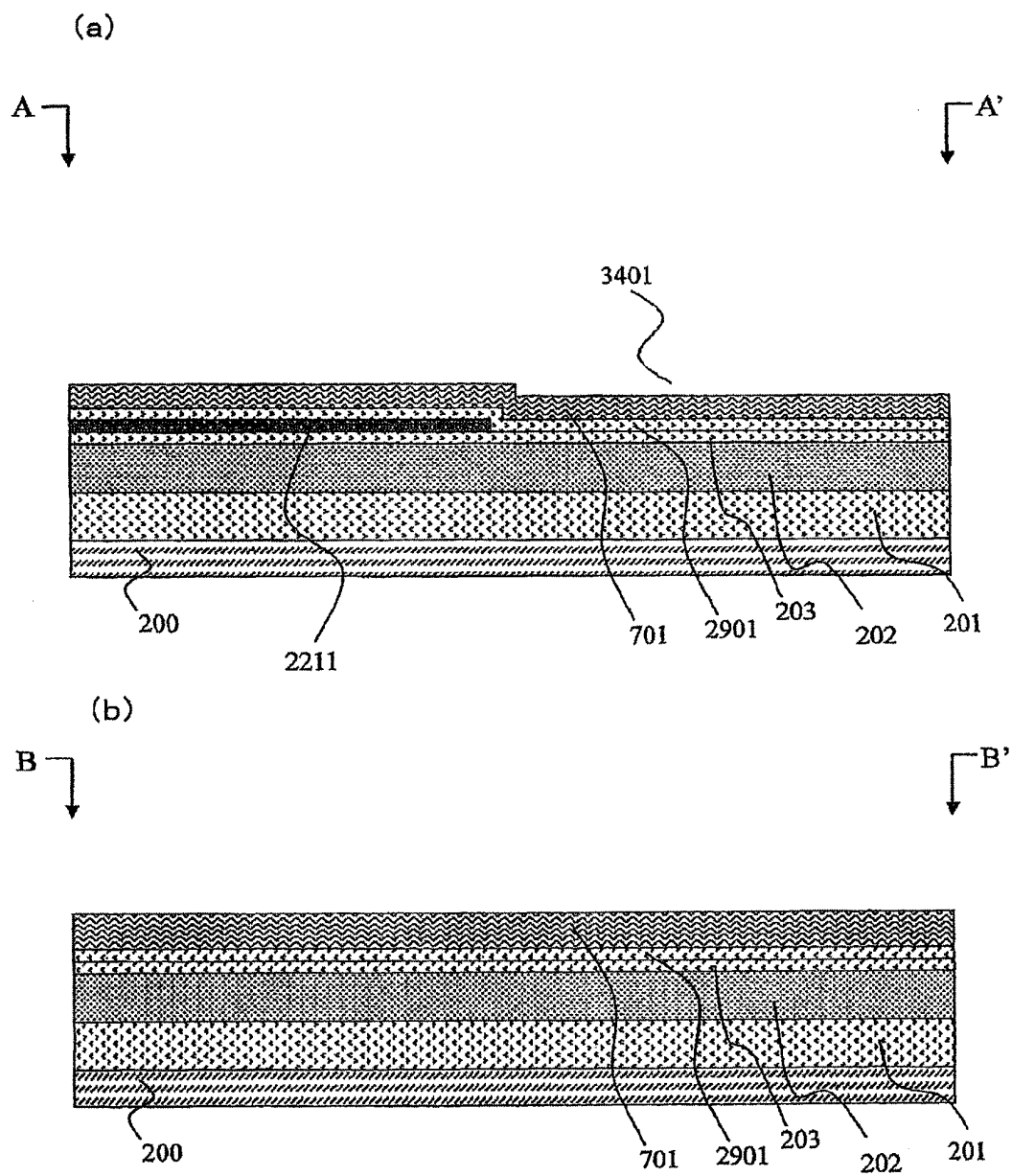


Fig. 34

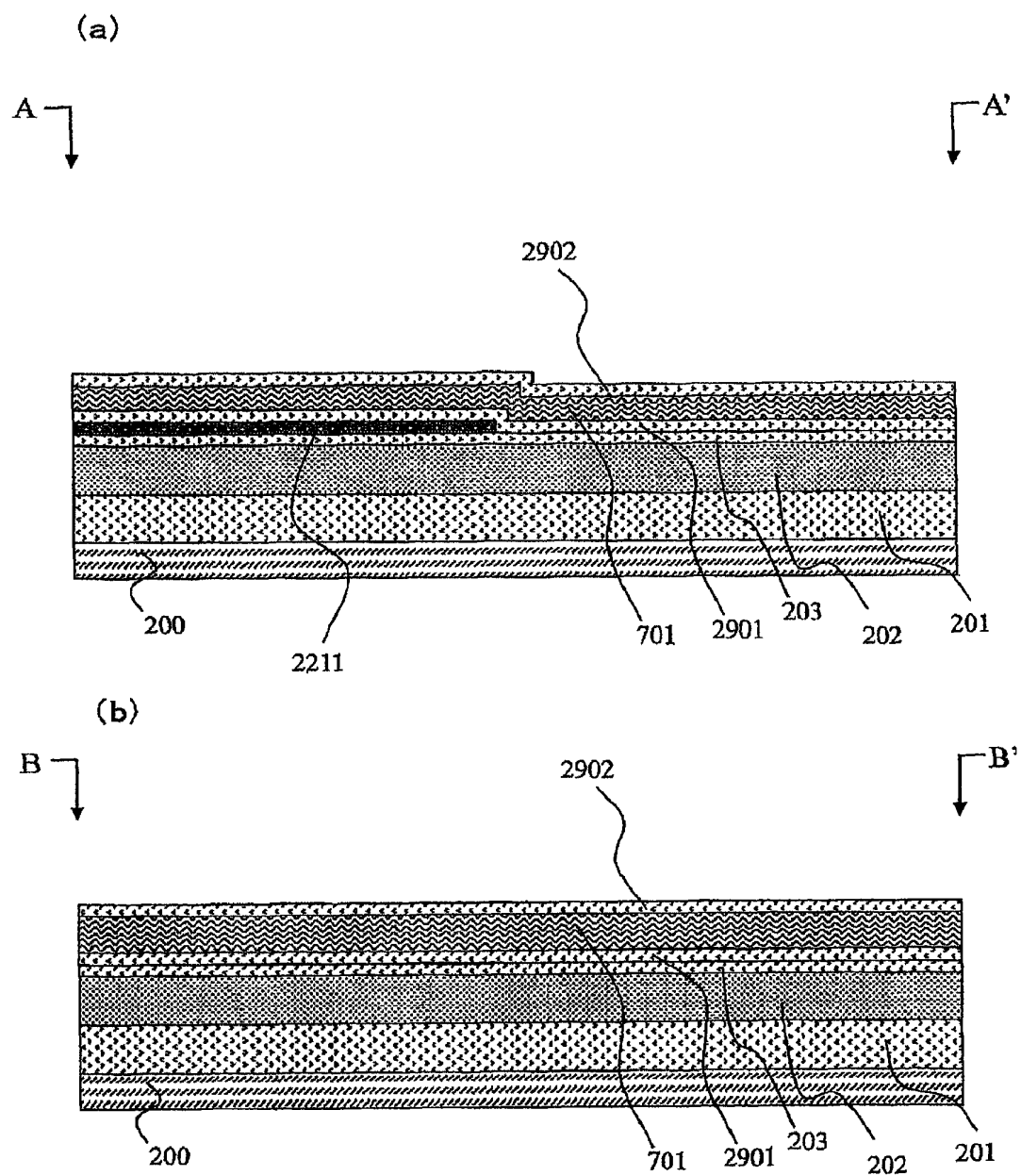


Fig. 35

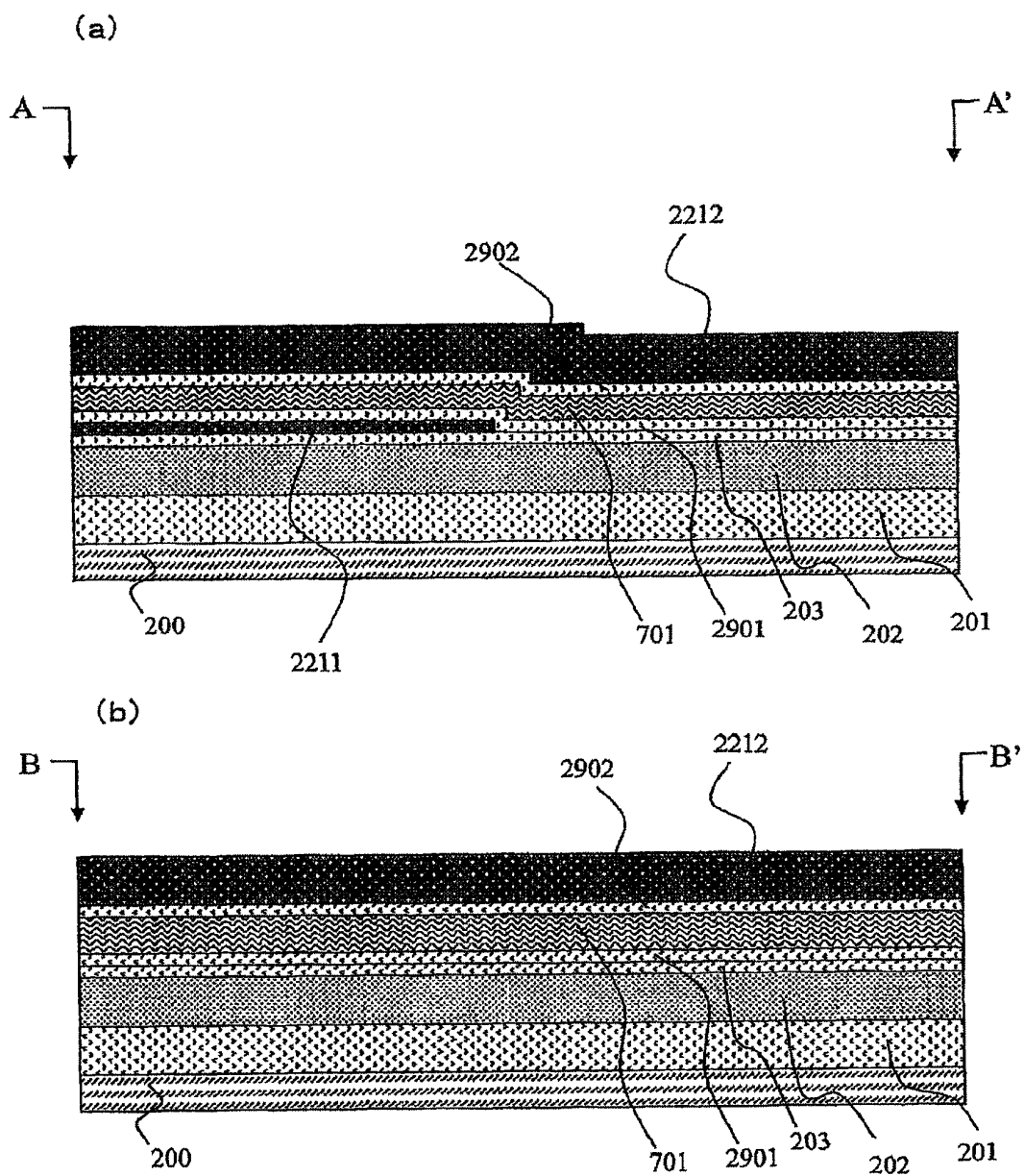


Fig. 36

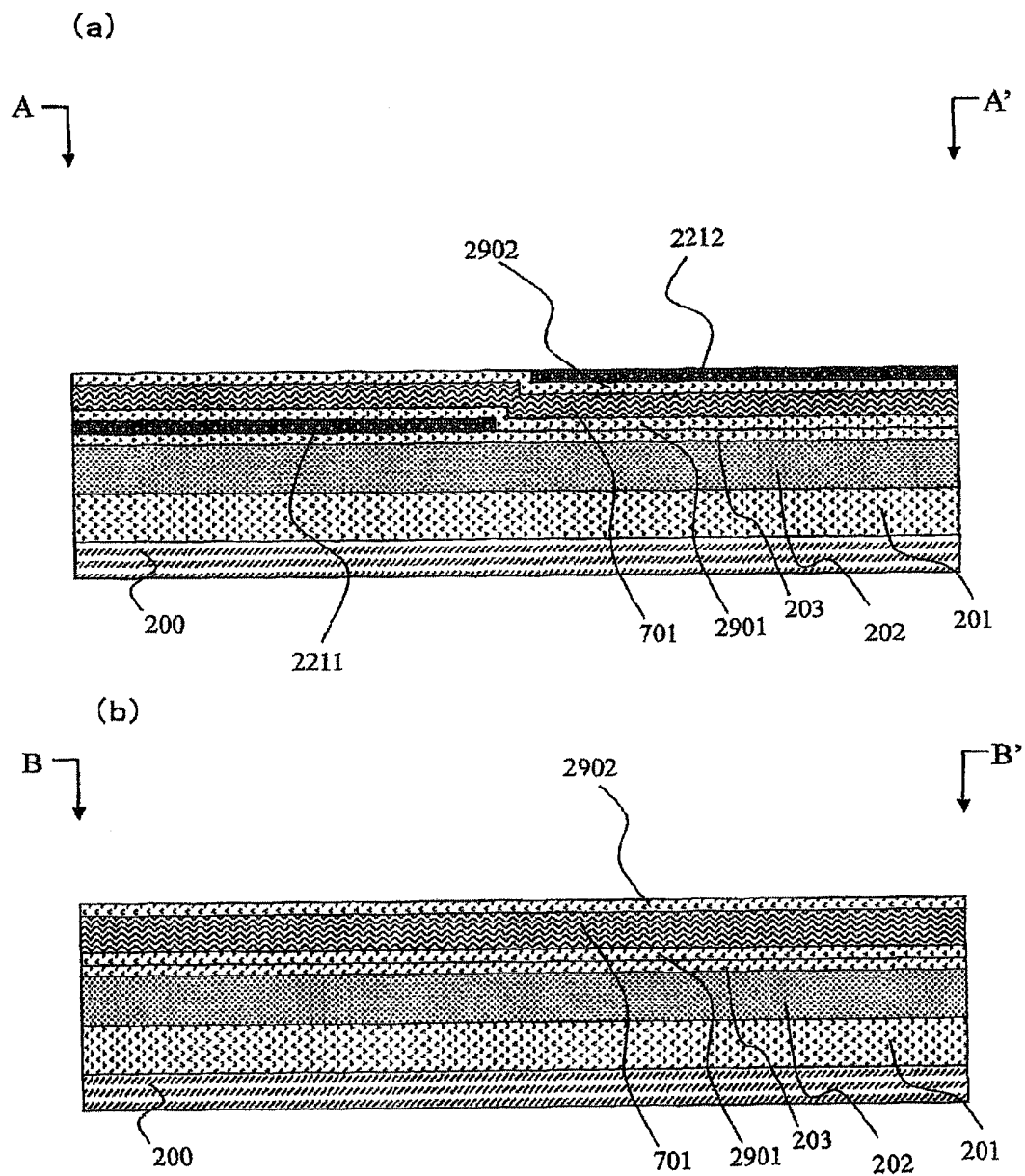


Fig. 37

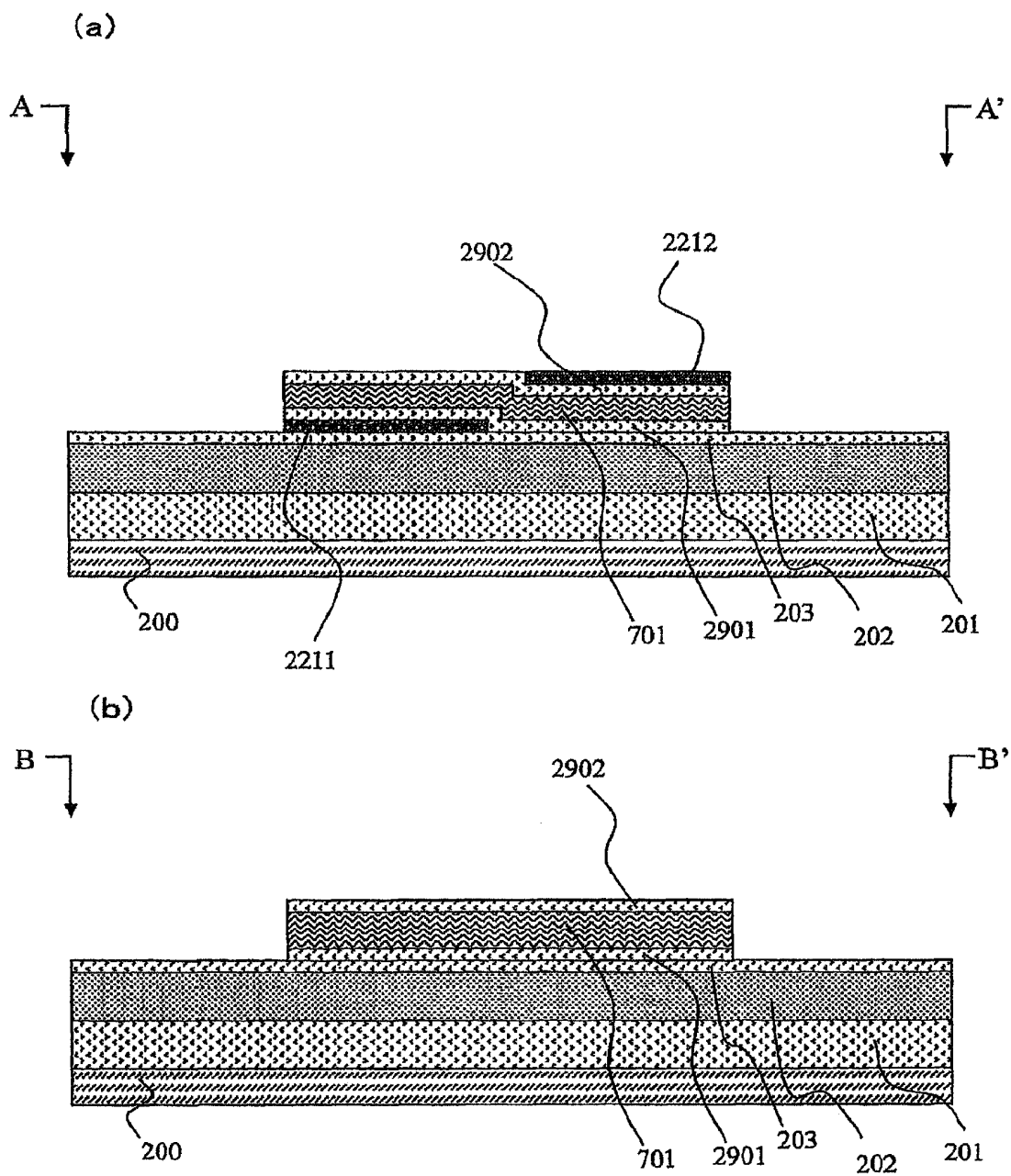


Fig. 38

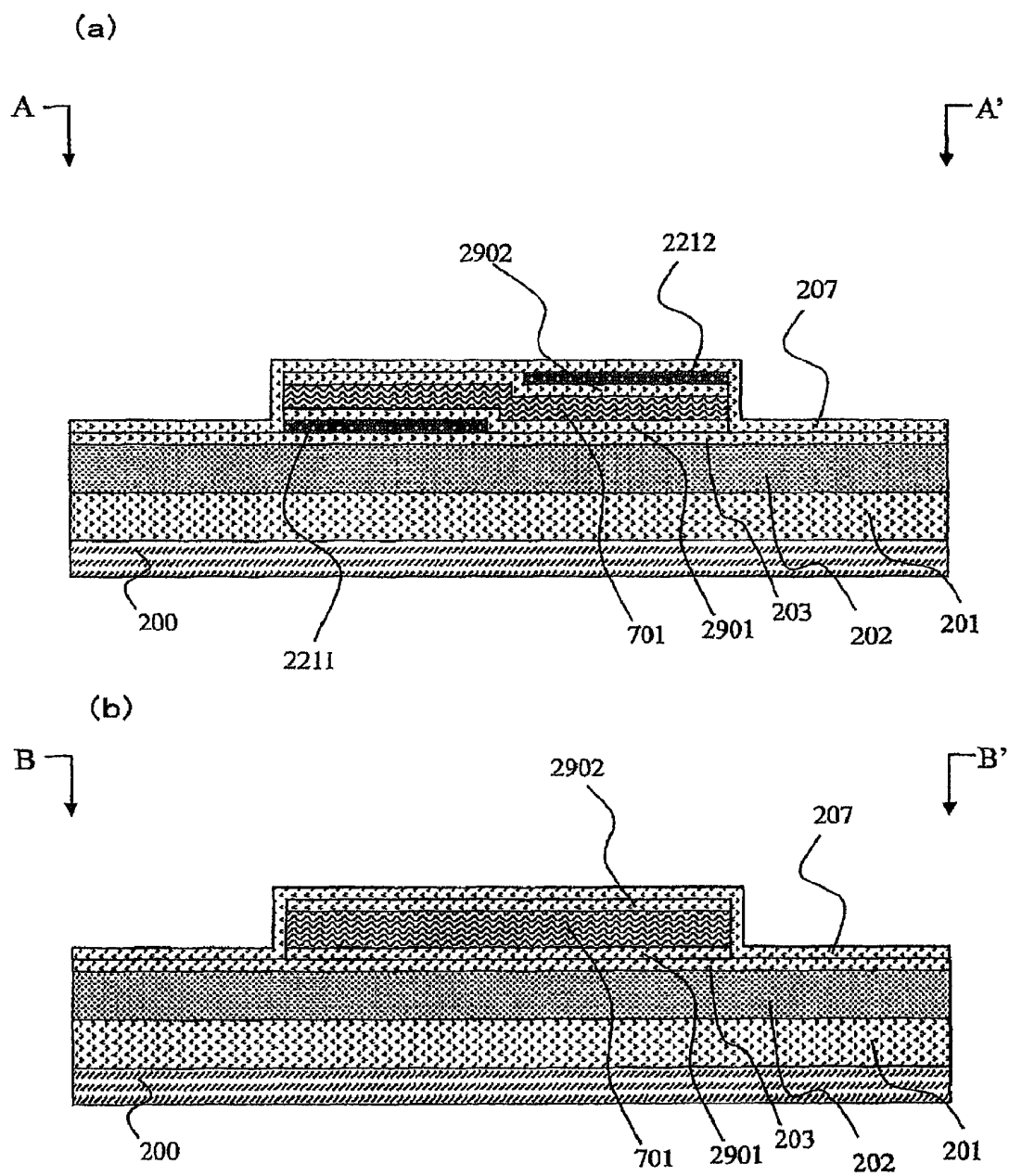


Fig. 39

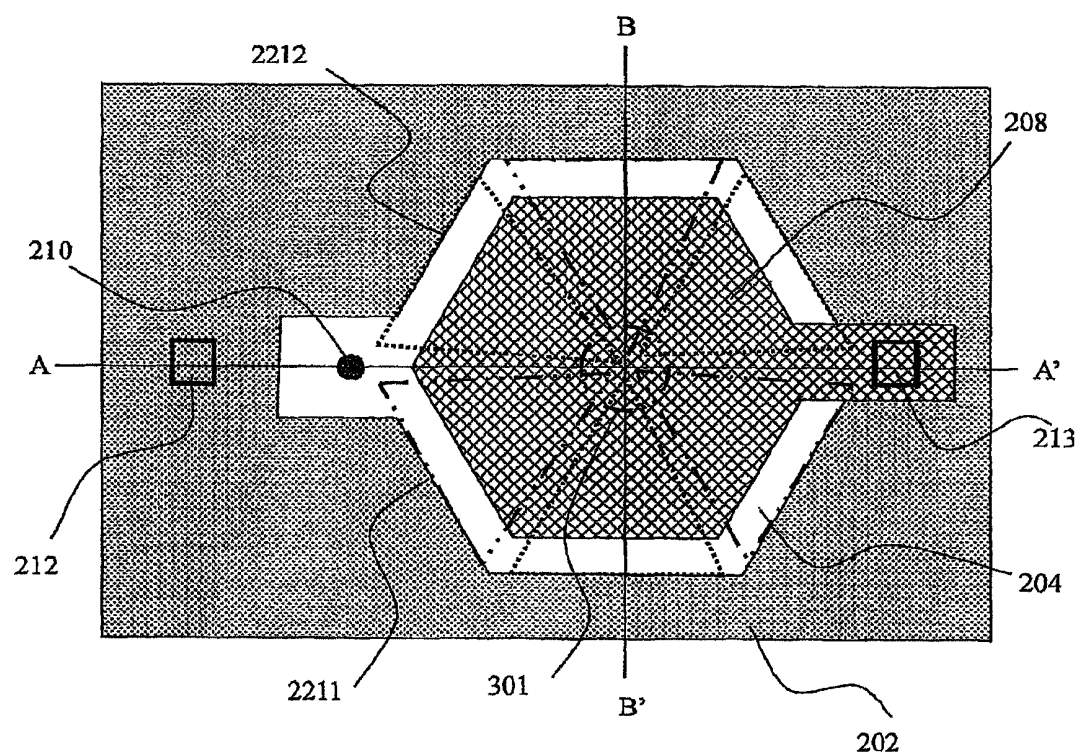
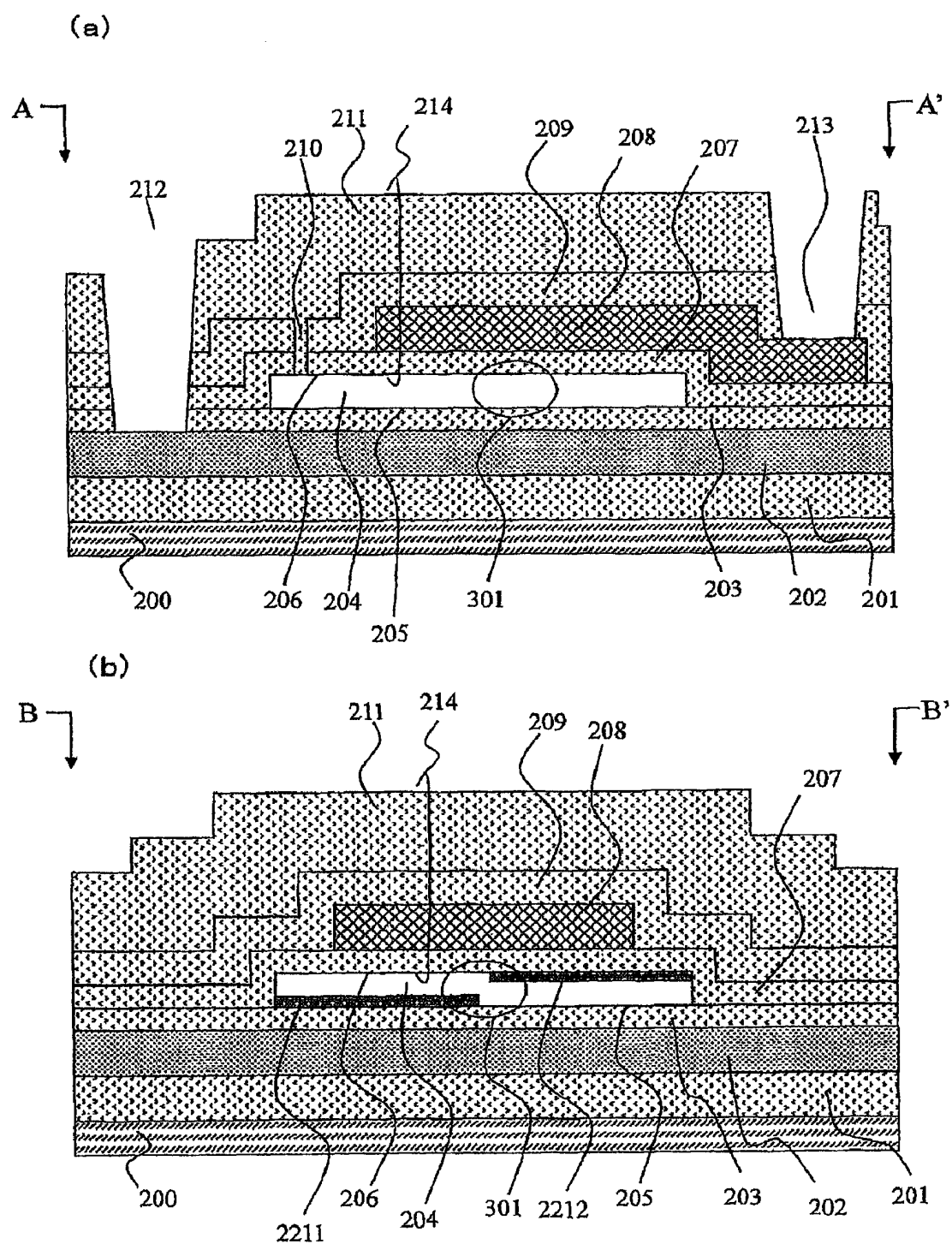


Fig. 40



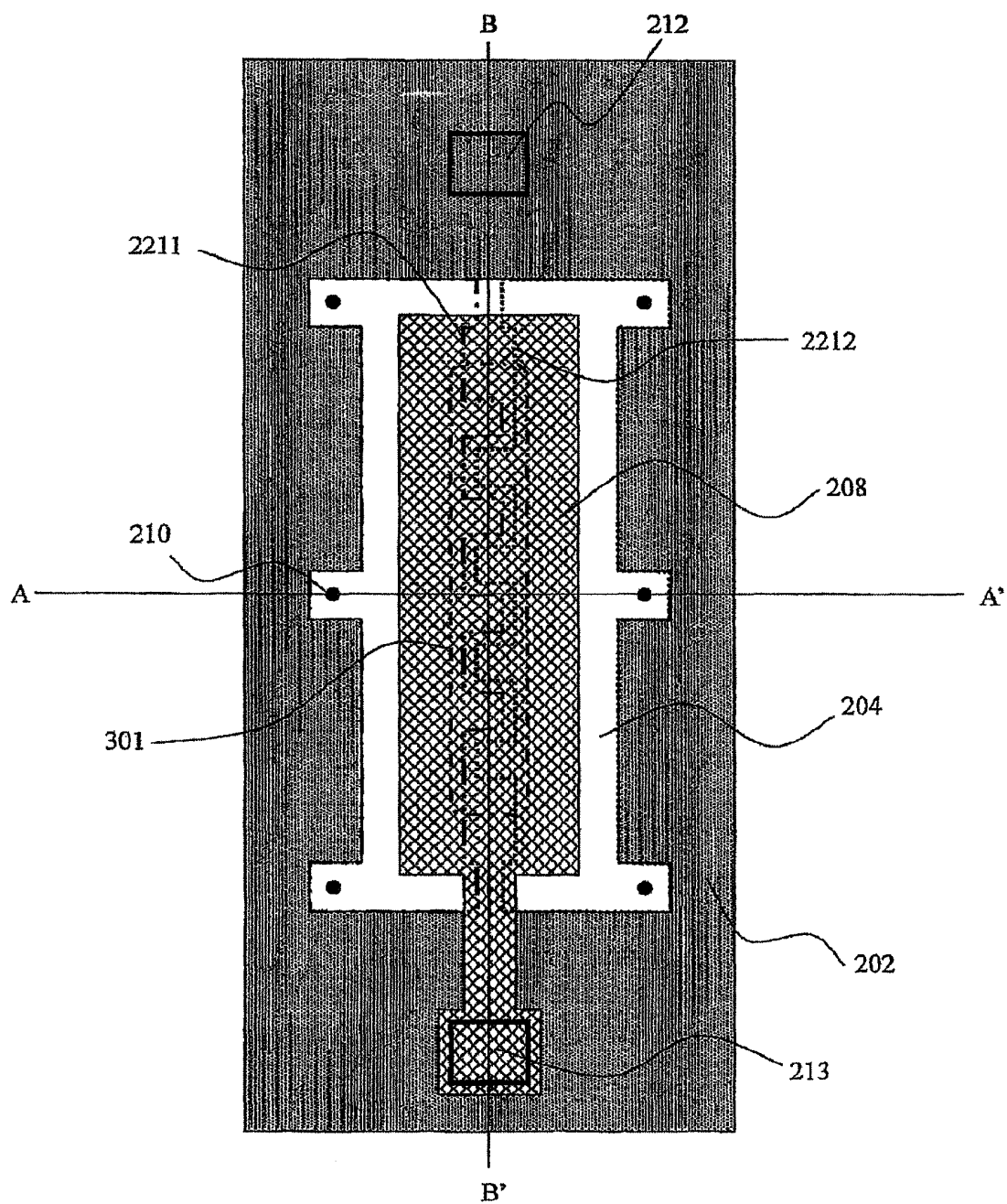


Fig. 42

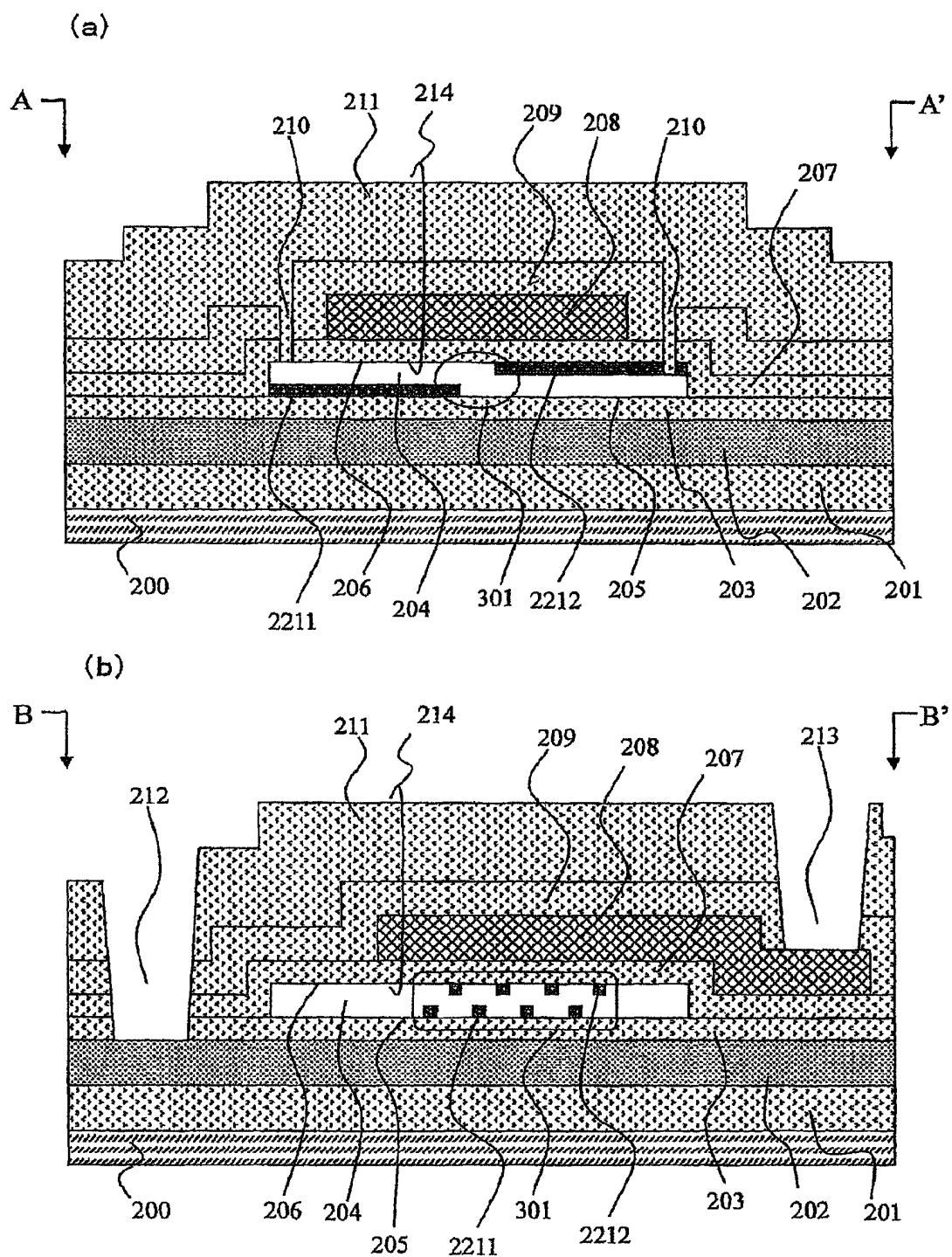


Fig. 43

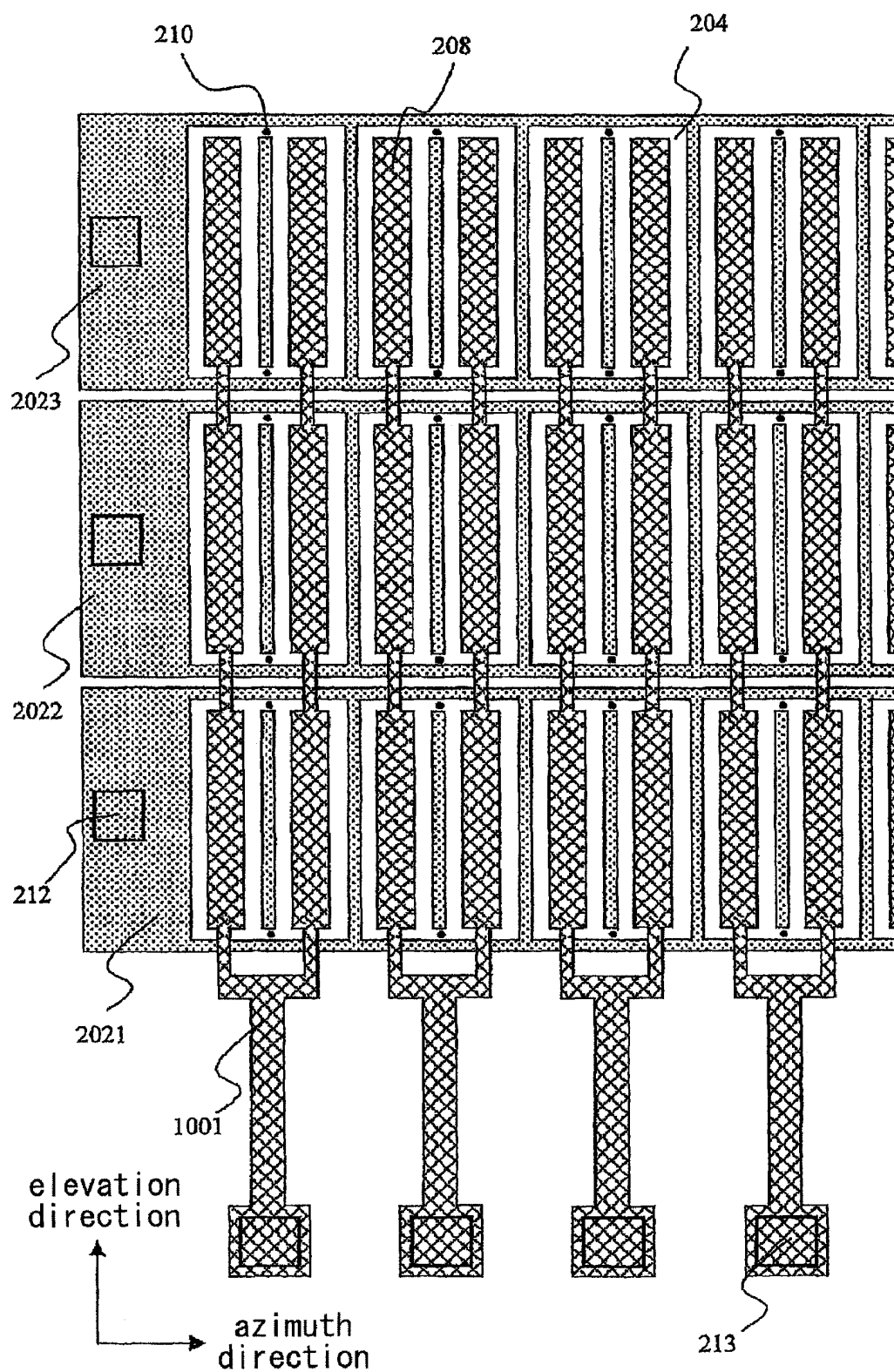


Fig. 44

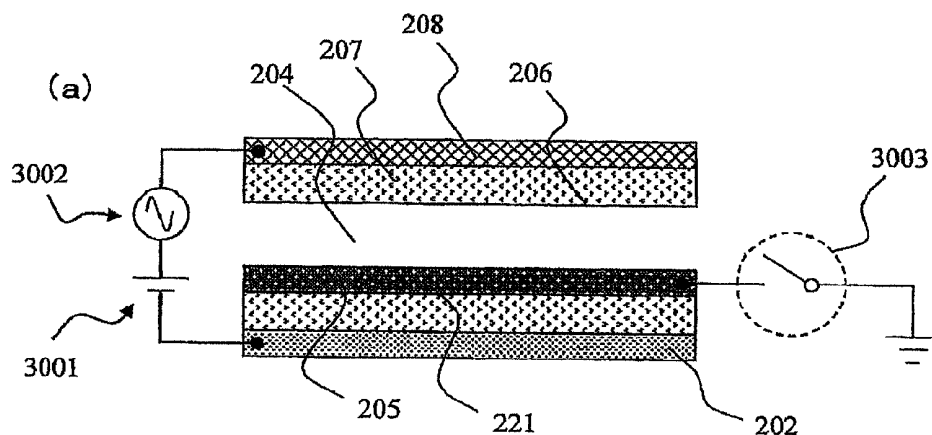


Fig. 45

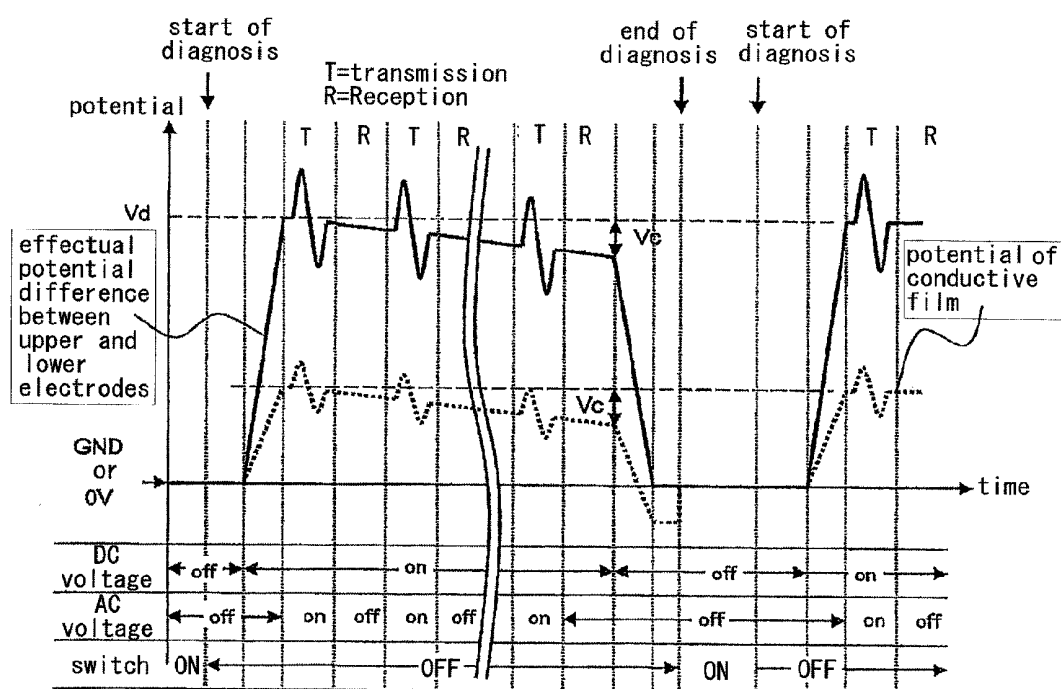


Fig. 46

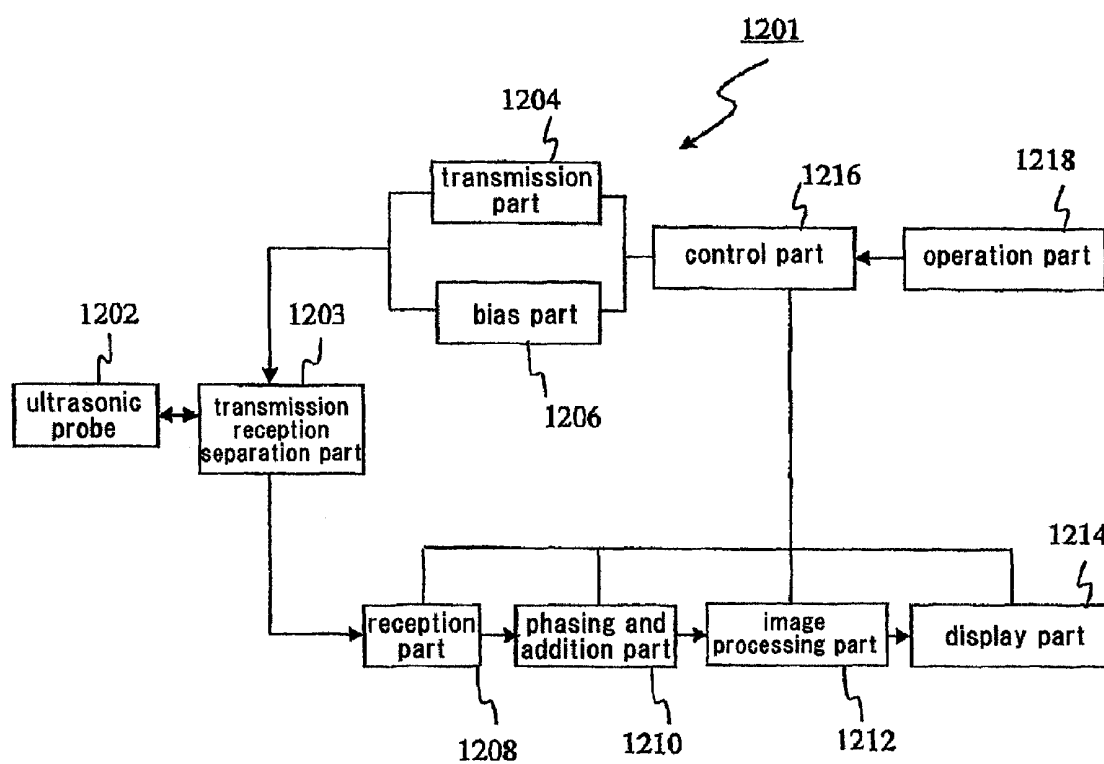


Fig. 47

ULTRASONIC TRANSDUCER AND ULTRASONIC DIAGNOSTIC DEVICE USING SAME

TECHNICAL FIELD

[0001] The present invention relates to an ultrasonic transducer and an ultrasonic diagnostic device using the same. In particular, the present invention relates to an ultrasonic transducer produced by the micro electro mechanical system (MEMS) technology, and an ultrasonic diagnostic device using the same.

BACKGROUND ART

[0002] Ultrasonic transducers transmit and receive ultrasonic waves, and thus they are used for diagnosis of tumors etc. in human bodies, nondestructive tests of structures, and so forth. As the ultrasonic transducers, those utilizing vibration of piezoelectric substances have so far been used. However, with progress of the MEMS technology in recent years, capacitive micromachined ultrasonic transducers (CMUTs) comprising a vibration part formed on a silicon substrate have been actively developed aiming at practical use thereof. For example, U.S. Pat. No. 6,320,239 B1 (Patent document 1) discloses a single CMUT and a CMUT array.

[0003] In contrast to the conventional transducers utilizing piezoelectric substances, CMUTs have advantages of the wide frequency band of usable ultrasonic waves, high sensitivity, and so forth. Moreover, since they are produced by using LSI processing techniques, micro processing can be used. In particular, CMUTs is considered to be indispensable when ultrasonic devices are arranged in an array and independently controlled. This is because, while wiring for each device is needed and thus the number of the wiring in the array becomes a huge number, CMUTs are produced by using LSI processing techniques, and therefore the wiring is easy. Moreover, that is also because the CMUTs can be embedded on one chip of a circuit which processes signals from the ultrasonic transmission and reception part.

[0004] With reference to FIG. 1, fundamental structure and operation of CMUT will be explained below. Above a lower electrode **101**, a hollow part **102** surrounded by an insulating film **103** is provided. Above the hollow part **102**, an upper electrode **104** is disposed through the insulating film **103**. If a direct voltage and an alternate voltage are superimposingly applied between the upper electrode **104** and the lower electrode **101**, an electrostatic force is generated between the upper electrode **104** and the lower electrode **101**, and a membrane **105** constituted by the insulating film **103** and the upper electrodes **104** above the hollow part **102** vibrates at the frequency of the applied alternate voltage to emit ultrasonic waves. Conversely, in the case of reception, the membrane **105** is vibrated by pressure of ultrasonic waves that arrive at the surface of the membrane **105**. Then, the distance between the upper electrode **104** and the lower electrode **101** varies, and therefore ultrasonic waves can be detected as change of electrostatic capacitance. According to the aforementioned principle of operation, by applying a direct voltage between the upper electrode **104** and the lower electrode **101**, an electrostatic force is generated between both the electrodes, and the membrane is deformed and stabilized at a deformation amount at which the spring restoring force induced by the deformation and the electrostatic force are balanced.

[0005] CMUT is usually driven at such a direct voltage that the electrostatic force between the electrodes and the spring restoring force are balanced. However, if a direct voltage larger than such a voltage that deformation amount of the membrane reaches about $\frac{1}{3}$ of the distance between the electrodes, called collapse voltage, is applied, the electrostatic force between the electrodes becomes larger than the spring restoring force of the membrane, thus the membrane cannot be stabilized at a fixed position, and the surface **106** above the hollow part contacts with the surface **107** below the hollow part. If they contact with each other, there is produced a structure that the insulating film **103** is held between the upper electrode and the lower electrode without the hollow part. As a result, electric field intensity in the insulating film becomes large in the contacting region, and electrical charge is injected into the insulating film from the electrodes to generate fixed electrical charge in the insulating film. After the direct voltage is shut off, if a direct voltage is applied again between the two electrodes, the electric field between the electrodes is shielded by the fixed electrical charge in the insulating film, and the voltage used for optimal operation of CMUT fluctuates. Moreover, it is also possible that the insulating property of the insulating film may be degraded depending on the injection rate of electrical charge into the insulating film, and thereby the upper electrode and the lower electrode may be short-circuited. Therefore, the CMUT disclosed in Patent document 1 is usually used with a voltage significantly lower than the collapse voltage in order to prevent the surface above the hollow part from contacting with the surface below the hollow part.

[0006] Japanese Patent Unexamined Publication (KOKAI) No. 2009-272824 (Patent document 2) discloses a structure in which a floating electrode is embedded in an insulating film between electrodes in order to reduce the direct voltage for driving CMUT or make continuous application thereof unnecessary.

PRIOR ART REFERENCES

Patent Documents

- [0007] Patent document 1: U.S. Pat. No. 6,320,239 B1
[0008] Patent document 2: Japanese Patent Unexamined Publication (KOKAI) No. 2009-272824

SUMMARY OF THE INVENTION

Object to be Achieved by the Invention

[0009] In order to improve reception sensitivity for ultrasonic waves, it is generally necessary to make the distance between the electrodes as short as possible at the time of use of CMUT, and therefore it is important to apply a voltage as close to the collapse voltage as possible between the electrodes. Moreover, in order to improve transmission sound pressure of the ultrasonic waves, it is desirable to maximize the vibration amplitude of the membrane **105**. However, in order to prevent the surface **106** above the hollow part from contacting with the surface **107** below the hollow part during the vibration, which results in injection of electrical charge into the insulating film, the alternate voltage to be superimposed on the direct voltage must also be a voltage significantly lower than the voltage at which the surface **106** above the hollow part contacts with the surface **107** below the hollow part.

[0010] Patent document 2 discloses a structure that a floating electrode is embedded in an insulating film between upper and lower electrodes. This structure is configured so that CMUT is driven by a potential difference between the floating electrode having electrical charge accumulated beforehand and the upper electrode or lower electrode. However, in order to prevent dissipation of the electrical charge accumulated in the floating electrode, it is necessary to cover circumference of the floating electrode with an insulating film, that is, embed the floating electrode in an insulating film. Further, since electrical charge is accumulated in the floating electrode beforehand, when the surfaces above and below the hollow part contact with each other, accumulation of electrical charge in the insulating film between the floating electrode and the upper electrode or lower electrode and reduction of the insulation withstand voltage of the insulating film are unavoidable.

[0011] As described above, because of the problems caused by the contact of the surfaces above and below the hollow part, it is difficult to use a larger direct current voltage or alternate current voltage, i.e., improve reception sensitivity or transmission sound pressure, in the conventional transducers according to the conventional techniques.

Means for Achieving the Object

[0012] Brief explanations of the outlines of the representative embodiments of the present invention disclosed in this application are as follows.

[0013] The present invention relates to an ultrasonic transducer comprising a first electrode, a first insulating film disposed on the first electrode, a hollow part provided above the insulating film, a second insulating film disposed above the hollow part, a second electrode disposed on the second insulating film, and an electrically isolated conductive film disposed between the first electrode and the second electrode, wherein the conductive film is disposed at such a position that, as seen from above, the conductive film overlaps with a region in which surfaces above and below the hollow part contact with each other when the transducer is driven, and the conductive film is exposed to the hollow part.

[0014] Another embodiment of the present invention is an ultrasonic transducer comprising a first electrode, a first insulating film disposed on the first electrode, a hollow part provided above the insulating film, a second insulating film disposed above the hollow part, a second electrode disposed on the second insulating film, a conductive film disposed between the first electrode and the second electrode at such a position that, as seen from above, the conductive film overlaps with a region in which surfaces above and below the hollow part contact with each other when the transducer is driven, and a switch connected to the conductive film for controlling ON/OFF of connection of the conductive film to the ground potential.

[0015] Still another embodiment of the present invention is an ultrasonic transducer comprising a first electrode, a first insulating film disposed on the first electrode, an electrically isolated first conductive film disposed on the first insulating film, a hollow part provided above the first conductive film, an electrically isolated second conductive film disposed above the hollow part, a second insulating film disposed on the second conductive film, and a second electrode disposed on the second insulating film, wherein the first conductive film and the second conductive film are disposed in a region in which surfaces above and below the hollow part contact with

each other when the transducer is driven, and the first conductive film and the second conductive film do not overlap with each other in that region as seen from above.

[0016] As another aspect, the present invention provides an ultrasonic diagnostic device provided with an ultrasonic probe comprising any of the aforementioned ultrasonic transducers, and a control part for controlling the ultrasonic probe.

Effect of the Invention

[0017] The present invention provides a structure of CMUT for suppressing accumulation of electrical charge in an insulating film between upper and lower electrodes and reduction of insulation withstand voltage thereof even when surfaces above and below the hollow part contact with each other, and an ultrasonic diagnostic device using it. The present invention also provides a CMUT that can improve reception sensitivity and transmission sound pressure compared with those of conventional CMUTs while securing reliability, and an ultrasonic diagnostic device using it.

BRIEF DESCRIPTION OF THE DRAWINGS

[0018] FIG. 1 is a sectional view of an ultrasonic transducer examined by the inventors of the present invention.

[0019] FIG. 2 is a top view of an ultrasonic transducer according to the embodiment 1 of the present invention, in which the hollow part has a hexagonal shape as seen from above.

[0020] FIG. 3, (a) is a sectional view of the ultrasonic transducer shown in FIG. 2 along the line A-A' drawn in FIG. 2, and (b) is a sectional view of the same along the line B-B' drawn in FIG. 2.

[0021] FIG. 4 include enlarged views of a contact region of an ultrasonic transducer according to the embodiment 1 in a state that the surfaces above and below the hollow part contact with each other in that region when the transducer is driven, (a) is such an enlarged view for the case where the conductive film is not disposed, and (b) is such an enlarged view for the case where the conductive film 221 is disposed so as to be exposed to the hollow part.

[0022] FIGS. 5, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer shown in FIG. 2 along the lines A-A' and B-B' drawn in FIG. 2, respectively.

[0023] FIGS. 6, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 5, (a) and (b).

[0024] FIGS. 7, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 6, (a) and (b).

[0025] FIGS. 8, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 7, (a) and (b).

[0026] FIGS. 9, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 8, (a) and (b).

[0027] FIGS. 10, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 9, (a) and (b).

[0028] FIGS. 11, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 10, (a) and (b).

[0029] FIGS. 12, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 11, (a) and (b).

[0030] FIGS. 13, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 12, (a) and (b).

[0031] FIGS. 14, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 13, (a) and (b).

[0032] FIG. 15 is a top view of an ultrasonic transducer according to the embodiment 1, in which the hollow part has a hexagonal shape as seen from above, and the conductive film is smaller than the hollow part as seen from above.

[0033] FIG. 16 is a top view of an ultrasonic transducer according to the embodiment 1, in which the hollow part has a hexagonal shape as seen from above, and the conductive film is larger than the hollow part as seen from above.

[0034] FIG. 17 is a top view of an ultrasonic transducer according to the embodiment 2, in which the hollow part has a hexagonal shape as seen from above.

[0035] FIG. 18, (a) is a sectional view of the ultrasonic transducer shown in FIG. 17 along the line A-A' drawn in FIG. 17, and (b) is a sectional view of the same along the line B-B' drawn in FIG. 17.

[0036] FIG. 19 is a top view of an ultrasonic transducer according to the first example of the embodiment 3, in which the hollow part has a rectangular shape as seen from above.

[0037] FIG. 20, (a) is a sectional view of the ultrasonic transducer shown in FIG. 19 along the line A-A' drawn in FIG. 19, and (b) is a sectional view of the same along the line B-B' drawn in FIG. 19.

[0038] FIG. 21, (a) is an enlarged view of a contact region of the ultrasonic transducer according to the embodiment 3 in a state that the surfaces above and below the hollow part contact with each other in that region when the transducer is driven, and (b) shows an equivalent circuit diagram for the ultrasonic transducer according to the embodiment 3 in a state that the surfaces above and below the hollow part contact with each other when the transducer is driven.

[0039] FIGS. 22, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer shown in FIG. 19 along the lines A-A' and B-B' drawn in FIG. 19, respectively.

[0040] FIGS. 23, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 22, (a) and (b).

[0041] FIGS. 24, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 23, (a) and (b).

[0042] FIGS. 25, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 24, (a) and (b).

[0043] FIGS. 26, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 25, (a) and (b).

[0044] FIGS. 27, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 26, (a) and (b).

[0045] FIGS. 28, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 27, (a) and (b).

[0046] FIG. 29 includes drawings showing an ultrasonic transducer according to the second example of the embodi-

ment 3, FIG. 29, (a) is a sectional view along the line A-A' drawn in FIG. 19, and (b) is a sectional view along the line B-B' drawn in FIG. 19.

[0047] FIGS. 30, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer shown in FIG. 29.

[0048] FIGS. 31, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 30, (a) and (b).

[0049] FIGS. 32, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 31, (a) and (b).

[0050] FIGS. 33, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 32, (a) and (b).

[0051] FIGS. 34, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 33, (a) and (b).

[0052] FIGS. 35, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 34, (a) and (b).

[0053] FIGS. 36, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 35, (a) and (b).

[0054] FIGS. 37, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 36, (a) and (b).

[0055] FIGS. 38, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 37, (a) and (b).

[0056] FIGS. 39, (a) and (b) are sectional views for explaining a manufacturing step of the ultrasonic transducer following the step shown in FIGS. 38, (a) and (b).

[0057] FIG. 40 is a top view of an ultrasonic transducer according to the third example of the embodiment 3.

[0058] FIG. 41, (a) is a sectional view of the ultrasonic transducer shown in FIG. 40 along the line A-A' drawn in FIG. 40, and (b) is a sectional view of the ultrasonic transducer along the line B-B' drawn in FIG. 40.

[0059] FIG. 42 is a top view of an ultrasonic transducer according to the fourth example of the embodiment 3.

[0060] FIG. 43, (a) is a sectional view of the ultrasonic transducer shown in FIG. 42 along the line A-A' drawn in FIG. 42, and (b) is a sectional view of the ultrasonic transducer along the line B-B' drawn in FIG. 42.

[0061] FIG. 44 is a top view of a chip on which the ultrasonic transducers according to the embodiment 4 are disposed in an array.

[0062] FIG. 45 is a schematic sectional view of an ultrasonic transducer according to the embodiment 5.

[0063] FIG. 46 is a graph showing effectual potential difference between the upper electrode and the lower electrode, electric potential of the conductive film, ON/OFF of direct voltage and alternating voltage, and switching of a switch(s) at the time of ultrasonic diagnosis using the ultrasonic transducer according to the embodiment 5.

[0064] FIG. 47 is a configurational diagram of an ultrasonic diagnostic device according to the embodiment 6.

MODES FOR CARRYING OUT THE INVENTION

[0065] Hereafter, embodiments of the present invention will be explained in detail with reference to the drawings. In all the drawings for explaining the embodiments, the same

members are basically indicated with the same numerals, and repetitive explanations for them are omitted.

[0066] In the following explanations of the embodiments, explanations are made with several sections or several examples for convenience as required, but they are mutually related, and are in such a relation that one of them is modification, details, supplemental explanation or the like of a part or all of the other, unless especially indicated. Moreover, in the following explanations of the embodiments, when a number of an element or the like (including number, numerical value, quantity, range etc.) is mentioned, the numeral is not limited to that specific number, and may be larger or smaller than the mentioned number, except for the case where it is explicitly indicated that the number should be the specifically mentioned number, or it is theoretically clear that the number should be limited to the specifically mentioned number. Furthermore, in the embodiments mentioned below, it is of course that the constituent elements (including steps as elements etc.) are not necessarily indispensable, except for the case where it is explicitly indicated that a specific element is indispensable, or it is theoretically clear that a specific element is indispensable. Similarly, in the following explanations of the embodiments, when shapes, positional relationship etc. of constituent elements etc. are mentioned, they include substantially similar or analogous shapes and so forth, except for the case where it is explicitly indicated, or it is theoretically clear that the above is not true. This shall also apply to the numerical values and ranges mentioned above. In addition, even in a plane view, hatching may be used for ease of understanding.

[0067] In the following embodiments, the object of suppressing accumulation of electrical charge in an insulating film and reduction of insulation withstand voltage thereof even when surfaces above and below the hollow part contact with each other is achieved by disposing a conductive film so as to be exposed to the hollow part from either one or both of upside and downside of the hollow part.

Embodiment 1

[0068] In the embodiment 1, the object of suppressing accumulation of electrical charge in an insulating film and reduction of insulation withstand voltage thereof even when surfaces above and below the hollow part contact with each other at the time of driving is achieved by disposing a conductive film so as to be exposed to the hollow part from the underside of the hollow part.

[0069] FIG. 2 is a top view of an ultrasonic transducer (CMUT) according to the embodiment 1. FIG. 2 shows a single CMUT cell. The CMUT cell comprises a lower electrode 202, a hollow part 204 formed above the lower electrode 202, an upper electrode 208 disposed above the hollow part 204, and so forth. An etching hole 210 for forming the hollow part is communicated with a portion to become the hollow part 204. An opening 212 is provided so as to reach the lower electrode 202, and an opening 213 is provided so as to reach the upper electrode 208. Between the lower electrode 202 and the hollow part 204, an insulating film 203 consisting of a silicon oxide film is formed so as to cover the lower electrode 202, and between the upper electrode 208 and the hollow part 204, an insulating film 207 consisting of a silicon oxide film is formed so as to cover the hollow part 204 and the lower electrode 202. However, these insulating films are not shown in the drawing, in order to show the hollow part 204 and the

lower electrode 202. Moreover, a conductive film 221 is formed so as to be exposed to the hollow part 204, but it is not shown in the drawing.

[0070] FIG. 3, (a) is a sectional view of the ultrasonic transducer along the line A-A' drawn in FIG. 2, and (b) is a sectional view of the same along the line B-B' drawn in FIG. 2. As shown in FIGS. 3, (a) and (b), the lower electrode 202 of the CMUT is disposed on the insulating film 201 consisting of a silicon oxide film and formed on a semiconductor substrate 200. Above the lower electrode 202, the hollow part 204 is formed through the insulating film 203 consisting of a silicon oxide film. Further, a conductive film 221 is disposed at such a position that it overlaps with the hollow part as seen from above so as to be exposed to the hollow part 204. The surfaces 205 and 206 correspond to upper and lower end planes of the hollow part 204. The insulating film 207 consisting of a silicon oxide film is disposed so as to surround the hollow part 204 and the conductive film 221, and the upper electrode 208 is formed on the insulating film 207. An insulating film 209 and an insulating film 211 consisting of silicon nitride films are disposed on the upper electrode 208. Further, the etching hole 210 is formed in the insulating film 207 and the insulating film 209 so as to penetrate these films, and filled with the insulating film 211. This etching hole 210 is formed for forming the hollow part 204. A membrane 214 according to the embodiment 1 is constituted with the insulating films 207, 209 and 211 and the upper electrode 208.

[0071] The characteristics of the embodiment 1 will be explained with reference to FIG. 4. FIG. 4 includes enlarged views of a region in which the surface 206 above the hollow part 204 and the surface 205 below the hollow part 204 contact with each other (contact region), when CMUT is driven, and the membrane 214 vibrates. FIG. 4, (a) is for the case where the conductive film is not disposed, and FIG. 4, (b) is for the case where the conductive film 221 is disposed according to the embodiment 1. This conductive film 221 is an electrically isolated film.

[0072] As shown in FIG. 4, (a), when CMUT is driven, in the region 301 where the surface 206 above the hollow part 204 and the surface 205 below the hollow part 204 contact with each other, there is provided a structure that there are only the insulating film 203 and the insulating film 207 between the lower electrode 202 and the upper electrode 208, and in the other region, there is also the hollow part 204 between the upper electrode and the lower electrode in addition to the insulating films 203 and 207. As a result, the electric field intensity in the insulating films 203 and 207 of the contact region 301 becomes higher than the electric field intensity in the insulating film 203 and 207 of the region other than the contact region 301. Therefore, extremely weak leak electric currents between the lower electrode 202 and the upper electrode 208 flowing through the insulating films 203 and 207 concentrate in the contact region 301, which leads to degradation of dielectric strength of the insulating films 203 and 207.

[0073] On the other hand, when the conductive film 221 is disposed so that it is exposed to the hollow part 204 as shown in FIG. 4, (b), since the conductive film 221 is an electrically isolated conductive film, the conductive film 221 is made to have a potential corresponding to a distributed potential of the potential difference between the lower electrode 202 and the upper electrode 208 by the capacitance of the insulating films 203 and 207 and the hollow part 204 existing between the lower electrode 202 and the upper electrode 208, and the

whole conductive film becomes isopotential. Therefore, in the insulating film 203 between the conductive film 221 and the lower electrode 202, electric field intensity is the same in the contact region 301 and the other region, thus concentration of the leak electric currents in the contact region 301 can be suppressed, and accumulation of electrical charge in the insulating film 203 and degradation of dielectric strength thereof can be suppressed. Although the electric field intensity in the insulating film 207 of the contact region 301 is still higher than that of the region except for the contact region 301, if the direction of the flow of electric current, i.e., the polarity of the electric potential between the upper electrode and the lower electrode, is taken into consideration, degradation of the insulating film 207 can also be suppressed. In the CMUT according to the embodiment 1 shown in FIGS. 2, 3, and 4, (b) using, for example, the lower electrode and upper electrode consisting of metals, it is sufficient to make the potential of the lower electrode to be lower than that of the upper electrode. In such a case, since the leak electric currents are produced by electrons, and electrons flow from the electrode of lower potential to the electrode of higher potential, electrons flow from the lower electrode 202 to the insulating film 203, the conductive film 221, the insulating film 207, and then the upper electrode in this order. In this example, since the dielectric strength of the insulating film 203 is not easily degraded, flow amount of electrons constituting leak electric currents itself can also be reduced. Therefore, even if the electric field intensity in the insulating film 207 of the contact region 301 remains to be higher than that in the region except for the contact region 301, the flow amount of electrons (current amount) concentrated in the contact region 301 itself can be made small, and therefore accumulation of electrical charge in the insulating film 207 and degradation of dielectric strength thereof can be suppressed. That is, when the conductive film is disposed on the lower electrode side, degradation of the dielectric strength of the insulating films 203 and 207 can be suppressed by applying a direct voltage between the upper electrode and the lower electrode, so that potential of the lower electrode is lower than that of the upper electrode. Moreover, since degradation of the dielectric strength of the insulating films 203 and 207 can be suppressed even when the surfaces above and below the hollow part contact with each other, the membrane can be vibrated to such an extent that the surfaces above and below the hollow part contact with each other, that is, the membrane can be vibrated by fully utilizing the thickness of the hollow part at maximum, and thus transmission sound pressure can be improved. Further, thickness of the hollow part can be made thinner to the minimum thickness that can secure amplitude of the membrane vibration that can provide sound pressure required for the diagnosis, and thus reception sensitivity can be improved.

[0074] Hereafter, the effects of the invention of the embodiment 1 will be explained by contrasting it with the conventional technique disclosed in Patent document 2. In the conventional technique, it is disclosed that a floating electrode is embedded in an insulating film and electrified to make the direct voltage unnecessary or reduce the direct voltage. On the other hand, the invention of the embodiment 1 uses a structure that the conductive film corresponding to the floating electrode is not embedded in an insulating film, but is exposed to the hollow part. In this structure, there is not any insulating film between the conductive film and the hollow part, and the conductive film is exposed to the hollow part. This is because it is indispensable for the invention of the

embodiment 1 to use a conductive film that is not charged or is not easily charged in order to achieve the aforementioned object. Therefore, in order to make the conductive film difficult to be charged, there is employed such a structure that even if electrical charge is accumulated in the conductive film, the accumulated electrical charge is easily discharged via the hollow part.

[0075] As described above, by using such a structure that electrical charge is hardly accumulated in the conductive film, even when the surfaces above and below the hollow part contact with each other at the time of driving of the transducer, there is extremely little accumulated electrical charge, and therefore it can be prevented from flowing into the insulating film 207. Therefore, accumulation of electrical charge in the insulating film 207 caused by the electric field between the floating electrode and the upper electrode and degradation of dielectric strength thereof can be more suppressed compared with the CMUT of Patent document 2, which comprises the floating electrode charged to such a degree that the direct voltage is effectually reduced. Moreover, while the accumulated electrical charges reduces with lapse of time in this conventional technique, the technique of the embodiment 1 provides very little change of the accumulated electrical charge due to such discharge, therefore the direct voltage set to be an optimal value beforehand is not need to be changed more than necessary, and thus CMUT can be used under a favorable condition, which is substantially the optimal value, for a long period of time.

[0076] Next, the method for producing the CMUT cell described as the embodiment 1 will be explained with reference to the drawings. In FIGS. 5 to 14, (a) shows section along the lines A-A' and (b) shows section along the lines B-B' drawn in FIG. 2, respectively.

[0077] First, as shown in FIGS. 5, (a) and (b), the insulating film 201 consisting of a silicon oxide film is deposited in 400 nm thickness on the semiconductor substrate 200 by the plasma-CVD (Chemical Vapor Deposition) method. Then, a titanium nitride film, an aluminum alloy film, and a titanium nitride film are deposited in 100 nm, 600 nm and 100 nm thicknesses, respectively, on the insulating film 201 by the sputtering method, and then patterning is performed by the photolithography and dry etching techniques to form the lower electrode 202 (FIGS. 6, (a) and (b)).

[0078] Then, as shown in FIGS. 7, (a) and (b), the insulating film 203 consisting of a silicon oxide film is deposited in 100 nm thickness on the lower electrode 202 by the plasma-CVD method, then an aluminum alloy film serving as the electrically isolated conductive film 221 is deposited in 50 nm thickness on the upper surface of the insulating film 203 by the sputtering method, a polycrystalline silicon film is further deposited in 100 nm thickness by the plasma-CVD method, and patterning is performed for the aluminum alloy film and the polycrystalline silicon film by photolithography and dry etching techniques to form a sacrificial layer 701 consisting of the conductive film 221 and the polycrystalline silicon film on the insulating film 203. The hollow part is formed at the position of the sacrificial layer 701 in a subsequent step.

[0079] Then, the insulating film 207 consisting of a silicon oxide film is deposited in 100 nm thickness by the plasma-CVD method so as to cover the conductive film 221, the sacrificial layer 701, and the insulating film 203 (FIGS. 8, (a) and (b)). Then, in order to form the upper electrode 208 of the CMUT cell, a laminate film consisting of a titanium nitride film, an aluminum alloy film, and a titanium nitride film are

deposited in 50 nm, 300 nm and 50 nm thicknesses, respectively, by the sputtering method. Then, the upper electrode 208 is formed by the photolithography and dry etching techniques (FIGS. 9, (a) and (b)).

[0080] Then, by the plasma-CVD method, the insulating film 209 consisting of a silicon nitride film is deposited in 500 nm thickness so as to cover the insulating film 207 and the upper electrode 208 (FIGS. 10, (a) and (b)). Next, the etching hole 210 is formed in the insulating films 209 and 207 by using the photolithography and dry etching techniques so as to reach the sacrificial layer 701 (FIGS. 11 (a) and (b)). Then, the sacrificial layer 701 is isotropically etched with xenon fluoride (XeF₂) gas through the etching hole 210 to form the hollow part 204 (FIGS. 12, (a) and (b)).

[0081] Then, in order to fill the etching hole 210, the insulating films 211 consisting of a silicon nitride film is deposited in 800 nm thickness by the plasma-CVD method (FIGS. 13, (a) and (b)). By this step, the membrane 214 consisting of the insulating films 203, 209 and 211, and the upper electrode 208 is formed. Then, the opening 212 for providing electric connection to the lower electrode 202 and the opening 213 for providing electric connection to the upper electrode 208 are formed by using the photolithography and dry etching techniques (FIGS. 14, (a) and (b)). In this way, the CMUT cell of the embodiment 1 can be formed.

[0082] The size of the conductive film 221 as seen from above will be explained below. In the example shown in FIG. 2, the hollow part 204 and the conductive film 221 have the same shape as seen from above, and are disposed so as to overlap with each other. However, they are not limited to have such a configuration. It is sufficient that the conductive film 221 has a size larger than the region where the surface 206 above the hollow part and the surface 205 below the hollow part contact with each other at least at the time of driving. In other words, this conductive film may be provided so that, in a static state, it exists in a region including a predetermined area of which center is the center of gravity of the membrane, in which the perpendicular displacement of the membrane becomes maximum. This is because concentration of the electric field can be more suppressed compared with the case using no conductive film. If the ultrasonic transducer is used at a voltage in such a range that the surfaces above and below the hollow part contact with each other at a point, it is sufficient that the conductive film is provided for an area including the point. On the other hand, when the ultrasonic transducer is used at a voltage in such a range that the surfaces above and below the hollow part contact with each other in an area, not a point, it is sufficient that the conductive film is provided for a region including the area. For example, it is sufficient that, as shown with broken lines in FIG. 15, the shape of the conductive film 221 is larger than the region 301 in which the surface 206 above the hollow part 204 and the surface 205 below the hollow part 204 contact with each other as seen from above. Alternatively, as shown with the broken lines in FIG. 16, the shape of the conductive film 221 may be larger than the hollow part 204 as seen from above. In this case, concentration of the electric currents in the insulating film of the contact region 301 can be further reduced due to the larger size of the conductive film 221.

[0083] In addition, although the CMUT cell shown FIG. 2 has a hexagonal shape as the planar shape, the shape is not limited such a shape, and may be, for example, a circular shape or a rectangular shape. Further, the materials constituting the CMUT cell shown as the embodiment 1 just constitute

an example of the combination thereof. The material of the sacrificial layer may also be any material that can secure etching selectivity with respect to the materials for the insulating films and the conductive films surrounding the sacrificial layer. Therefore, the conductive film may be a metal film or the like, rather than a polycrystalline silicon film. Furthermore, it is sufficient that the lower electrode of CMUT is a conductive film, or it may be a semiconductor substrate, or as shown in FIG. 3, a conductive film on an insulating film formed on a semiconductor substrate, or a conductive film on a semiconductor substrate in which a signal processing circuit is formed.

Embodiment 2

[0084] Whereas the embodiment 1 is an embodiment in which the conductive film is exposed to the hollow part from the underside of the hollow part, the embodiment 2 is an embodiment in which the conductive film is exposed to the hollow part from the upside of the hollow part.

[0085] FIG. 17 is a top view of an ultrasonic transducer (CMUT) according to the embodiment 2. FIG. 17 shows a single CMUT cell. The CMUT cell is constituted with the lower electrode 202, the hollow part 204 formed above the lower electrode 202, the upper electrode 208 formed above the hollow part 204, and so forth. The etching hole 210 for forming the hollow part is communicated with a portion to become the hollow part 204. The opening 212 is provided so as to reach the lower electrode 202, and the opening 213 is provided so as to reach the upper electrode 208. Between the lower electrode 202 and the hollow part 204, the insulating film 203 consisting of a silicon oxide film is formed so as to cover the lower electrode 202, and between the upper electrode 208 and the hollow part 204, the insulating film 207 consisting of a silicon oxide film is formed so as to cover the hollow part 204 and the lower electrode 202. However, these insulating films are not shown in the drawing, in order to show the hollow part 204 and the lower electrode 202. Moreover, the conductive film 221 is formed so as to be exposed to the hollow part 204, but it is not shown in the drawing.

[0086] FIG. 18, (a) is a sectional view along the line A-A' drawn in FIG. 17, and FIG. 18, (b) is a sectional view along the line B-B' drawn in FIG. 17. As shown in FIGS. 18, (a) and (b), the lower electrode 202 of the CMUT is disposed on the insulating film 201 consisting of a silicon oxide film and formed on the semiconductor substrate 200. Above the lower electrode 202, the hollow part 204 is formed through the insulating film 203 consisting of a silicon oxide film. Further, the conductive film 221 is disposed so that it is exposed to the hollow part 204 from the upside thereof at such a position that it overlaps with the hollow part as seen from above. The surfaces 205 and 206 correspond to upper and lower end planes of the hollow part. The insulating film 207 consisting of a silicon oxide film is disposed so as to surround the conductive film 221 and the hollow part 204, and the upper electrode 208 is formed on the insulating film 207. The insulating film 209 and the insulating film 211 consisting of silicon nitride films are disposed on the upper electrode 208. Further, the etching hole 210 is formed in the insulating film 207, the insulating film 209 and the conductive film 221 so as to penetrate these films and filled with the insulating film 211. This etching hole 210 is formed for forming the hollow part 204. The membrane 214 according to the embodiment 2 is constituted with the insulating films 207, 209 and 211, the upper electrode 208 and the conductive film 221.

[0087] The embodiment 2 is characterized in that the conductive film 221 is disposed to be exposed to the hollow part from the upside of the hollow part 204, contrary to the embodiment 1. When the conductive film 221 is disposed to be exposed to the hollow part from the upside of the hollow part 204, since the conductive film is an electrically isolated conductive film as in the embodiment 1, the conductive film 221 is made to have a potential corresponding to a distributed potential of the potential difference between the lower electrode 202 and the upper electrode 208 by the capacitance of the insulating films 203 and 207, and the hollow part 204 existing between the lower electrode 202 and the upper electrode 208, and the whole conductive film becomes isopotential. Therefore, in the insulating film 207 between the conductive film 221 and the lower electrode 208, electric field intensity is the same in the contact region 301 and the other region, thus concentration of leak electric currents in the contact region 301 can be suppressed, and accumulation of electrical charge in the insulating film 207 and degradation of dielectric strength thereof can be suppressed.

[0088] When the conductive film is disposed as described above, and the potential of the lower electrode is higher than that of the upper electrode when the CMUT is driven, electrons constituting the leak electric currents flow from the upper electrode 208 to the insulating film 207, the conductive film 221, the insulating film 207, and then the lower electrode 202 in this order. In this example, since the dielectric strength of the insulating film 207 is not degraded, flow of electrons itself can also be suppressed, and thus the leak electric currents can be reduced. Therefore, even if the electric field intensity of the insulating film 203 in the region in which the surface 206 above the hollow part and the surface 205 below the hollow part contact with each other remains to be higher than that in the region except for the contact region, the flow amount of electrons (current amount) concentrated in the contact region itself can be made small, and therefore accumulation of electrical charge in the insulating film 203 and degradation of dielectric strength thereof can be suppressed. That is, when the conductive film is disposed on the upper electrode side, degradation of the dielectric strength of the insulating films 203 and 207 can be suppressed by applying a direct voltage between the upper electrode and the lower electrode, so that potential of the lower electrode is higher than that of the upper electrode. As other effects, effects similar to those of the embodiment 1 can be obtained, provided that the relation of the upside and downside should be reversed as required.

[0089] As for the method for producing the CMUT cell of the embodiment 2, the CMUT cell can be produced by the same steps as shown in FIGS. 5 to 14, except that the order of the depositions of the conductive film and the sacrificial layer shown in FIG. 7 for the embodiment 1 should be reversed.

[0090] In the example shown in FIG. 17, the hollow part 204 and the conductive film 221 have the same shape as seen from above, and are disposed so as to overlap with each other. However, similarly to the embodiment 1, they are not limited to have such a configuration, the details of the acceptable size of the conductive film 221 as seen from above, a shape of the CPUT cell and materials constituting the CMUT cell are as described for the embodiment 1, and also similarly to the embodiment 1, the lower electrode may be a semiconductor substrate. Therefore, detailed explanations are omitted.

Embodiment 3

[0091] Although the embodiments 1 and 2 are embodiments in which the conductive film is exposed to the hollow

part from either one of the upside and underside of the hollow part, the embodiment 3 is an embodiment in which both a conductive film exposed to the hollow part from the upside thereof and a conductive film exposed to the hollow part from the underside thereof are disposed.

[0092] FIG. 19 is a top view of an example (first example) of ultrasonic transducer (CMUT) according to the embodiment 3. FIG. 19 shows a single CMUT cell as shown for the embodiments 1 and 2, but the shape of the cell of the embodiment 3 is different from those of the cells of the embodiments 1 and 2. The CMUT cell is constituted with the lower electrode 202, the hollow part 204 formed above the lower electrode 202, the upper electrode 208 disposed above the hollow part 204, and so forth. The etching hole 210 for forming the hollow part is communicated with a portion to become the hollow part 204. The opening 212 is provided so as to reach the lower electrode 202, and the opening 213 is provided so as to reach the upper electrode 208. Between the lower electrode 202 and the hollow part 204, the insulating film 203 consisting of a silicon oxide film is formed so as to cover the lower electrode 202, and between the upper electrode 208 and the hollow part 204, the insulating film 207 consisting of a silicon oxide film is formed so as to cover the hollow part 204 and the lower electrode 202. However, these insulating films are not shown in the drawing, in order to show the hollow part 204 and the lower electrode 202.

[0093] A conductive film 2211 is disposed so as to be exposed to the hollow part from the underside of the hollow part, and the shape thereof as seen from above is indicated with an alternate long and short dash line. Moreover, a conductive film 2212 is disposed so as to be exposed to the hollow part from the upside of the hollow part, and the shape thereof as seen from above is indicated with a dotted line. Further, the region 301 in which the surface below the hollow part 204 and the surface above the hollow part 204 contact with each other when the CMUT cell is driven is indicated with a two-dot chain line. Since the cell has a rectangular shape, the contact region 301 also has an approximately rectangular shape.

[0094] FIG. 20, (a) is a sectional view along the line A-A' drawn in FIG. 19, and FIG. 20, (b) is a sectional view along the line B-B' drawn in FIG. 19. As shown in FIGS. 20, (a) and (b), the lower electrode 202 of the CMUT is disposed on the insulating film 201 consisting of a silicon oxide film and formed on the semiconductor substrate 200. Above the lower electrode 202, the hollow part 204 is formed through the insulating film 203 consisting of a silicon oxide film. Further, the conductive film 2211 is disposed so as to be exposed to the hollow part 204, and the conductive film 2212 is disposed so as to be exposed to the hollow part 204. The insulating film 207 consisting of a silicon oxide film is disposed so as to surround the conductive films 2211 and 2212, and the hollow part 204, and the upper electrode 208 is disposed on the insulating film 207. The insulating film 209 and the insulating film 211 consisting of silicon nitride films are disposed on the upper electrode 208. Further, the etching hole 210 is formed in the insulating film 207, the insulating film 209 and the conductive film 2212 so as to penetrate these films and filled with the insulating film 211. This etching hole 210 is formed for forming the hollow part 204. The membrane 214 according to the embodiment 3 is constituted with the insulating films 207, 209 and 211, the upper electrode 208 and the conductive film 2212.

[0095] The embodiment 3 is characterized in that both the conductive film 2211 disposed on the side of the surface 205

below the hollow part **204** and the conductive film **2212** disposed on the side of the surface **206** above the hollow part **204** are disposed so that they are not overlap with each other in the region **301** in which the surface **205** below the hollow part and the surface **206** above the hollow part contact with each other as seen from above, when the CMUT cell is driven, and that the contact region **301** and both the conductive films **2211** and **2212** overlap with each other as seen from above. According to the embodiment 3, for example, in a vertical section including the hollow part (FIG. 20, (a)), the conductive film **2211** is disposed on the left of the center of the hollow part, and the conductive film **2212** is disposed on the right of the center of the hollow part, and parts of these conductive films extend to the contact region **301**.

[0096] FIGS. 21, (a) and (b) are an enlarged view of the contact region **301** in a state that the surface **205** below the hollow part **204** and the surface **206** above the hollow part **204** contact with each other when the CMUT cell according to the embodiment 3 is driven, and an equivalent circuit diagram, respectively. It is not necessarily required that both the conductive films **2211** and **2212** are exposed to the hollow part **204**, and an insulating film may be disposed between the conductive films and the hollow part. However, for convenience of explanation, explanation will be made with reference to a structure in which the conductive films are exposed to the hollow part, like the embodiments 1 and 2. Hereafter, effects of the embodiment 3 will be explained.

[0097] When the conductive film **2211** exposed to the hollow part from the side of the surface **205** below the hollow part **204** and the conductive film **2212** exposed to the hollow part from the side of the surface **206** above the hollow part **204** are disposed so that the both overlap with the contact region **301** as seen from above as shown in FIGS. 19 and 20, both the conductive films **2211** and **2212** has the same structure in the contact region, i.e., they are between the lower electrode **202** and the upper electrode **208** through the insulating films **203** and **207**, when the CMUT cell is driven. In such a case, potentials of the conductive films **2211** and **2212** are those obtained by distributing the voltage applied between the lower electrode **202** and the upper electrode **208** according to the capacitances of the insulating films **203** and **207** as shown in FIG. 21, (b), and as a result, the conductive films **2211** and **2212** have the same potential V1. This is because the conductive films **2211** and **2212** are electrically isolated conductive films.

[0098] At this time, in the region of the conductive film **2211** shown in FIG. 21, (b), electric field intensities in the contact region **301** and the region other than the contact region of the insulating film **203** between the conductive film **2211** and the lower electrode **202** become equivalent, thus concentration of the leak electric currents in the contact region **301** can be suppressed, and accumulation of electrical charge in the insulating film **203** and degradation of dielectric strength thereof can be suppressed. On the other hand, electric field intensity of the insulating film **207** in the contact region **301** corresponds to a value obtained by dividing V2 with thickness of the insulating film **207**, and is higher than that of the non-contact region other than the contact region **301**. However, since the conductive film **2212** having the same electric potential as that of the conductive film **2211** is also disposed, in the region of the conductive film **2212**, electric field intensity of the insulating film **207** in the non-contact region other than the contact region **301** also corresponds to a value obtained by dividing V2 with thickness of

the insulating film **207**, which is equal to the electric field intensity of the insulating film **207** in the contact region in the region of conductive film **2211**. As a result, concentration of the leak electric currents in the insulating film **207** in the contact region can be suppressed.

[0099] Also in the region of the conductive film **2212**, electric field intensities of the contact region **301** and the region other than the contact region of the insulating film **207** between the conductive film **2212** and the upper electrode **208** become equivalent, thus concentration of the leak electric currents in the contact region **301** can be suppressed, and accumulation of electrical charge in the insulating film **207** and degradation of dielectric strength thereof can be suppressed, as in the aforementioned embodiment 2. On the other hand, electric field intensity of the insulating film **203** in the contact region **301** corresponds to a value obtained by dividing V1 with thickness of the insulating film **203**, and is higher than that of the non-contact region other than the contact region **301**. However, since the conductive film **2211** having the same electric potential as that of the conductive film **2212** is also disposed, electric field intensity of the insulating film **203** in the non-contact region other than the contact region **301** in the region of the conductive film **2211** also corresponds to a value obtained by dividing V1 with thickness of the insulating film **203**, which is equal to the electric field intensity of the insulating film **207** in the contact region in the region of conductive film **2212**. As a result, concentration of the leak electric currents in the insulating film **203** of the contact region can be suppressed.

[0100] That is, even if the surfaces above and below the hollow part contact with each other, the conductive film **2212** exerts an electric field attenuating function for the insulating film **207** with respect to the conductive film **2211**, and the conductive film **2211** exerts an electric field attenuating function for the insulating film **203** with respect to the conductive film **2212**. Therefore, concentration of the leak electric currents in the insulating films **203** and **207** in the contact region **301** can be suppressed, and accumulation of electrical charge in the insulating films **203** and **207** and degradation of dielectric strength thereof can be suppressed.

[0101] Next, the method for producing the CMUT cell described as the embodiment 3 will be explained with reference to the drawings. The steps up to the formation of the insulating film **203** are the same as those shown in FIGS. 5 and 6 explained for the aforementioned embodiment 1. FIG. 22, (a) to FIG. 28, (a) show sections along the line A-A' drawn in FIG. 19, and FIG. 22, (b) to FIG. 28, (b) show sections along the line B-B' drawn in FIG. 19.

[0102] First, as shown in FIGS. 22 (a) and (b), an aluminum alloy film serving as the electrically isolated conductive film **2211** is deposited in 50 nm thickness on the upper surface of the insulating film **203** by the sputtering method, and patterning is performed by photolithography and dry etching techniques. Then, a polycrystalline silicon film **7011** is deposited in 150 nm thickness by the plasma-CVD method. Then, as shown in FIGS. 23, (a) and (b), the polycrystalline silicon film **7011** is polished by 100 nm by the CMP method (Chemical Mechanical Polishing) to expose the surface of the aluminum alloy film **2211** serving as the electrically isolated conductive film **2211**. Then, as shown in FIGS. 24, (a) and (b), a polycrystalline silicon film **7012** is deposited in 50 nm thickness by the plasma-CVD method.

[0103] Then, an aluminum alloy film serving as the conductive film **2212** is deposited in 50 nm thickness on the upper

surface of the polycrystalline silicon film **7012** and the aluminum alloy film **2211** by the sputtering method, and patterning is performed by the photolithography and dry etching techniques (FIGS. **25**, (a) and (b)). This patterning is performed so that the conductive films **2211** and **2212** do not overlap with each other as seen from above, and they overlap with the region in which the surfaces above and below the hollow part formed by the following steps contact with each other as seen from above when the CMUT cell is driven.

[**10104**] Then, as shown in FIGS. **26**, (a) and (b), a polycrystalline silicon film **7013** is deposited in 150 nm thickness by the plasma-CVD method. Then, as shown in FIGS. **27**, (a) and (b), the polycrystalline silicon film **7013** is polished by 100 nm by the CMP method to expose the surface of the aluminum alloy film serving as the conductive film **2212**. Then, patterning is performed for the aluminum alloy films **2211** and **2212** and the polycrystalline silicon films **7011**, **7012**, and **7013** by the photolithography and dry etching techniques to form a sacrificial layer consisting of the conductive films **2211** and **2212** and the polycrystalline silicon films **7011**, **7012**, and **7013** on the insulating film **203** (FIGS. **28**, (a) and (b)). The hollow part is formed at the position of the sacrificial layer in a subsequent step. As for the following steps, the CMUT cell of this embodiment 3 shown in FIGS. **19** and **20** can be produced by the same steps as those shown in FIGS. **8** to **14** explained for the embodiment 1.

[**10105**] FIG. **29** includes sectional views of the ultrasonic transducer according to the second example of the embodiment 3. The top view of the ultrasonic transducer of this example is the same as that shown in FIG. **19**. The difference from the first example is that the conductive films **2211** and **2212** are in contact with the hollow part **204** through the insulating films **2901** and **2902**, respectively, and the other structures are the same. Even with such a configuration, concentration of the leak electric currents in the contact region **301** can be suppressed, and accumulation of electrical charge in the insulating films **203**, **2901**, **207**, and **2902**, and degradation of dielectric strength thereof can be reduced.

[**10106**] The method for producing the ultrasonic transducer shown in FIG. **29** is shown in FIGS. **30** to **39**. The steps up to the formation of the insulating film **203** are the same as those shown in FIGS. **5** and **6** explained for the aforementioned embodiment 1. In this case, thickness of the insulating film consisting of a silicon oxide film between the upper and lower electrodes is set to be the same as that of the first example of this embodiment 3, i.e., 50 nm. First, as shown in FIGS. **30**, (a) and (b), an aluminum alloy film serving as the conductive film **2211** is deposited in 50 nm thickness on the upper surface of the insulating film **203** by the sputtering method, and patterning is performed by the photolithography and dry etching techniques. Then, an insulating film consisting of a silicon oxide film is deposited in 50 nm thickness by the plasma-CVD method (FIGS. **31**, (a) and (b)).

[**10107**] Then, as shown in FIGS. **32** (a) and (b), a polycrystalline silicon film **7011** is deposited in 200 nm thickness by the plasma-CVD method, and the polycrystalline silicon film **701** is polished by 100 nm by the CMP method (FIGS. **33**, (a) and (b)). Then, as shown in FIGS. **34**, (a) and (b), patterning is performed for the polycrystalline silicon film **701** by the photolithography and dry etching techniques to form a pit **3401** of 50 nm.

[**10108**] Then, as shown in FIGS. **35**, (a) and (b), an insulating film **2902** consisting of a silicon oxide film is deposited by the plasma-CVD method so as to cover the polycrystalline

silicon film **701**. At the time of this deposition, the insulating film **2902** also deposits in the pit **3401**. Then, an aluminum alloy film serving as the conductive film **2212** is deposited in 200 nm thickness on the upper surface of the insulating film **2902** by the sputtering method (FIGS. **36**, (a) and (b)), and polished by 150 nm by the CMP method to expose the surface of the insulating film **2902** (FIGS. **37**, (a) and (b)).

[**10109**] Then, patterning is performed for the insulating films **2901** and **2902**, the aluminum alloy films **2211** and **2212**, and the polycrystalline silicon film **701** by the photolithography and dry etching techniques to form a sacrificial layer consisting of the conductive films **2211** and **2212** and the polycrystalline silicon film **701** on the insulating film **203** (FIGS. **38**, (a) and (b)). The hollow part is formed at the position of the sacrificial layer in a subsequent step. Finally, the insulating film **207** consisting of a silicon oxide film is deposited in 50 nm thickness by the plasma-CVD method (FIGS. **39**, (a) and (b)). The following steps are the same steps as those shown in FIGS. **8** to **14** explained for the embodiment 1 to produce the CMUT cell of the second example according to the embodiment 3 shown in FIG. **29**.

[**10110**] The characteristics of the embodiment 3 will be further explained in more detail. The effect of the disposition of the conductive films **221** and **2212** so that both of them overlap with the region **301** in which the surface **205** below the hollow part and the surface **206** above the hollow part contact with each other as seen from above when the CMUT cell is driven is as explained with reference to FIG. **21**, (b). Another characteristic effect of the disposition, i.e., such disposition of the conductive film **2211** disposed on the side of the surface **205** below the hollow part **204** and the conductive film **2212** disposed on the side of the surface **206** above the hollow part **204** that they do not overlap with each other in the contact region **301** as seen from above, will be explained below. If the conductive films **2211** and **2212** are disposed so that they overlap with each other in the area of the contact region **301** as seen from above, and the conductive films are not covered with an insulating film, the conductive films **2211** and **2212** directly contact with each other. When the conductive films **2211** and **2212** contact with each other, they have the same potential, and there arises a problem that they are adsorbed by each other due to electrostatic attraction between the electrical charges induced in the conductive films, and cannot be separated.

[**10111**] Further, even if the conductive films are covered with insulating films, the conductive films contact with each other through only the insulating films, and therefore there arises a problem that the conductive films are adsorbed by each other through the insulating films due to strong electrostatic attraction. Therefore, such a disposition as mentioned above is intentionally employed to suppress the mutual adsorption of the conductive films.

[**10112**] That is, in the case of the example in which the conductive films are exposed to the hollow part, since the conductive films are disposed so that they do not overlap with each other as seen from above, even if the surfaces above and below the hollow part contact with each other, the conductive films **2211** and **2212** do not contact with each other, and therefore the aforementioned problem of the adsorption can be avoided. Further, in the case of the example in which the conductive films are exposed to the hollow part through insulating films, that is, the conductive films are embedded in insulating films, if the conductive films do not overlap with each other as seen from above, the aforementioned problem

of the adsorption can be avoided. In a more preferred example, the conductive films and the insulating films **2901** and **2902** covering them are formed so that a hollow part is provided between the insulating films **2901** and **2902** in the contact region **301**, when the surfaces above and below the hollow part contact with each other. This is because such disposition can further reduce the electrostatic attraction between the conductive films, and suppress the adsorption by the electrostatic attraction.

[0113] In addition, in the case of the example in which the conductive films are exposed to the hollow part, the effect that electrical charge does not easily accumulate can of course be further obtained like the embodiment 1. Further, a structure in which electrical charge is more easily accumulated is provided by the insulating films **2901** and **2902** compared with a case where these insulating films are not provided, but even if the surfaces above and below the hollow part contact with each other, the conductive film **2212** exerts an electric field attenuating function for the insulating film **207** with respect to the conductive film **2211**, and the conductive film **2211** exerts an electric field attenuating function for the insulating film **203** with respect to the conductive film **2212**, as described above. Therefore, concentration of the leak electric currents in the insulating films **203** and **207** in the contact region **301** can be suppressed, and accumulation of electrical charge in the insulating films **203** and **207** and degradation of dielectric strength thereof can be suppressed.

[0114] In addition, although the CMUT cell according to the embodiment 3 shown FIG. **19** has a rectangular shape as the planar shape, it may have another shape. FIGS. **40** and **41** are a top view and a sectional view of an example where the cell has a hexagonal shape (third example). Also in this case, the conductive film **2211** exposed to the hollow part from the side of the surface below the hollow part **204** and the conductive film **2212** exposed to the hollow part from the side of the surface above the hollow part **204** are disposed so that they do not overlap with each other as seen from above, and both the conductive films **2211** and **2212** overlap with the region **301** where the surfaces below and above the hollow part contact with each other as seen from above, when the CMUT cell is driven. Therefore, concentration of the leak electric currents in the contact region **301** can be suppressed, and accumulation of electrical charge in the insulating films **203** and **207**, and degradation of dielectric strength thereof can be suppressed.

[0115] Further, although shapes of the conductive films **2211** and **2212** shown in FIG. **19** are symmetric with respect to the line B-B' as seen from above, they may be unsymmetrical as shown in FIG. **42** (fourth example). If the conductive films **2211** and **2212** are disposed so that the both overlap with the contact region **301** as seen from above, the same effect can be obtained. FIG. **43**, (b) is a sectional view along the line B-B' drawn in FIG. **42**. In the example shown in FIGS. **40** to **43**, the conductive films may contact with the hollow part through insulating films like the relation between the configurations of FIGS. **20** and **29**. Moreover, although the end of the conductive film is located at the same position as the end of the hollow part in all the drawings, the structure is not limited to such an example in which the conductive film reaches the end of the hollow part. Furthermore, only one of the hollow part may be exposed to the hollow part, but the other conductive film may contact with the hollow part through an insulating film. In addition, materials constituting the CMUT cell are similar to those explained for the embodiment 1, and

similarly to the embodiment 1, the lower electrode may be a semiconductor substrate. Therefore, detailed explanations are omitted.

Embodiment 4

[0116] In the embodiments 1 to 3 mentioned above, single CMUT cells have been explained. However, as the embodiment 4, a chip on which the CMUT cells are integrated and arranged in an array will be explained. FIG. **44** shows a part of a chip comprising rectangular CMUT cells of the embodiment 3 arranged in an array. It comprises the lower electrodes **2021**, **2022** and **2023**, the hollow parts **204** formed above the lower electrodes, the upper electrodes **208** formed above the hollow parts **204**, and so forth. The etching holes **211** for forming the hollow parts are communicated with the spaces serving as the hollow parts **204**. The openings **212** are provided so as to reach the lower electrodes **2021**, **2022** and **2023**, and the openings **213** are provided so as to reach the upper electrodes **208**. As explained for FIGS. **19** and **20**, the conductive films **2211** are disposed so as to be exposed to the hollow parts, the conductive films **2212** are disposed so as to be exposed to the hollow parts, but they are not shown in the drawing. Between the upper electrodes **208** and the hollow parts **204**, the insulating films **207** consisting of silicon oxide films are formed so as to cover the hollow parts **204**, the conductive films **2212** and the lower electrodes **202**, and between the lower electrodes **202**, and the hollow parts **204** and the conductive films **2211**, the insulating films **203** consisting of silicon oxide films are formed so as to cover the lower electrodes. However, these insulating films are not shown in the drawing, in order to show the lower electrodes **202** and the hollow parts **204**. The layer structure of a section of each CMUT cell shown in FIG. **44** is the same as that shown in FIG. **20**.

[0117] The disposition directions of the upper electrodes and the lower electrodes are perpendicular to each other, two CMUT cells are disposed at one intersection, and the upper electrodes of them are connected with wirings **1001**. In FIG. **44**, there is shown a part of the array, which comprises the upper electrodes for four channels in the azimuth direction and the lower electrodes for three channels in the elevation direction. As for a probe used for an ultrasonic diagnostic device, in the case of a general linear probe, for example, upper electrodes for 192 channels are disposed.

[0118] In the case of a probe having such a plurality of lower electrodes disposed in the elevation direction as shown in FIG. **44**, form and intensity of ultrasonic beam transmitted and received at each intersection of the upper electrode and the lower electrode can be controlled by changing the voltage applied to each lower electrode, and thereby improvement in image quality of diagnostic images can be expected. Although difference of the voltage applied to the upper and lower electrodes changes according to the voltage applied to each lower electrode, since electric potential of the conductive film is determined by difference of potential between those of the upper electrode and lower electrode applied in each CMUT cell, the effect of suppressing accumulation of electrical charge in an insulating film and degradation of dielectric strength thereof obtained by the disposition of the conductive films in each single CMUT cell is also effective for the case in which the CMUT cells are arranged in an array and used as an ultrasonic probe.

[0119] The shapes of the conductive films **2211** and **2212** as seen from above may be a shape that includes the region **301**

where the surface **206** above the hollow part and the surface **205** below the hollow part contact with each other. They may not have the same size as that of the hollow part **204**, but a size included in the area of the hollow part, as seen from above. The size may be appropriately chosen so that concentration of electric fields in the insulating film can be reduced. Further, the sizes of the conductive films **2211** and **2212** may be larger than that of the hollow part **204** as seen from above. In this case, concentration of the electric currents in the insulating film in the contact region **301** can be further reduced by the larger conductive films **2211** and **2212**.

[0120] Although the CMUT cells shown in FIGS. **19**, **40**, and **42** have a rectangular shape or a hexagonal shape as the planar shape, the shape is not limited to these, and the CMUT cell may have, for example, a circular shape or a polygonal shape. In addition, materials constituting the CMUT cell are similar to those explained for the embodiment 1, and similarly to the embodiment 1, the lower electrode may be a semiconductor substrate. Therefore, detailed explanations are omitted.

Embodiment 5

[0121] As the embodiments 1 to 4, CMUT cells constituting an ultrasonic transducer and a cell array have been explained. As the embodiment 5, an example relating to driving of CMUT cell will be explained.

[0122] FIG. **45** is a schematic sectional view of the CMUT cell of the embodiment 1. The conductive film **221** is disposed on the lower electrode **202** through the insulating film **203** so as to be exposed to the hollow part. Further, the upper electrode is disposed above the hollow part **204** through the insulating film **207**. A direct voltage **3001** and an alternating voltage **3002** are superimposingly applied to the lower electrode and the upper electrode, and a switch **3003** is connected to the conductive film **221** to provide a configuration that the conductive film **221** can be grounded via the switch **3003**.

[0123] At the time of driving the CMUT cell, if the surface **206** above the hollow part contacts with the surface **205** below the hollow part, and the conductive film is charged with weak leak electric currents flowing in the insulating films **203** and **207**, effectual potential difference between the upper and lower electrodes may be changed. The embodiment 5 is characterized in that the state of the conductive film **221** is made to be switchable between a grounded state and a floating state by connection and disconnection with the switch **3003**, so that electrical charge charged in the conductive film **221** can be discharged. Since the transducer of this embodiment is provided with such a switch with which electrical charge can be discharged from the conductive film, the effect of disposing the conductive film so as to be exposed to the hollow part as shown in FIG. **45** can be similarly obtained even when an insulating film is disposed between the conductive film and the hollow part, i.e., even when the conductive film is embedded in the insulating film.

[0124] The operation of the switch **3003** at the time of carrying out ultrasonic diagnosis with a probe using the ultrasonic transducer constituted with the CMUT cells according to this embodiment will be explained with reference to FIG. **46**. FIG. **46** shows effectual potential difference between the upper electrode **208** and the lower electrode **202**, electric potential of the conductive film **221**, ON/OFF of the direct voltage **3001** and the alternating voltage **3002**, and disconnection and connection (OFF/ON) of the switch **3003** at the time of ultrasonic diagnosis.

[0125] Before starting the diagnosis, the switch **3003** is made to be in the ON state to ground the conductive film **221**. At the time of starting the diagnosis, the state of the switch **3003** is changed to the OFF state from the ON state to make the conductive film **221** in a floating state, i.e., a state that it is electrically isolated, and the diagnosis is performed. Degradation of the insulating films **203** and **207** can be thereby suppressed as explained for the embodiments 1, 2 and 3. If the conductive film **221** is gradually charged during the diagnosis, and charged for a potential of V_c at the end of the diagnosis, the effectual potential difference V_d between the upper and lower electrodes set at the time of the start of the diagnosis in order to obtain transmission sound pressure of supersonic waves and reception sensitivity required for the diagnosis is lowered by V_c . If the switch **3003** is continuously maintained to be in the OFF state, i.e., the conductive film **221** is in a state that it cannot be grounded, the conductive film **221** is further charged at the time of the next diagnosis, thus the effectual potential difference is further reduced from that reduced by V_c , and transmission sound pressure of supersonic waves and reception sensitivity required for the diagnosis can no longer be obtained. However, since this embodiment employs a configuration that the conductive film **221** can be grounded via the switch **3003**, the switch **3003** can be made to be in the ON state at the end of the diagnosis to ground the conductive film **221**, and thereby the charged electrical charge can be discharged. Therefore, the effectual potential difference between the upper and lower electrodes can be returned to V_d at the time of the next diagnosis, and the transmission sound pressure of supersonic waves and reception sensitivity required for the diagnosis can be obtained.

[0126] The timing for turning on or off the switch **3003** may be determined according to the electrification amount V_c of the conductive film. Although the state of the switch is changed in a period between one diagnosis and a subsequent diagnosis in the example shown in FIG. **46**, the switch may be turned on or off when it becomes impossible to obtain the transmission sound pressure of supersonic waves and reception sensitivity required for the diagnosis due to reduction by V_c . Therefore, it may be changed in a shorter cycle, for example, between transmission and reception or between sets of transmission and reception, or it may be changed in a longer cycle, for example, once a day.

[0127] Further, although this embodiment was explained with reference to the CMUT cell in which the conductive film **221** is disposed so as to be exposed to the hollow part mentioned for the embodiment 1, the same effect can also be obtained for the CMUT cells or array mentioned as the embodiments 2, 3 and 4 by providing the configuration that the conductive film can be grounded via a switch. When there are two conductive films as in, for example, the embodiments 3 and 4, a switch for controlling grounding and no grounding may be connected to each of the both conductive films, or only one of them.

Embodiment 6

[0128] Finally, configuration and role of an ultrasonic diagnostic device provided with the ultrasonic transducer of the present invention will be explained with reference to FIG. **47**. The ultrasonic diagnostic device **1201** comprises an ultrasonic probe **1202**, a transmission and reception separation part **1203**, a transmission part **1204**, a bias part **1206**, a recep-

tion part **1208**, a phasing and addition part **1210**, an image processing part **1212**, a display part **1214**, a control part **1216**, and an operation part **1218**.

[0129] The ultrasonic probe **1202** is a device for transmitting and receiving ultrasonic waves to and from a subject, which is used by being contacted with the subject. Ultrasonic waves are transmitted to the subject from the ultrasonic probe **1202**, and reflected echo signals emitted from the subject are received by the ultrasonic probe **1202**. The ultrasonic transducer according to any one of the embodiments 1 to 5 is disposed inside the ultrasonic probe **1202** and electrically connected with the transmission and reception separation part **1203** explained later. The transmission part **1204** and the bias part **1206** are devices for supplying driving signals to the ultrasonic probe **1202**. The reception part **1208** is a device for receiving the reflected echo signals outputted from the ultrasonic probe **1202**. The reception part **1208** further performs processings such as analog-to-digital conversion for the received reflected echo signals. The transmission and reception separation part **1203** is for switching and separating transmission and reception, so that the driving signals are passed from the transmission part **1204** to the ultrasonic probe **1202** at the time of transmission, and received signals are passed from the ultrasonic probe **1202** to the reception part **1208** at the time of reception. The phasing and addition part **1210** is a device for performing phasing and addition of the received reflected echo signals. The image processing part **1212** is a device for constituting a diagnosis image (for example, tomographic images and angiographic images) on the basis of the reflected echo signals subjected to the phasing and addition. The display part **1214** is a display device for displaying a diagnostic image produced by image processing. The control part **1216** is a device for controlling the elements mentioned above. The control part **1216** has a role of controlling the ultrasonic probe **1202** as well as a role of controlling ON/OFF of the switch for controlling grounding and no grounding of the conductive film of the embodiment 5. The operation part **1218** is a device for giving directions to the control part **1216**. The operation part **1218** may be, for example, an inputting device such as trackball, keyboard and mouse.

INDUSTRIAL APPLICABILITY

[0130] The ultrasonic transducer and ultrasonic diagnostic device of the present invention can be widely used as medical diagnostic devices or diagnostic devices for structures.

DESCRIPTION OF NUMERICAL NOTATIONS

[0131] **101, 202, 2021, 2022, 2023** Lower electrode
 [0132] **102, 204** Hollow part
 [0133] **200** Semiconductor substrate
 [0134] **103, 201, 203, 207, 209, 211, 2901, 2902** Insulating film
 [0135] **104, 208** Upper electrode
 [0136] **105, 214** Membrane
 [0137] **106, 206** Surface above hollow part
 [0138] **107, 205** Surface below hollow part
 [0139] **210** Etching hole
 [0140] **212** Opening reaching lower electrode
 [0141] **213** Opening reaching upper electrode
 [0142] **221, 2211, 2212** Conductive film
 [0143] **301** Region for contact of surface above hollow part and surface below hollow part

[0144] **701, 7011, 7012, 7013** Sacrificial layer
 [0145] **1001** Wiring connecting upper electrodes
 [0146] **3001** Direct voltage
 [0147] **3002** Alternating voltage
 [0148] **3003** Switch connected to conductive film
 [0149] **3401** Pit
 [0150] **1201** Ultrasonic diagnostic device
 [0151] **1202** Ultrasonic probe
 [0152] **1203** Transmission and reception separation part
 [0153] **1204** Transmission part
 [0154] **1206** Bias part
 [0155] **1208** Reception part
 [0156] **1210** Phasing and addition part
 [0157] **1212** Image processing part
 [0158] **1214** Display part
 [0159] **1216** Control part
 [0160] **1218** Operation part

1. An ultrasonic transducer comprising:

a first electrode,
 a first insulating film disposed on the first electrode,
 a hollow part provided above the first insulating film,
 a second insulating film disposed above the hollow part,
 a second electrode disposed on the second insulating film,
 and

an electrically isolated conductive film disposed between the first electrode and the second electrode, wherein:
 the conductive film is disposed at such a position that, as seen from above, the conductive film overlaps with a region in which surfaces above and below the hollow part contact with each other when the transducer is driven, and the conductive film is exposed to the hollow part.

2. The ultrasonic transducer according to claim 1, wherein:
 the conductive film is larger than the region as seen from above.

3. The ultrasonic transducer according to claim 1, wherein:
 the conductive film is disposed on the side of the first insulating film, and
 a voltage lower than that applied to the second electrode is applied to the first electrode.

4. The ultrasonic transducer according to claim 1, wherein:
 the conductive film is disposed on the side of the second insulating film, and
 a voltage higher than that applied to the second electrode is applied to the first electrode.

5. An ultrasonic diagnostic device provided with:
 an ultrasonic probe comprising the ultrasonic transducer according to claim 1, and
 a control part for controlling the ultrasonic probe.

6. An ultrasonic transducer comprising:
 a first electrode,
 a first insulating film disposed on the first electrode,
 a hollow part provided above the first insulating film,
 a second insulating film disposed above the hollow part,
 a second electrode disposed on the second insulating film,
 a conductive film disposed between the first electrode and the second electrode at such a position that, as seen from above, the conductive film overlaps with a region in which surfaces above and below the hollow part contact with each other when the transducer is driven, and
 a switch connected to the conductive film for controlling ON/OFF of connection of the conductive film to the ground potential.

7. The ultrasonic transducer according to claim 6, wherein: the conductive film is exposed to the hollow part.
8. The ultrasonic transducer according to claim 6, wherein: the conductive film is embedded in either one of the first insulating film and the second insulating film.
9. The ultrasonic transducer according to claim 6, wherein: the conductive film is larger than the region as seen from above.
10. The ultrasonic transducer according to claim 6, wherein:
 - the conductive film is disposed on the side of the first insulating film, and
 - a voltage lower than that applied to the second electrode is applied to the first electrode.
11. The ultrasonic transducer according to claim 6, wherein:
 - the conductive film is disposed on the side of the second insulating film, and
 - a voltage higher than that applied to the second electrode is applied to the first electrode.
12. An ultrasonic diagnostic device provided with:
 - an ultrasonic probe comprising the ultrasonic transducer according to claim 6, and
 - a control part for controlling the ultrasonic probe.
13. An ultrasonic diagnostic device provided with:
 - an ultrasonic probe comprising the ultrasonic transducer according to claim 6, and
 - a control part for controlling the ultrasonic probe and the switch, wherein:
 - the control part switches state of the switch from ON state to OFF state at the time of start of diagnosis.
14. An ultrasonic transducer comprising:
 - a first electrode,
 - a first insulating film disposed on the first electrode,
 - an electrically isolated first conductive film disposed on the first insulating film,
 - a hollow part provided above the first conductive film,
 - an electrically isolated second conductive film disposed above the hollow part,
 - a second insulating film disposed on the second conductive film, and
 - a second electrode disposed on the second insulating film, wherein:
 - the first conductive film and the second conductive film are disposed in a region in which surfaces above and below the hollow part contact with each other when the transducer is driven, and
 - the first conductive film and the second conductive film do not overlap with each other in that region as seen from above.
15. The ultrasonic transducer according to claim 14, wherein:
 - the first and second conductive films are exposed to the hollow part.
16. The ultrasonic transducer according to claim 14, wherein:
 - the first conductive film is embedded in the first insulating film, and
 - the second conductive film is embedded in the second insulating film.
17. The ultrasonic transducer according to claim 14, wherein:
 - the first conductive film is disposed on the left of the center of the hollow part in a vertical section including the hollow part, and
 - the second conductive film is disposed on the right of the center of the hollow part in the vertical section.
18. The ultrasonic transducer according to claim 14, which is further provided with:
 - a first switch connected to the first conductive film for controlling ON/OFF of connection of the first conductive film to the ground potential, and
 - a second switch connected to the second conductive film for controlling ON/OFF of connection of the second conductive film to the ground potential.
19. An ultrasonic diagnostic device provided with:
 - an ultrasonic probe comprising the ultrasonic transducer according to claim 14, and
 - a control part for controlling the ultrasonic probe.
20. An ultrasonic diagnostic device provided with:
 - an ultrasonic probe comprising the ultrasonic transducer according to claim 18, and
 - a control part for controlling the ultrasonic probe, the first switch and the second switch, wherein:
 - the control part switches states of the first and second switches from ON states to OFF states at the time of start of diagnosis.

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专利名称(译)	超声波换能器和使用其的超声波诊断装置		
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摘要(译)

在超声换能器中，包括第一电极，设置在第一电极上的第一绝缘膜，设置在第一绝缘膜上方并设置在中空部分上方和下方的表面之间的中空部分，设置在中空部分上方的第二绝缘膜，和设置在第二绝缘膜上的第二电极，设置在中空部分下方的表面一侧上的第一导电膜和设置在中空部分上方的表面一侧上的第二导电膜，第一导电膜和设置第二导电膜使得它们与当驱动换能器时从上方看时空部分上方和下方的表面彼此接触的区域重叠，并且它们在该区域中彼此不重叠。以上。利用这种结构，提供了一种结构，即使当中空部分上方的表面与中空部分下方的表面接触时，也能够抑制接触区域中的绝缘膜中的电场和电流的集中，并且抑制注入。电荷进入绝缘膜并降低其介电强度，以及使用它的超声波诊断装置。

